



US009076768B2

(12) **United States Patent**
Kippelen et al.(10) **Patent No.:** **US 9,076,768 B2**(45) **Date of Patent:** **Jul. 7, 2015**(54) **SYSTEMS AND METHODS FOR PRODUCING LOW WORK FUNCTION ELECTRODES**(75) Inventors: **Bernard Kippelen**, Decatur, GA (US); **Canek Fuentes-Hernandez**, Atlanta, GA (US); **Yinhua Zhou**, Atlanta, GA (US); **Antoine Kahn**, Princeton, NJ (US); **Jens Meyer**, Princeton, NJ (US); **Jae Won Shim**, Atlanta, GA (US); **Seth R. Marder**, Atlanta, GA (US)(73) Assignees: **GEORGIA TECH RESEARCH CORPORATION**, Atlanta, GA (US); **THE TRUSTEES OF PRINCETON UNIVERSITY**, Princeton, NJ (US)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/117,965**(22) PCT Filed: **May 16, 2012**(86) PCT No.: **PCT/US2012/038125**

§ 371 (c)(1),

(2), (4) Date: **Feb. 3, 2014**(87) PCT Pub. No.: **WO2012/166366**PCT Pub. Date: **Dec. 6, 2012**(65) **Prior Publication Data**

US 2014/0131868 A1 May 15, 2014

Related U.S. Application Data

(60) Provisional application No. 61/486,368, filed on May 16, 2011, provisional application No. 61/591,370, filed on Jan. 27, 2012, provisional application No. 61/608,408, filed on Mar. 8, 2012.

(51) **Int. Cl.****H01L 21/441** (2006.01)**H01L 51/00** (2006.01)

(Continued)

(52) **U.S. Cl.**CPC **H01L 29/45** (2013.01); **H01L 51/5221** (2013.01); **H01B 1/24** (2013.01); (Continued)(58) **Field of Classification Search**

CPC ... H01L 29/45; H01L 51/5221; H01L 21/283; H01L 51/5092

USPC 438/642, 658, 99, 780

See application file for complete search history.

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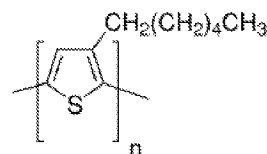
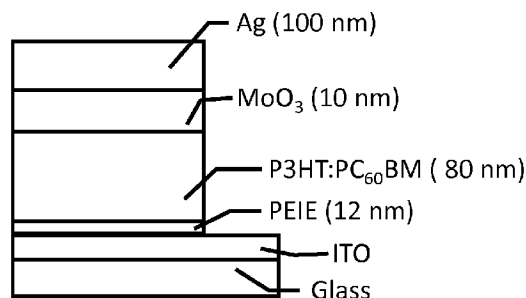
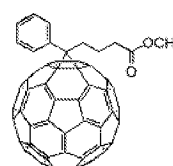
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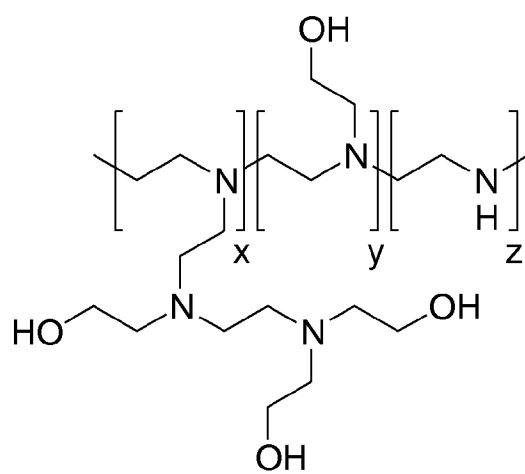
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Primary Examiner — Michele Fan(74) *Attorney, Agent, or Firm* — Troutman Sanders LLP; Ryan A. Schnider; Mark Lehi Jones(57) **ABSTRACT**

According to an exemplary embodiment of the invention, systems and methods are provided for producing low work function electrodes. According to an exemplary embodiment, a method is provided for reducing a work function of an electrode. The method includes applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer; and based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. According to another exemplary embodiment of the invention, a device is provided. The device includes a semiconductor; at least one electrode disposed adjacent to the semiconductor and configured to transport electrons in or out of the semiconductor.

18 Claims, 89 Drawing Sheets**P3HT****PC₆₀BM**

- (51) **Int. Cl.**
H01L 29/45 (2006.01)
H01L 51/52 (2006.01)
H01B 1/24 (2006.01)
H01L 51/50 (2006.01)
H01L 21/283 (2006.01)
H01L 51/10 (2006.01)
H01L 51/44 (2006.01)
- (52) **U.S. Cl.**
CPC **H01L 51/0036** (2013.01); **H01L 51/5092**
(2013.01); **H01L 51/5234** (2013.01); **H01L**
2251/308 (2013.01); **H01L 21/283** (2013.01);
H01L 51/0037 (2013.01); **H01L 51/105**
(2013.01); **H01L 51/445** (2013.01)
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FIG. 1

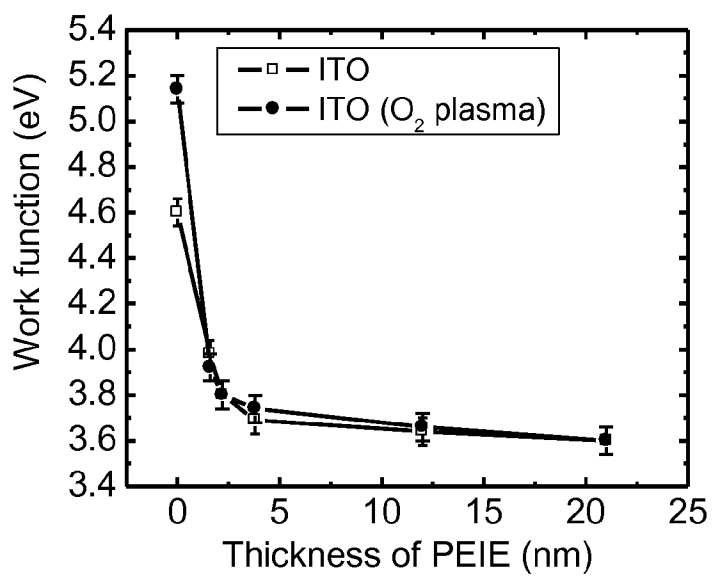


FIG. 2

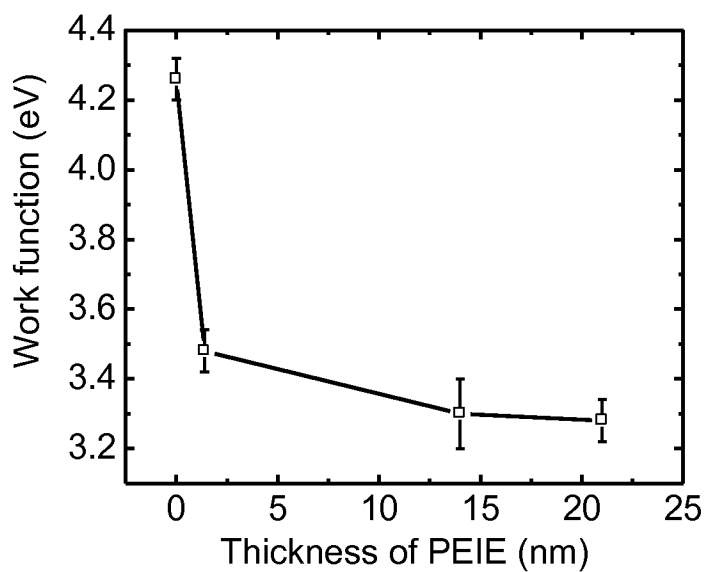


FIG. 3

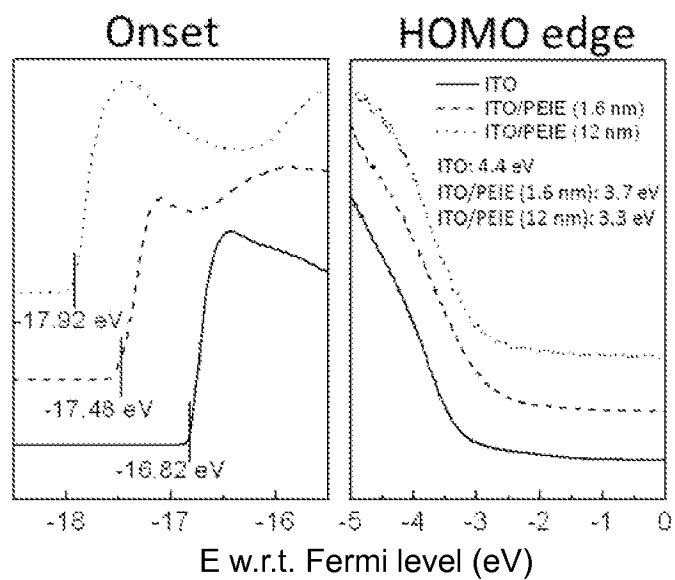


FIG. 4

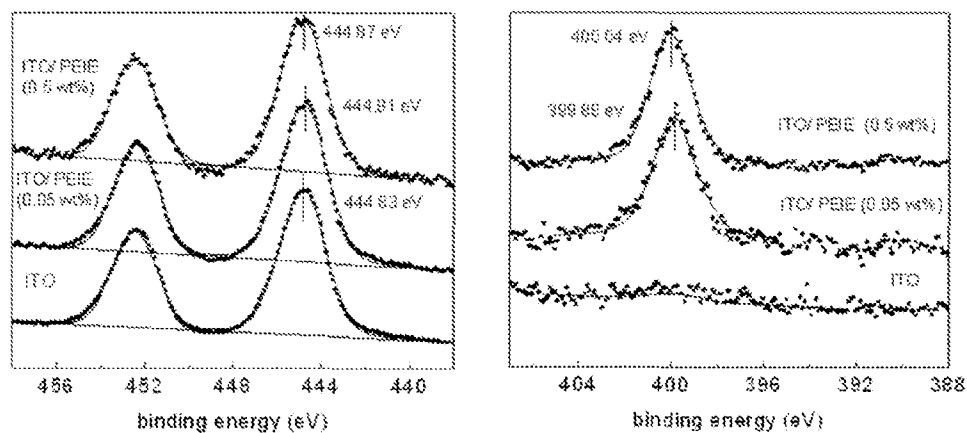


FIG. 5

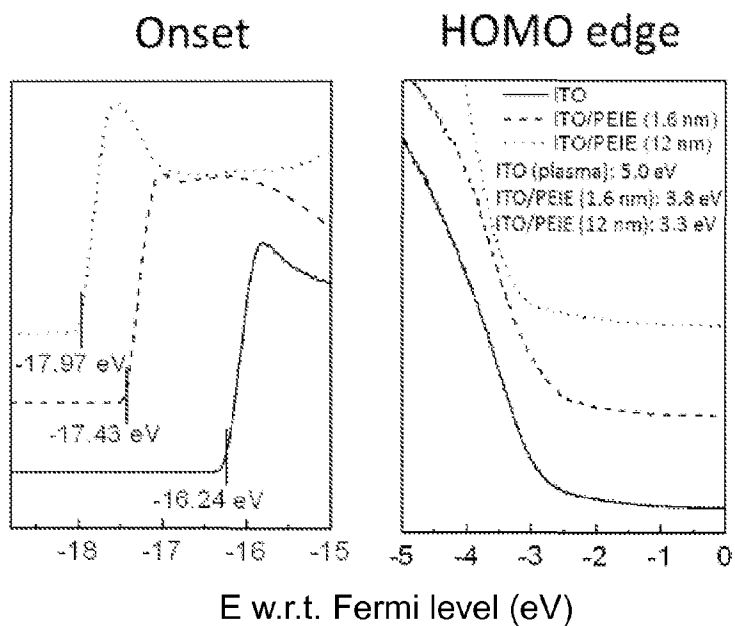


FIG. 6

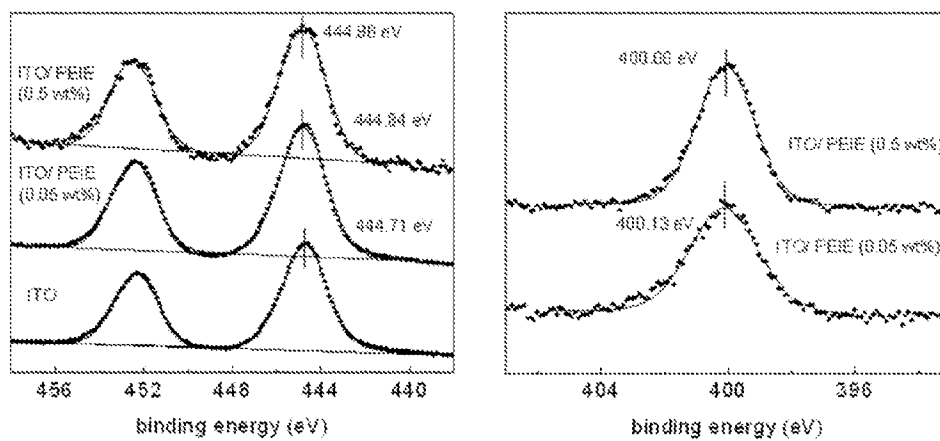


FIG. 7

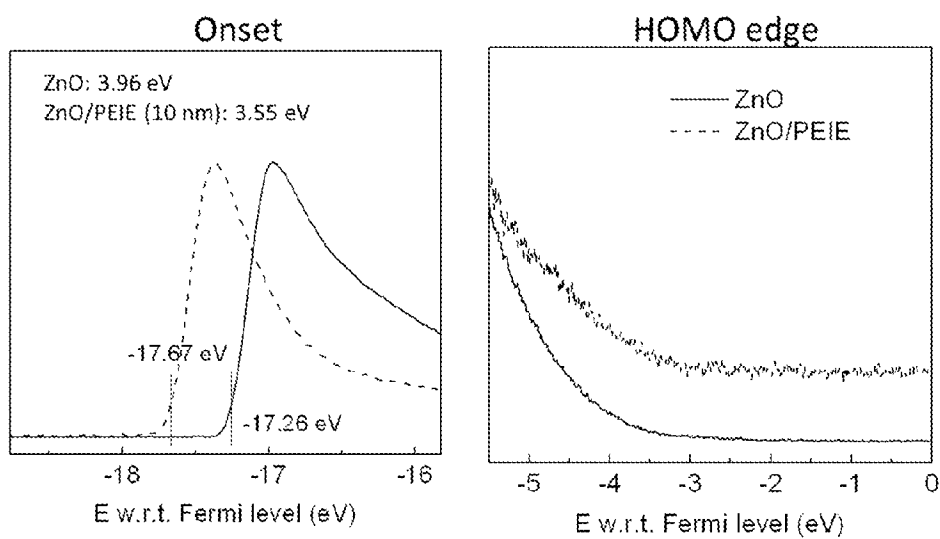


FIG. 8

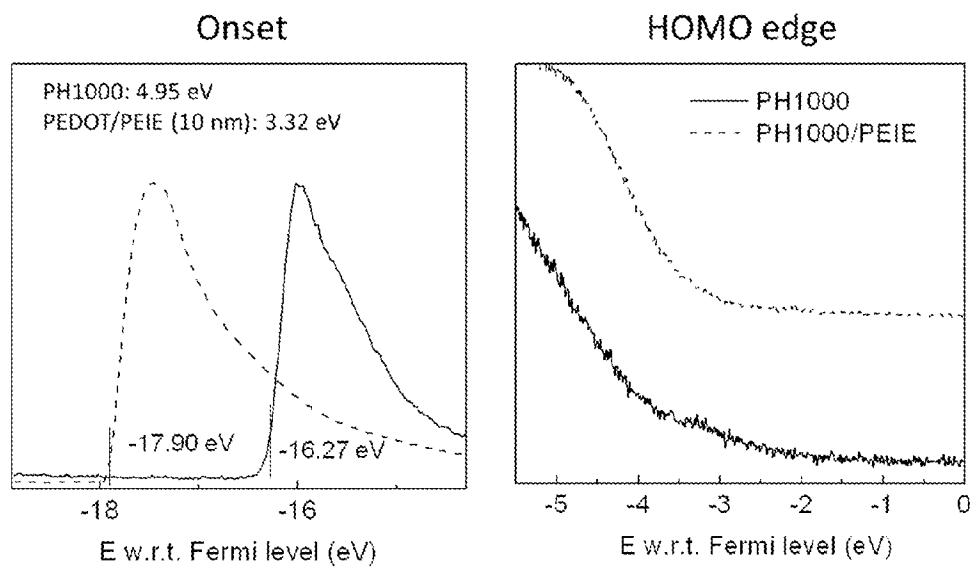


FIG. 9

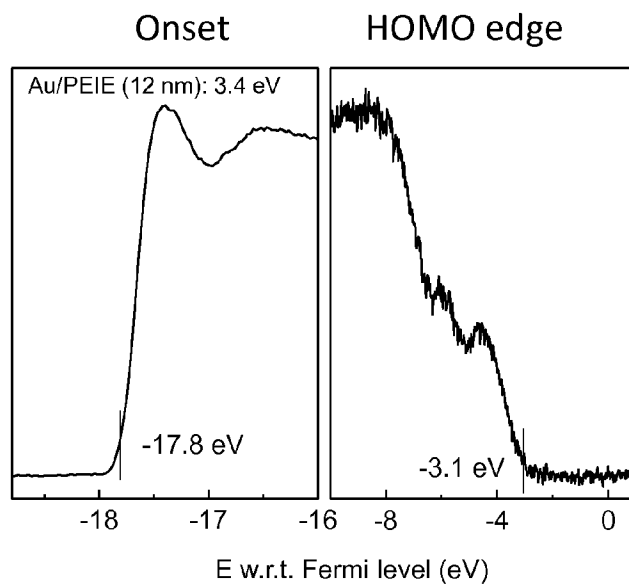


FIG. 10

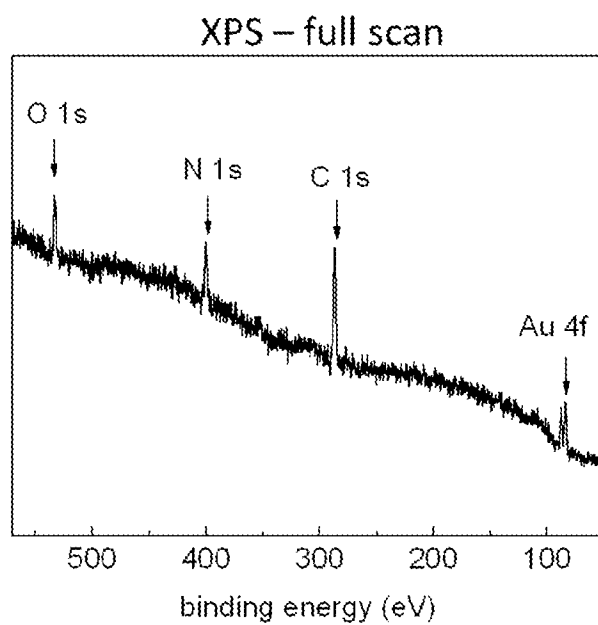


FIG. 11

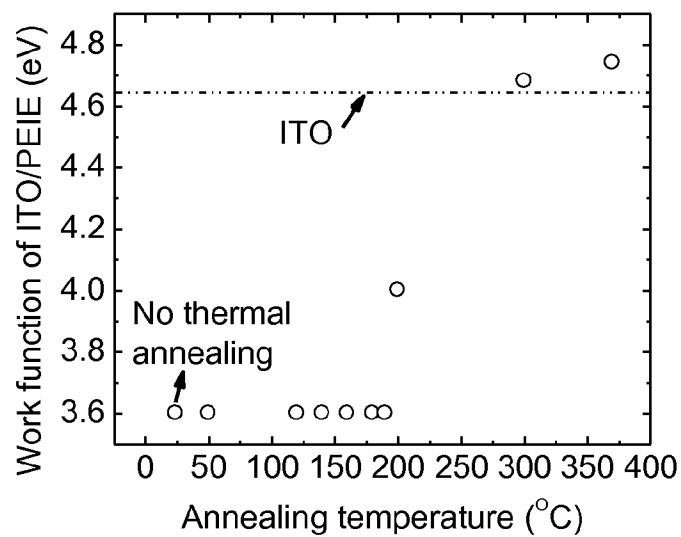
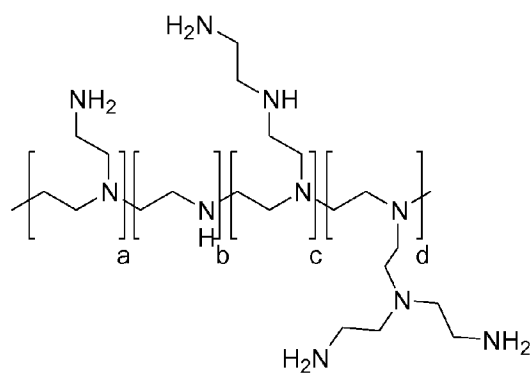


FIG. 12



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FIG. 13

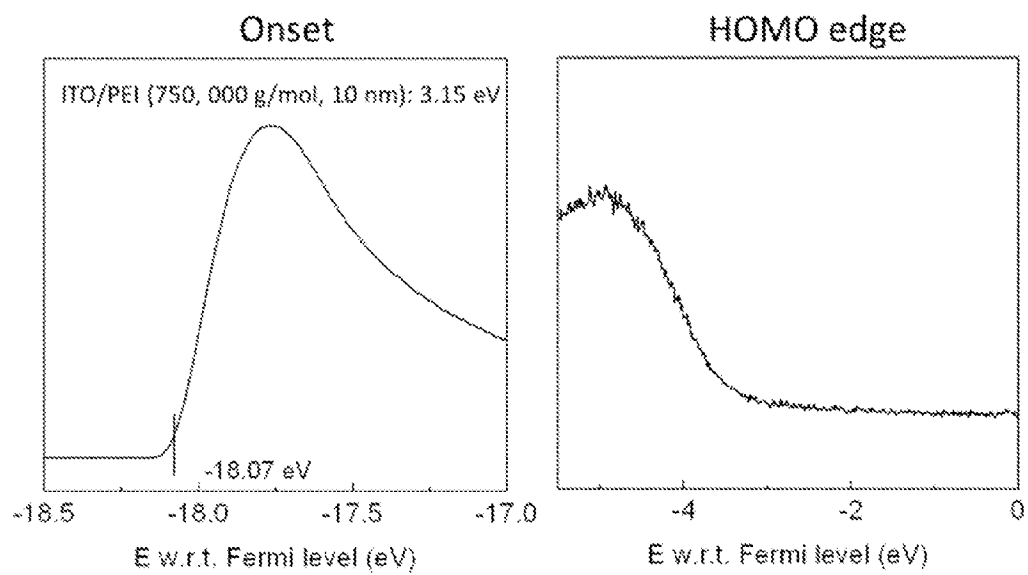


FIG. 14

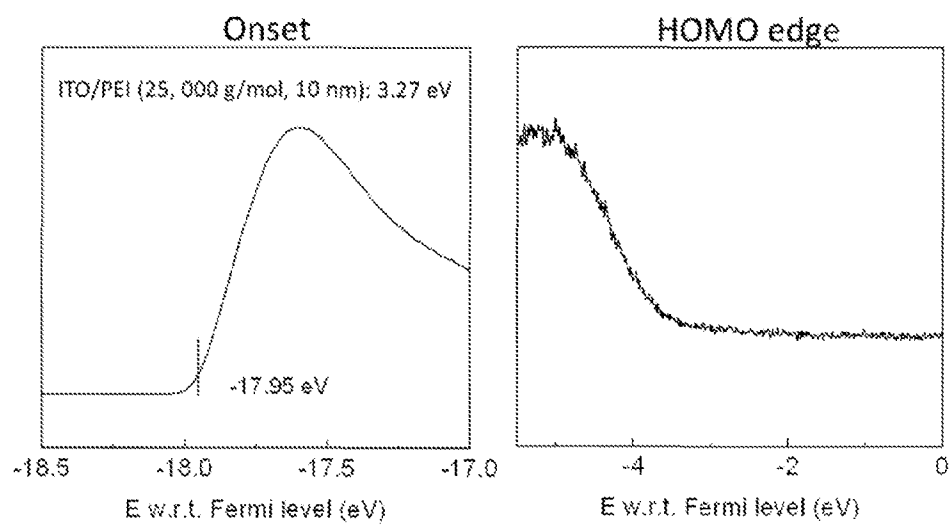


FIG. 15

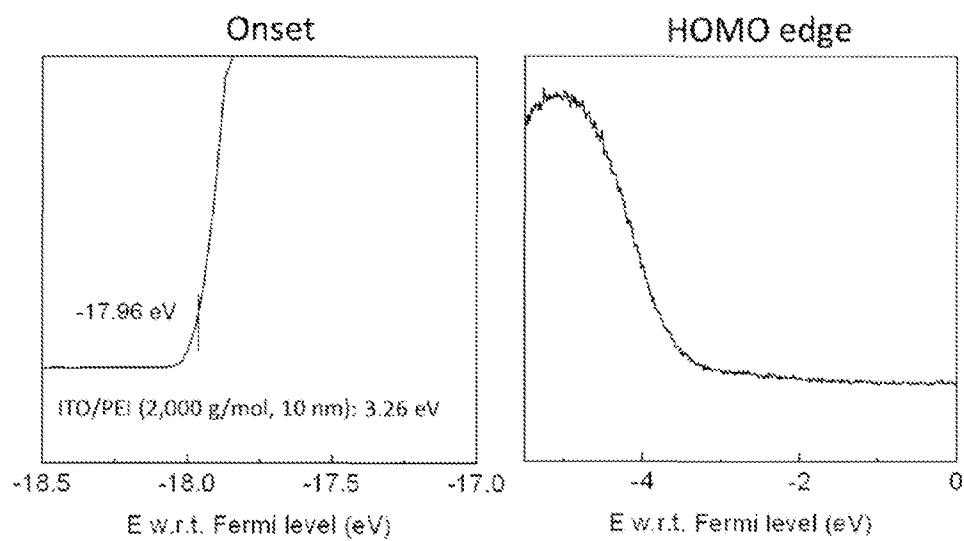


FIG. 16

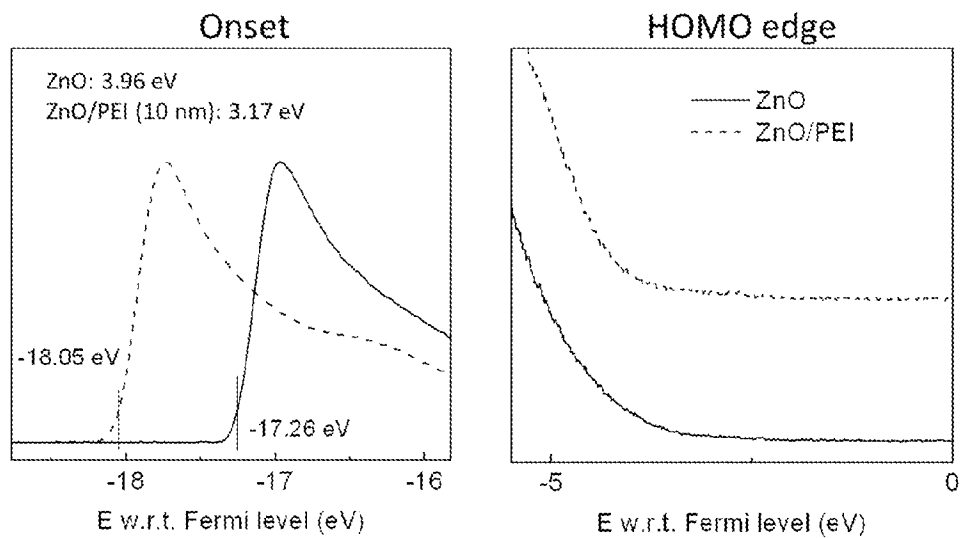


FIG. 17

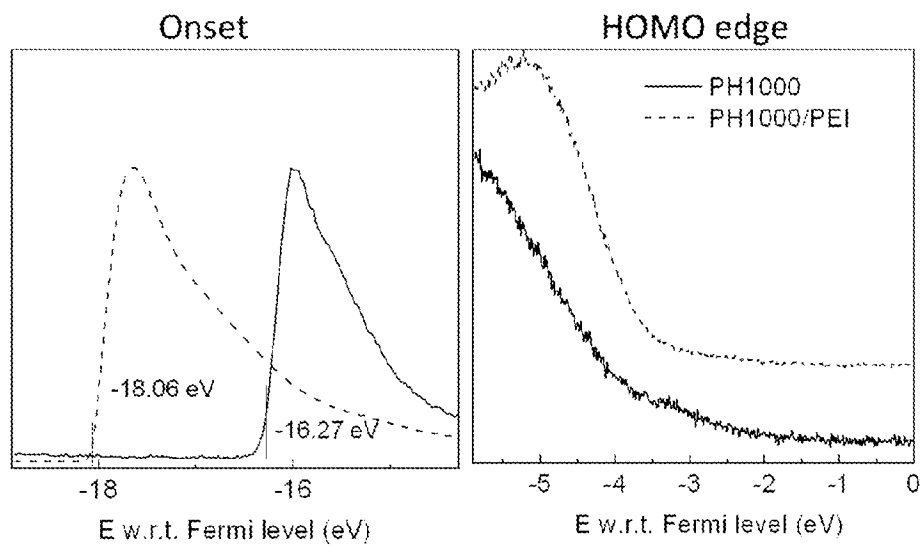


FIG. 18

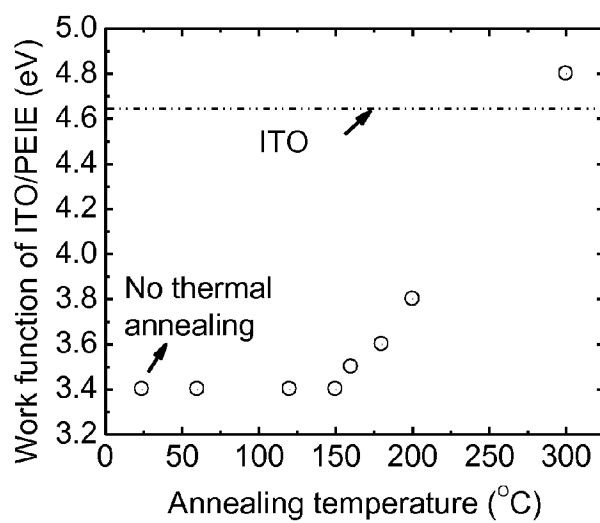


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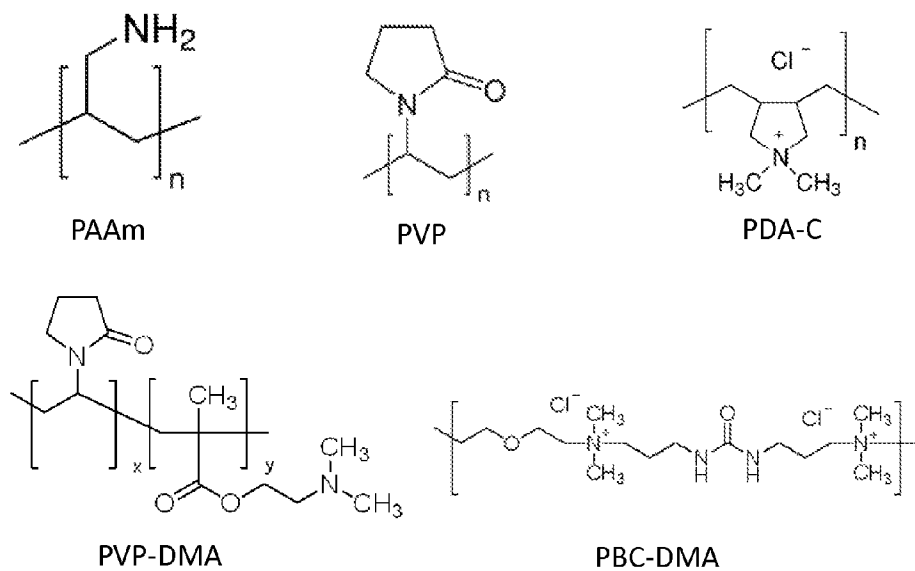


FIG. 20

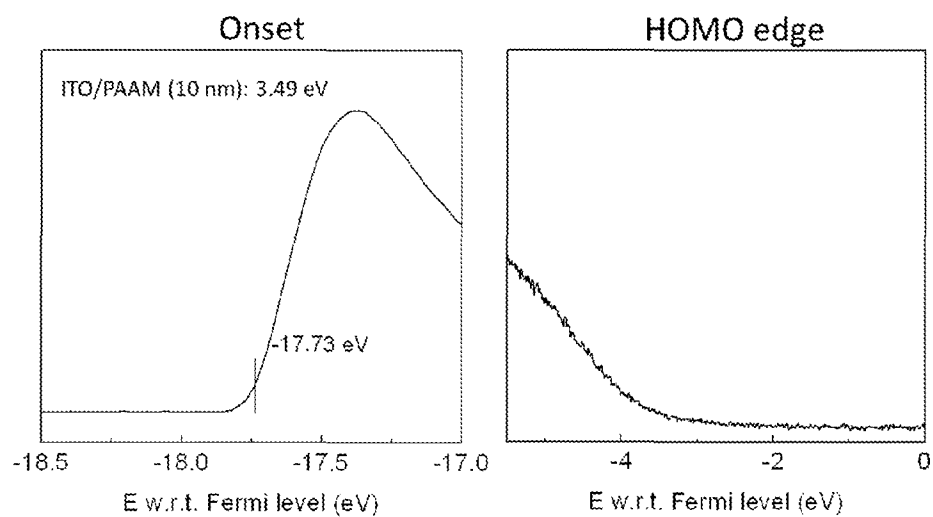


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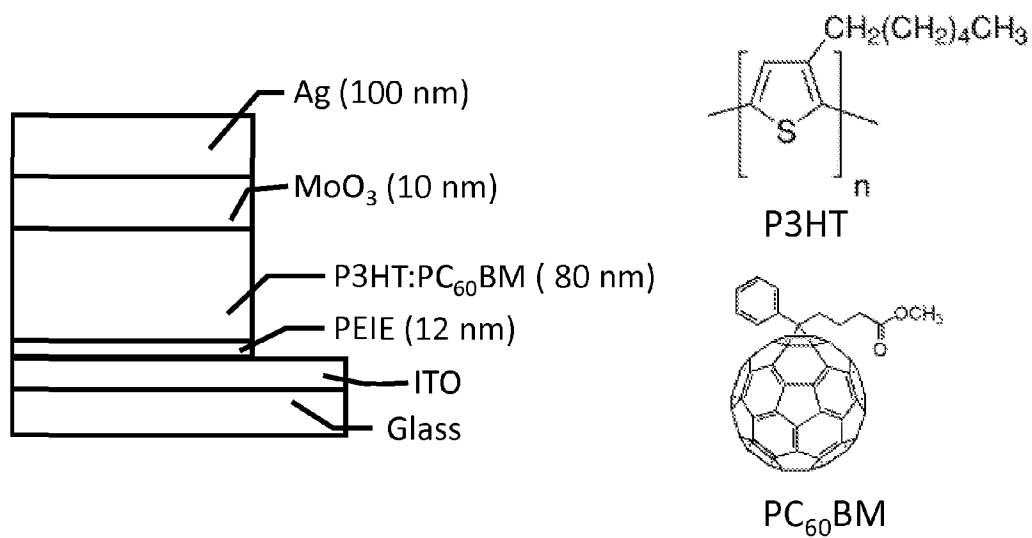


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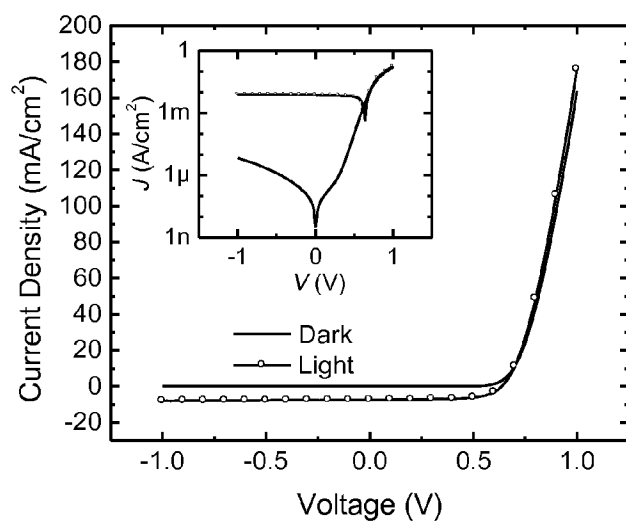


FIG. 23

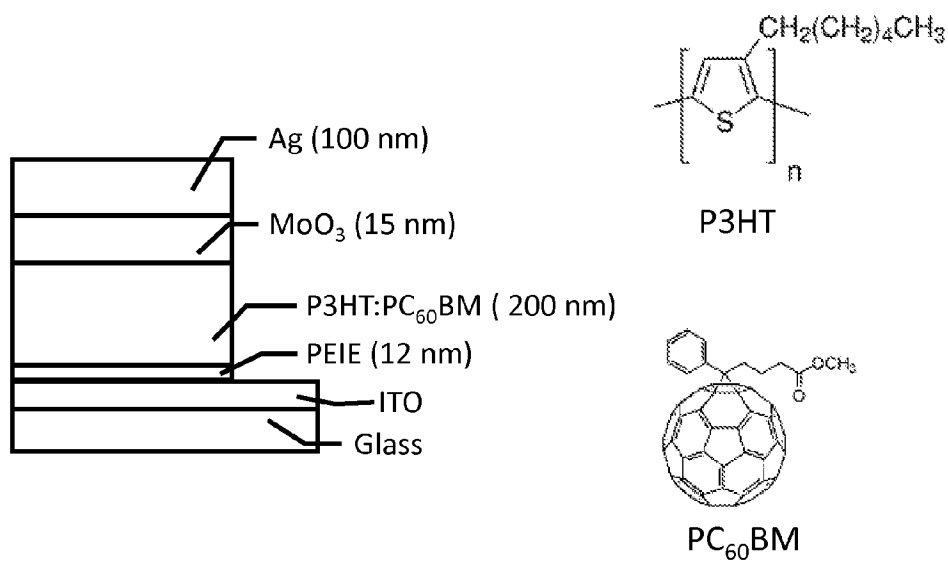


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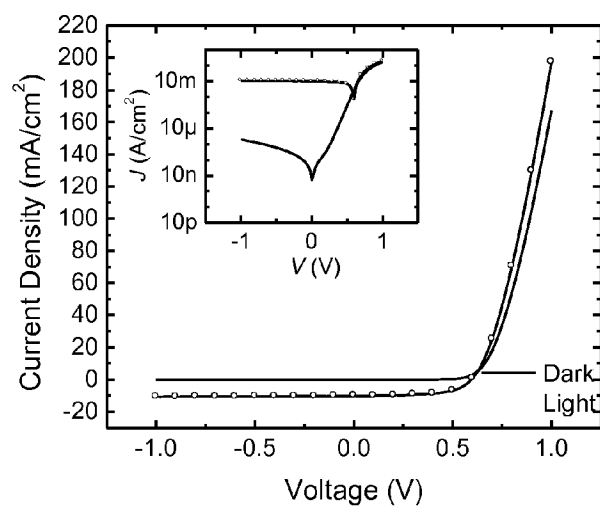


FIG. 25

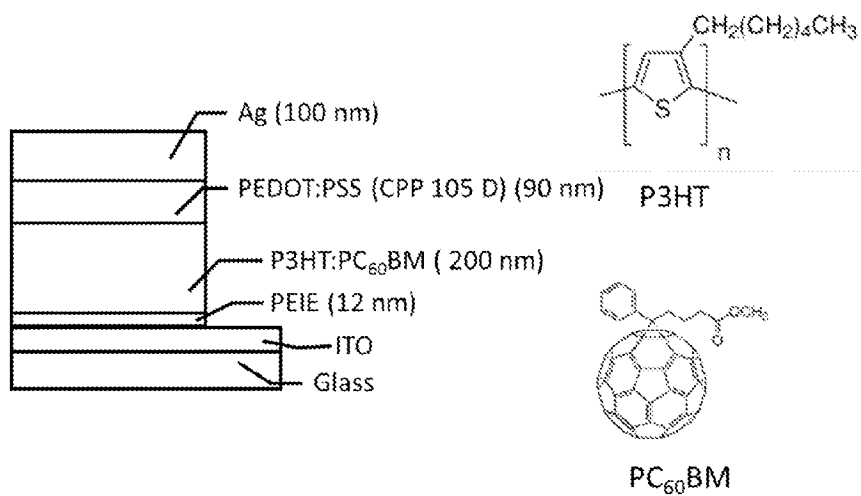


FIG. 26

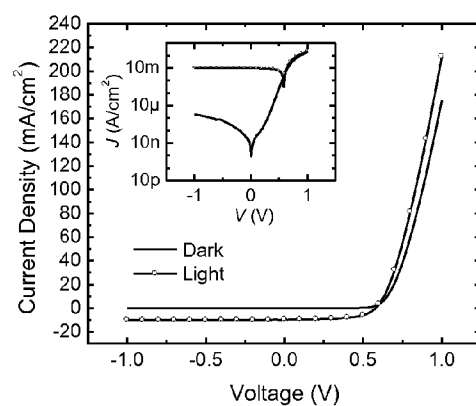


FIG. 27

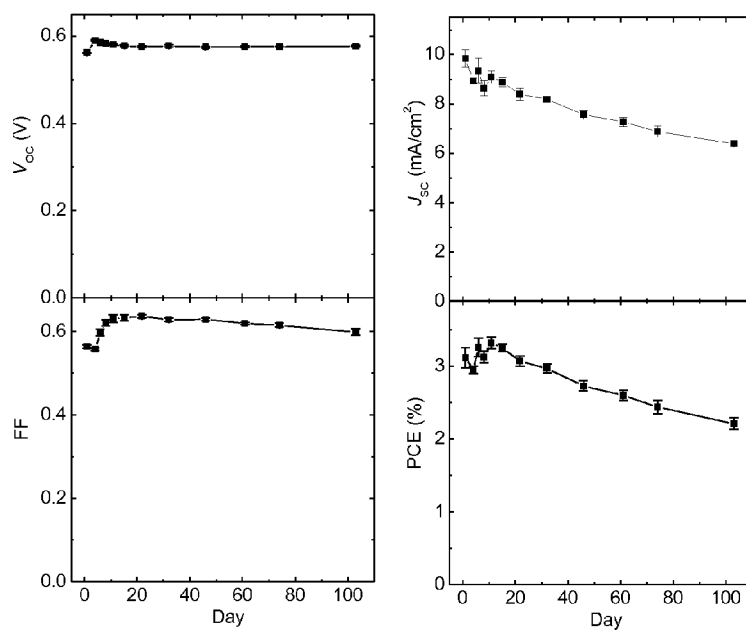


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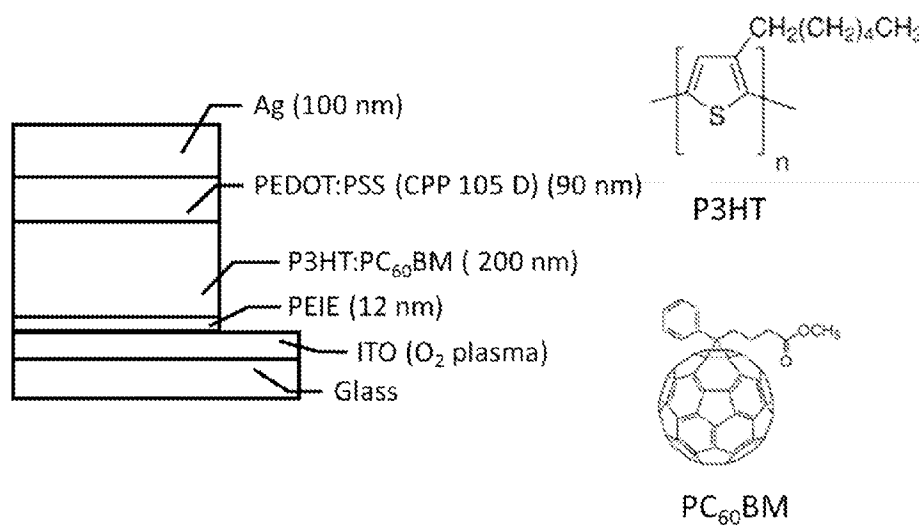


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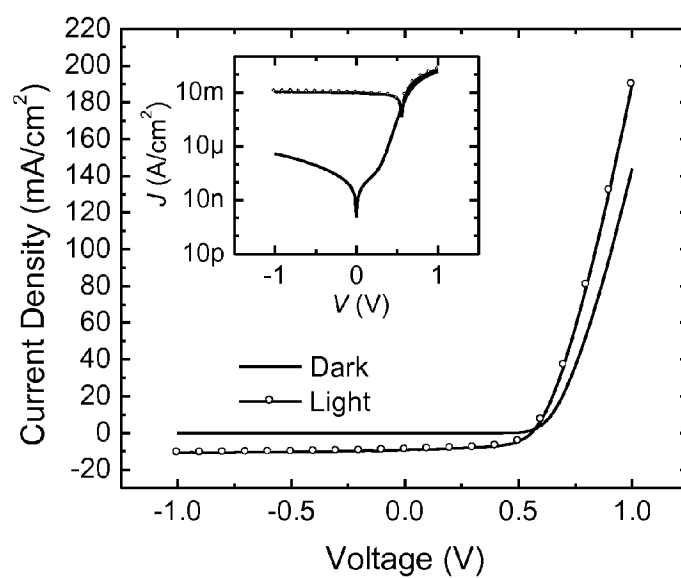


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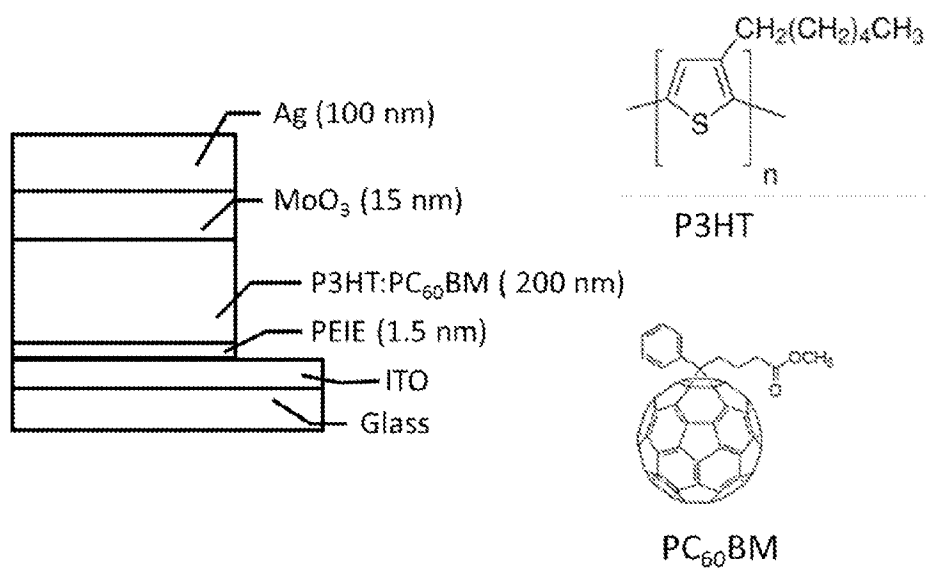


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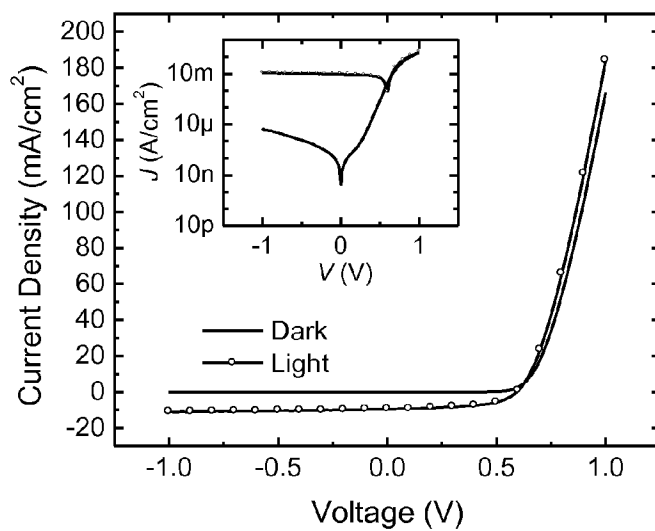


FIG. 32

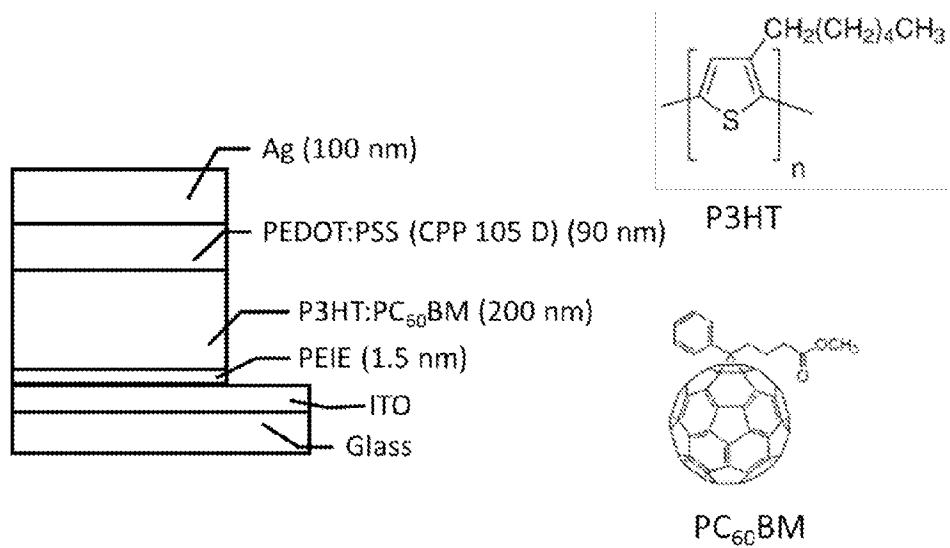


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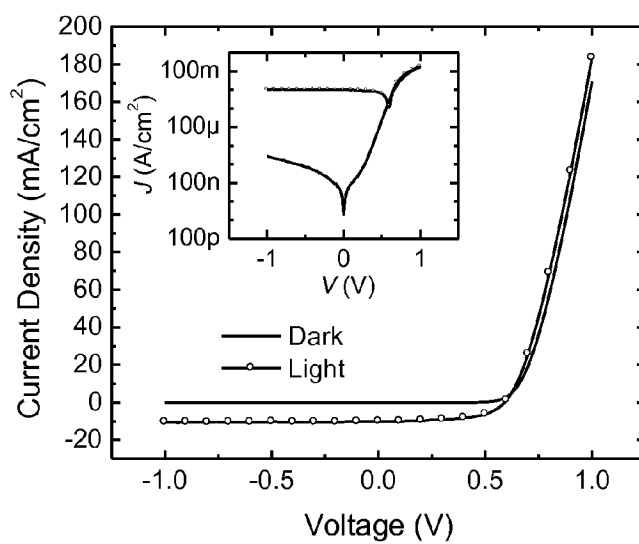


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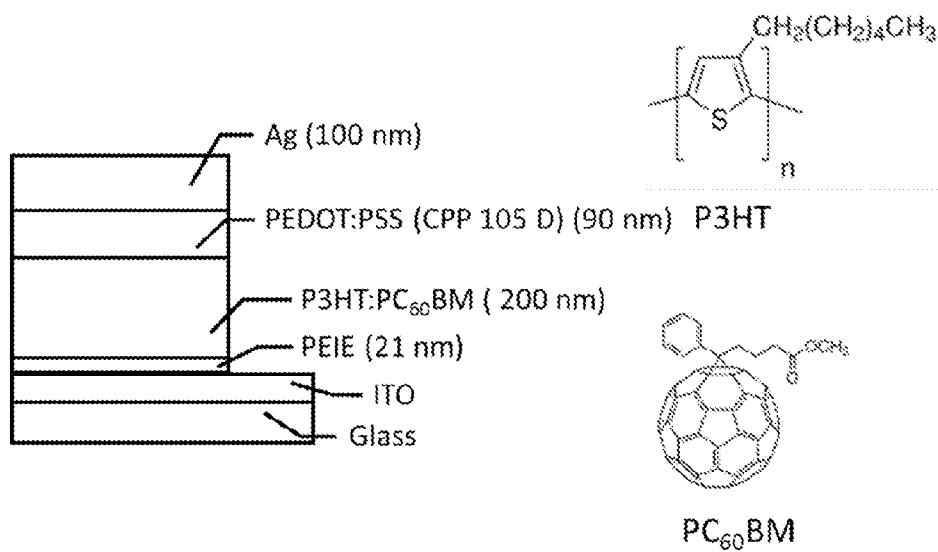


FIG. 35

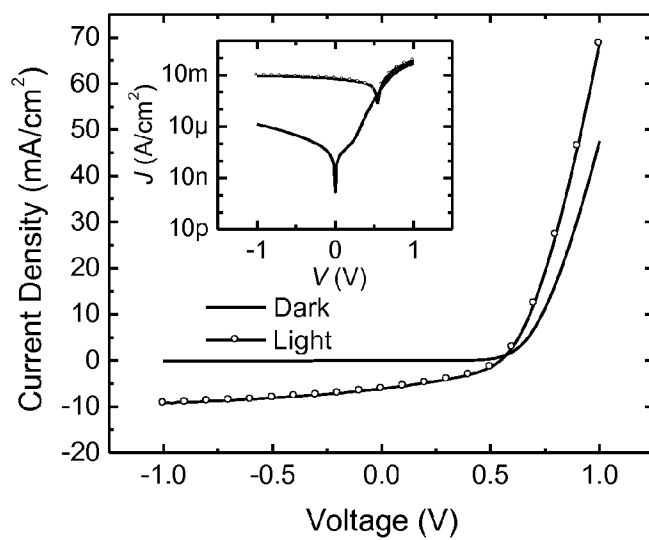


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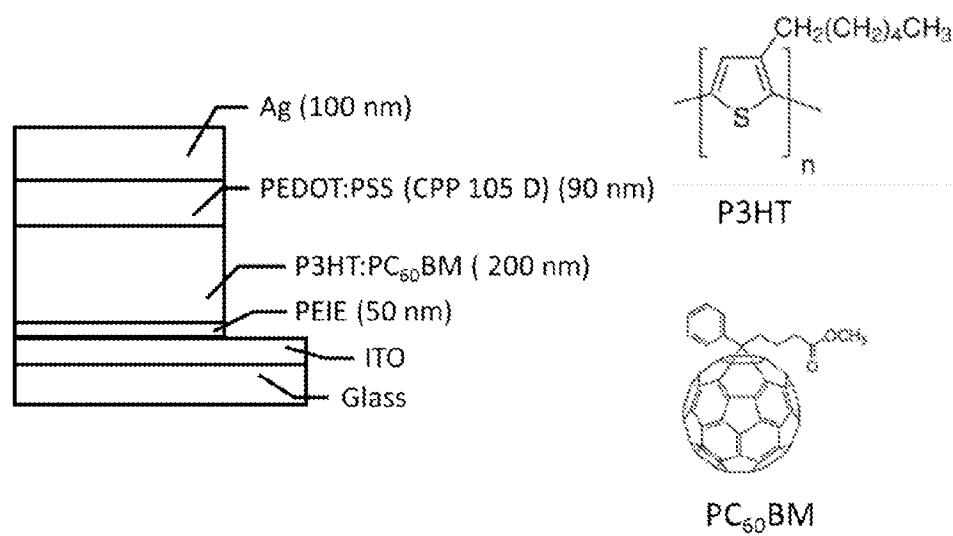


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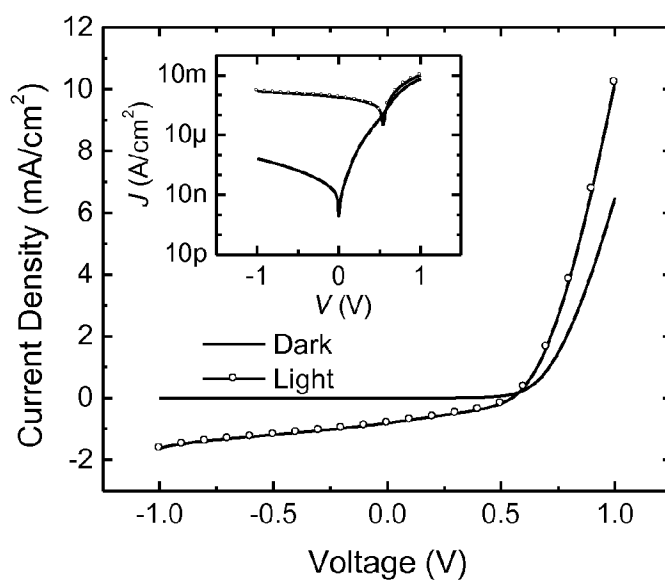


FIG. 38

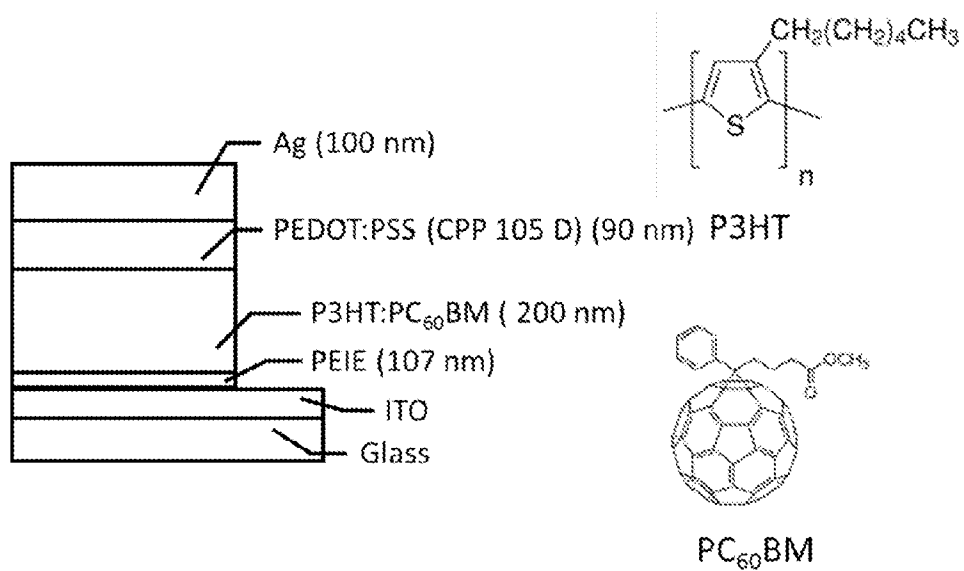


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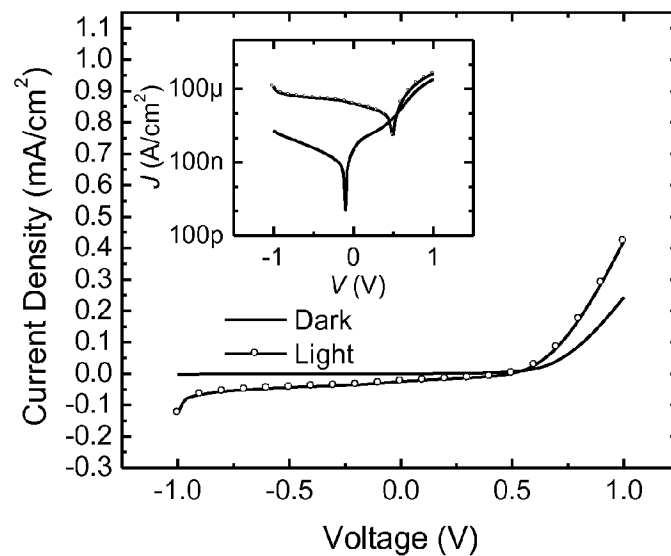


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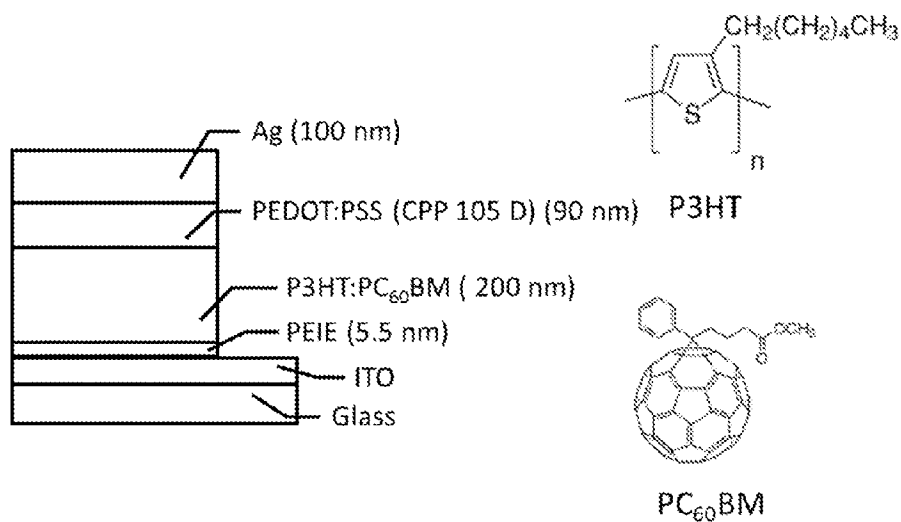


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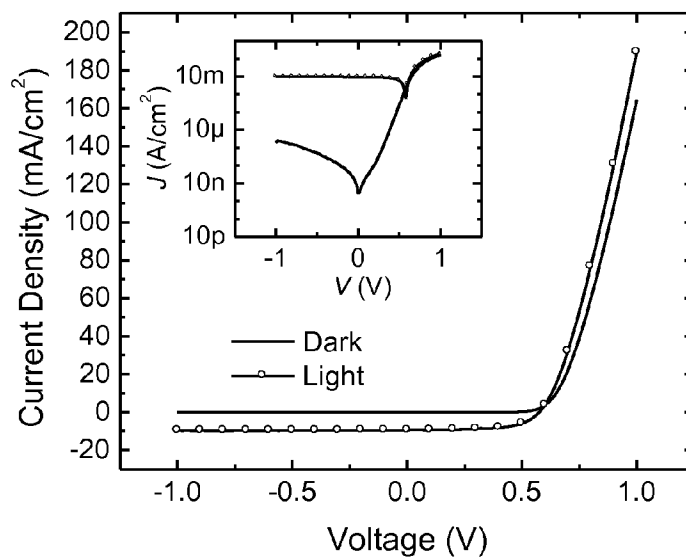


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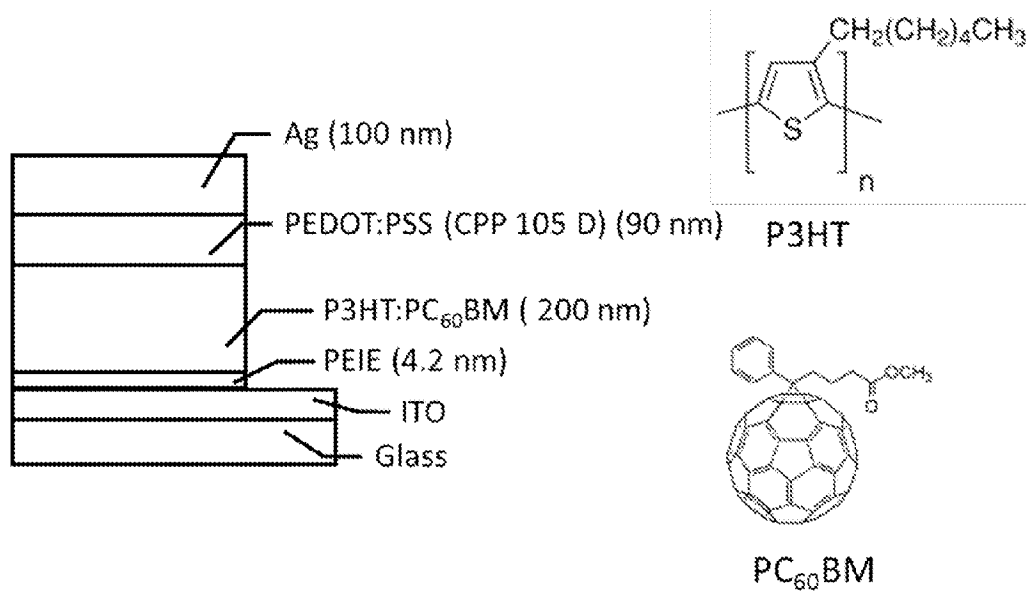


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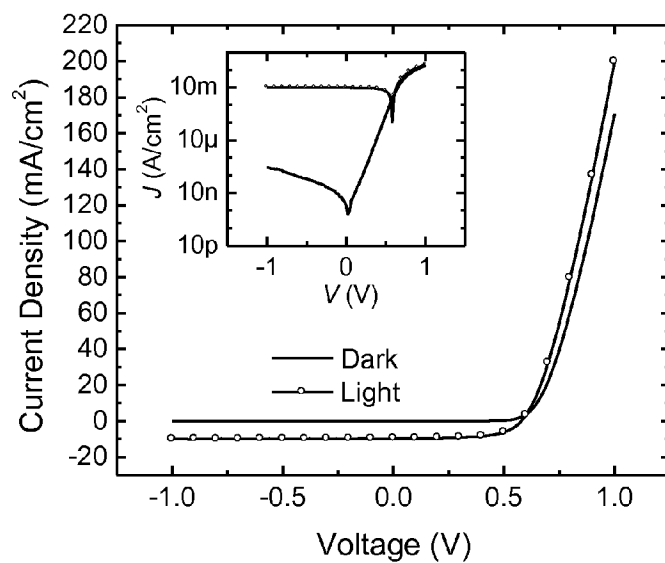


FIG. 44

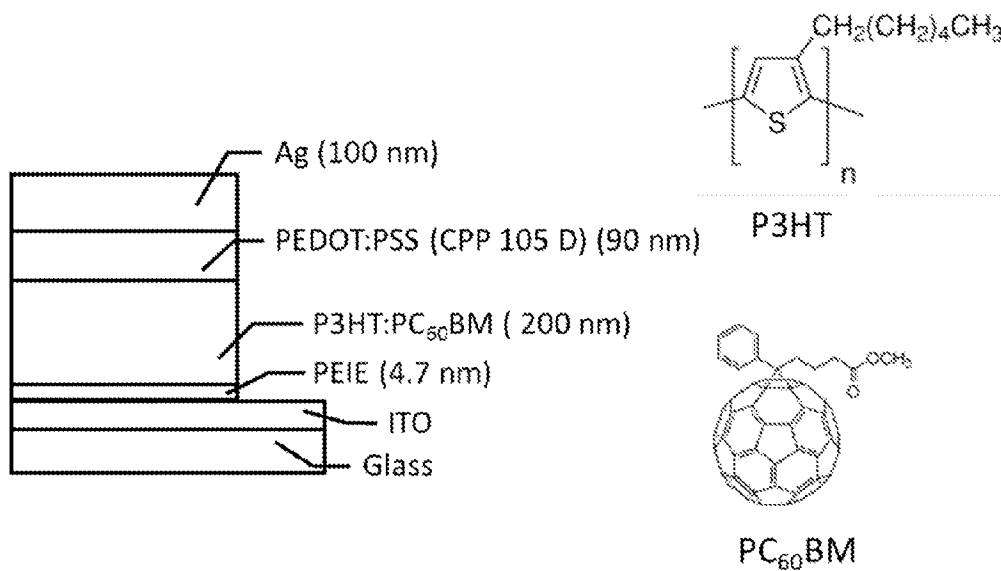


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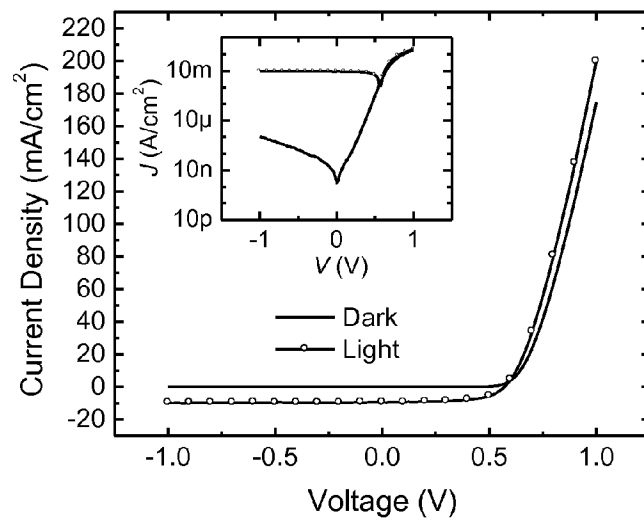


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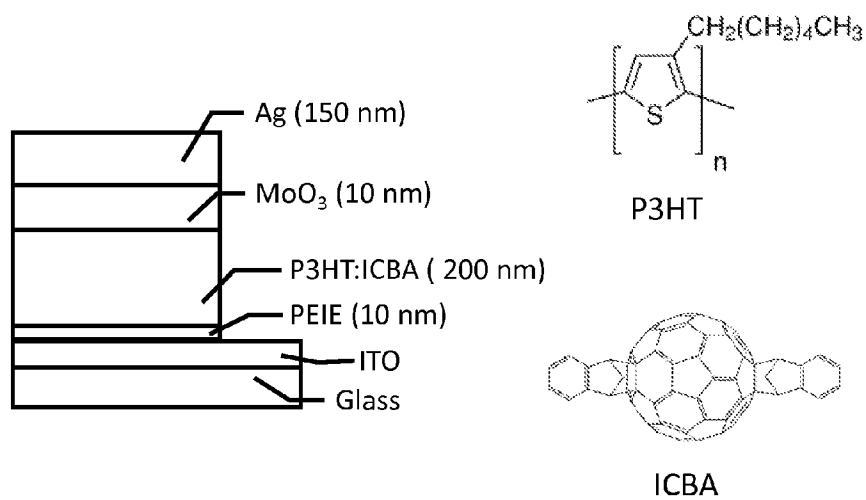


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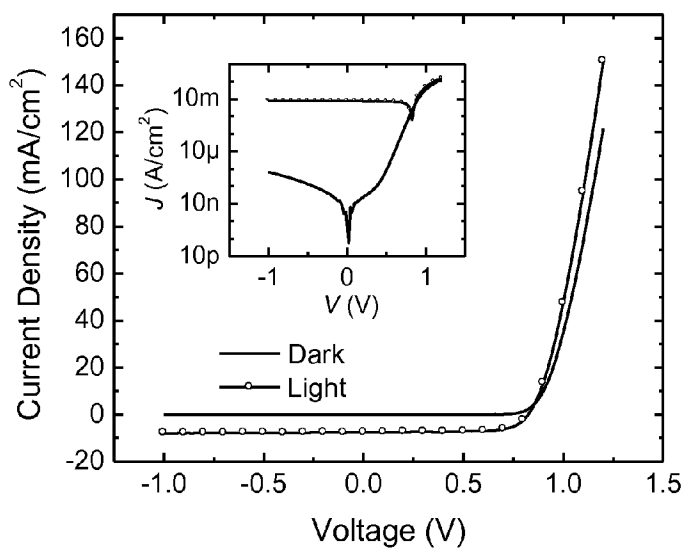


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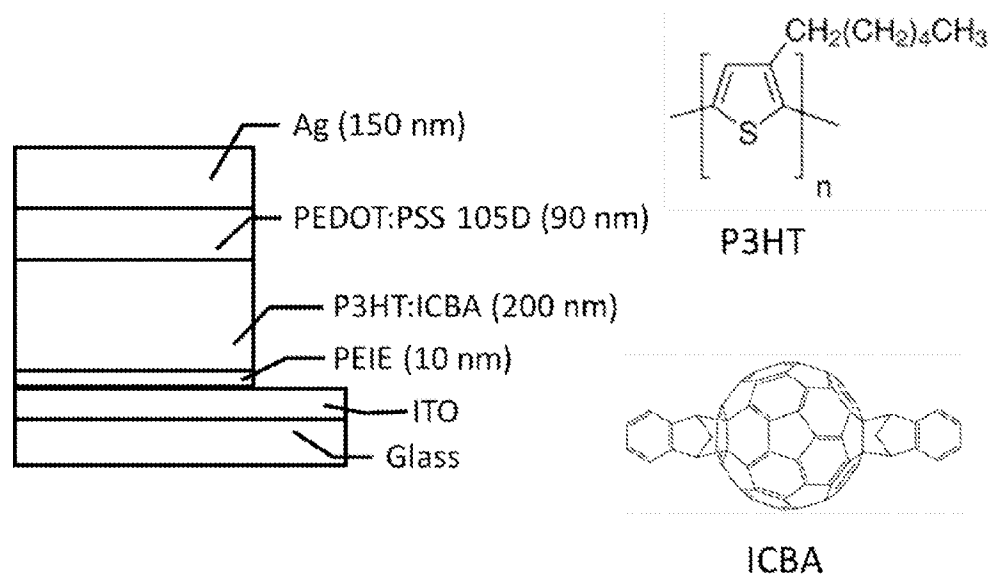


FIG. 49

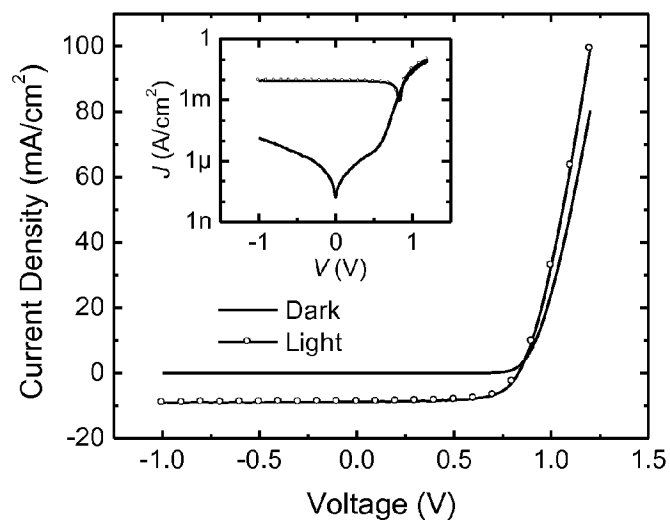


FIG. 50

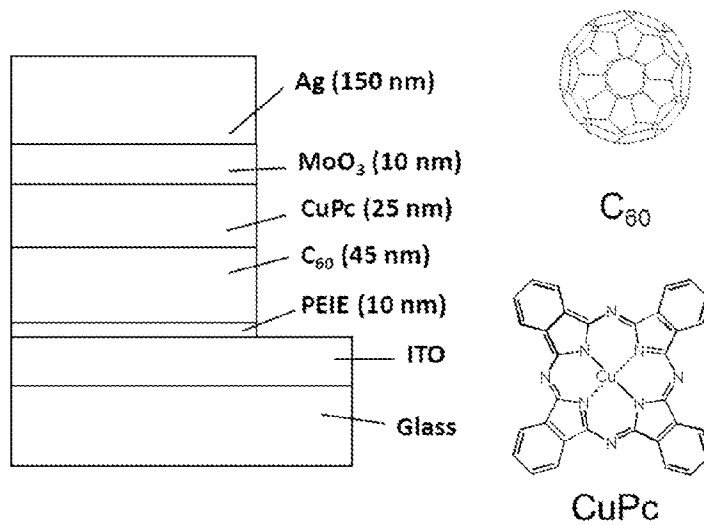


FIG. 51

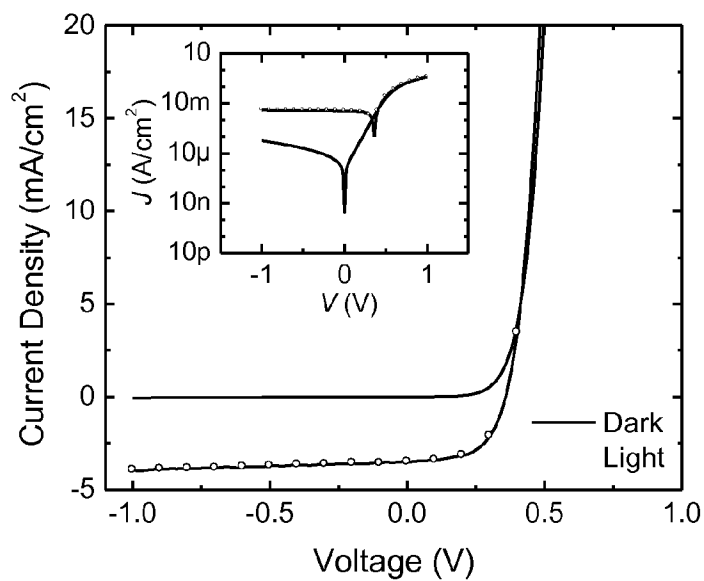


FIG. 52

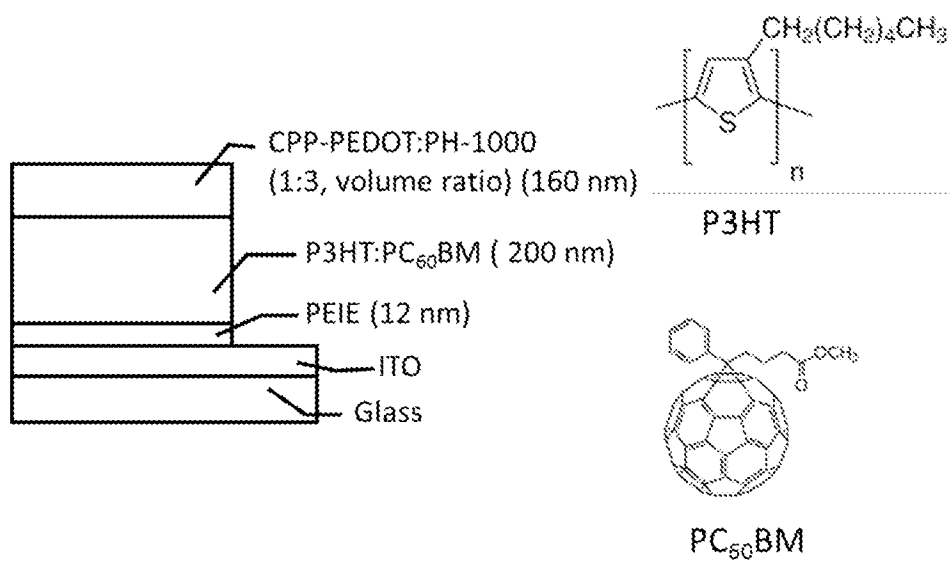


FIG. 53

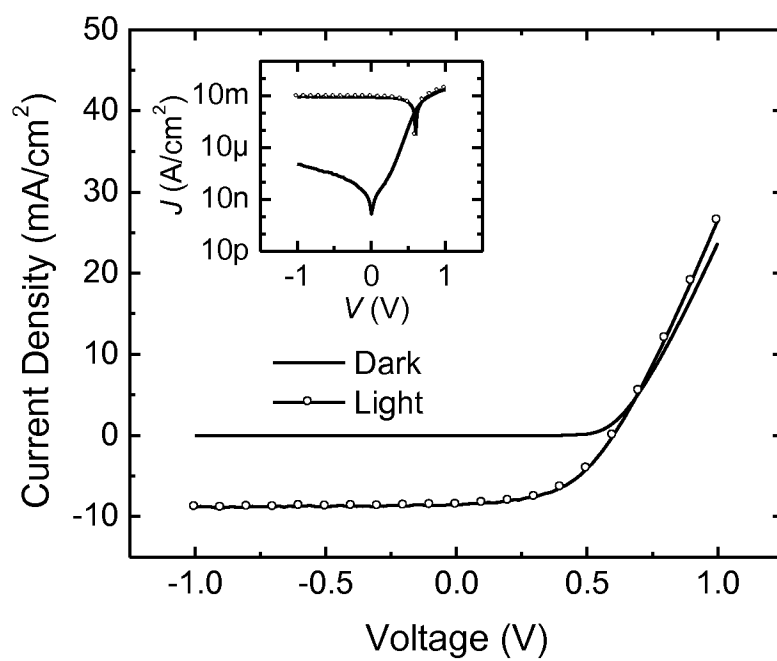


FIG. 54

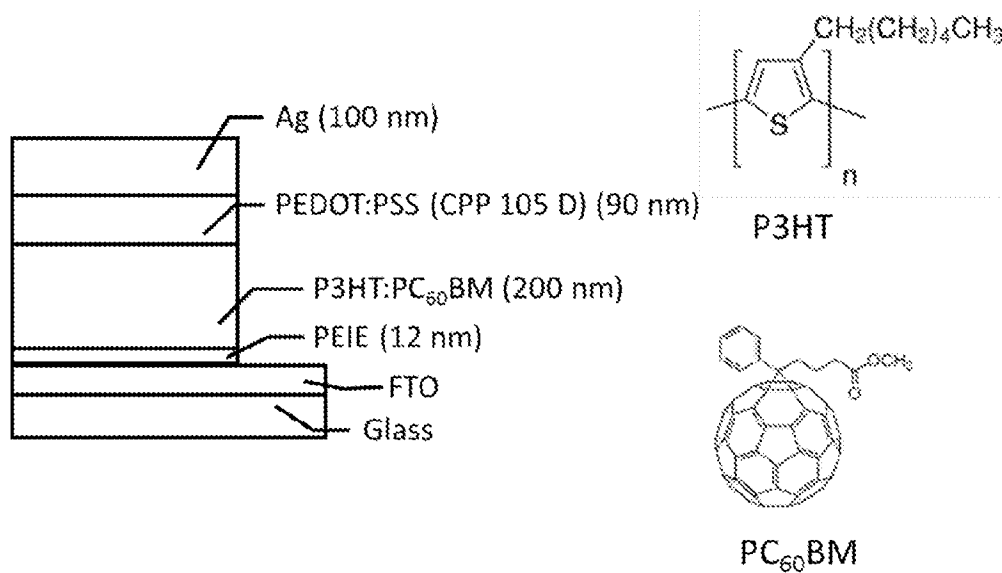


FIG. 55

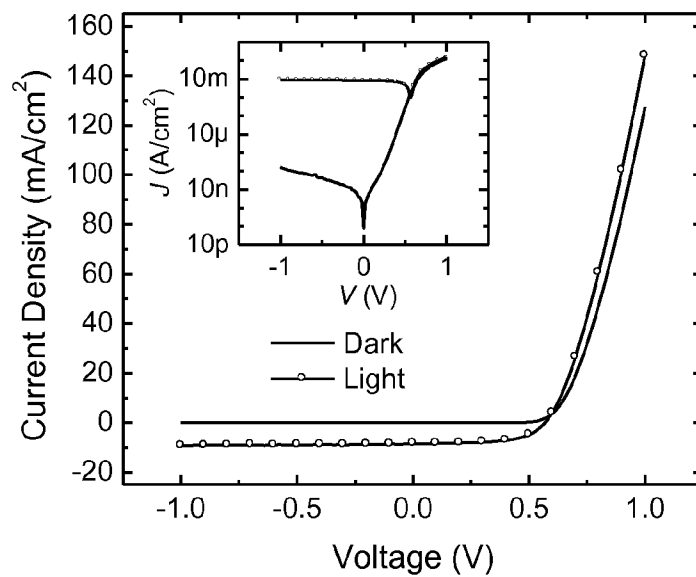


FIG. 56

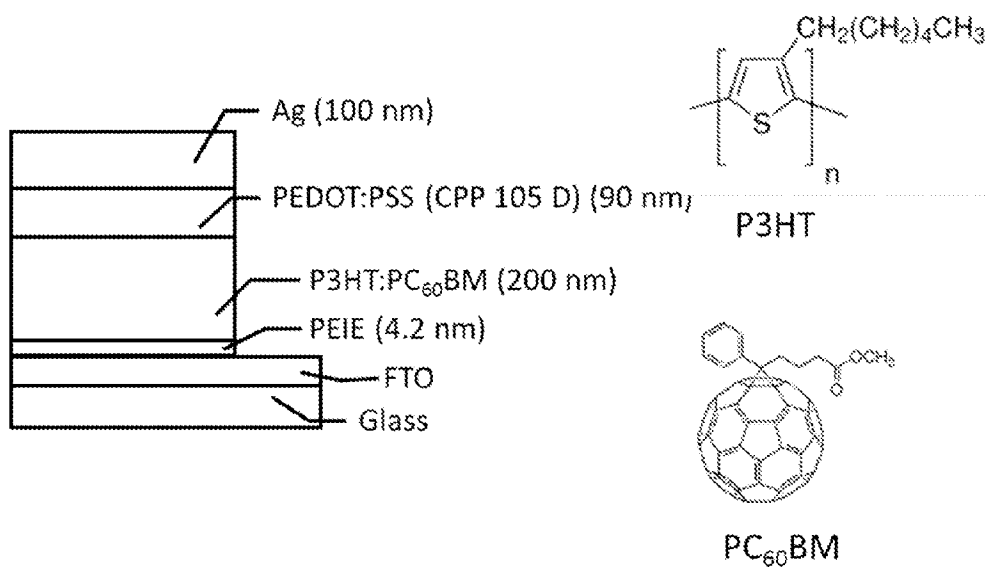


FIG. 57

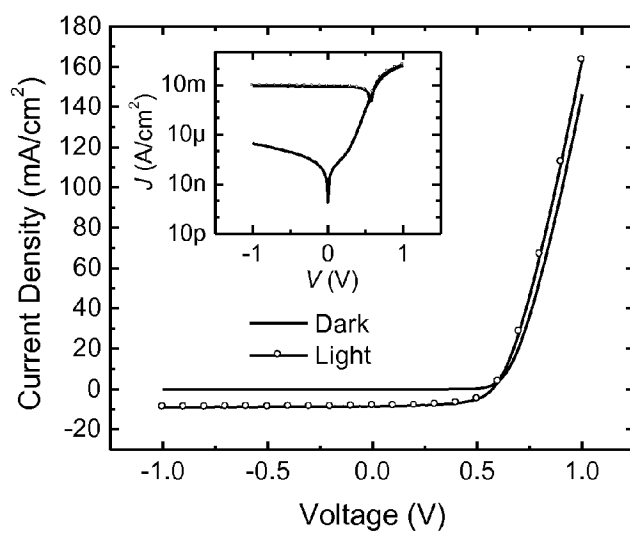


FIG. 58

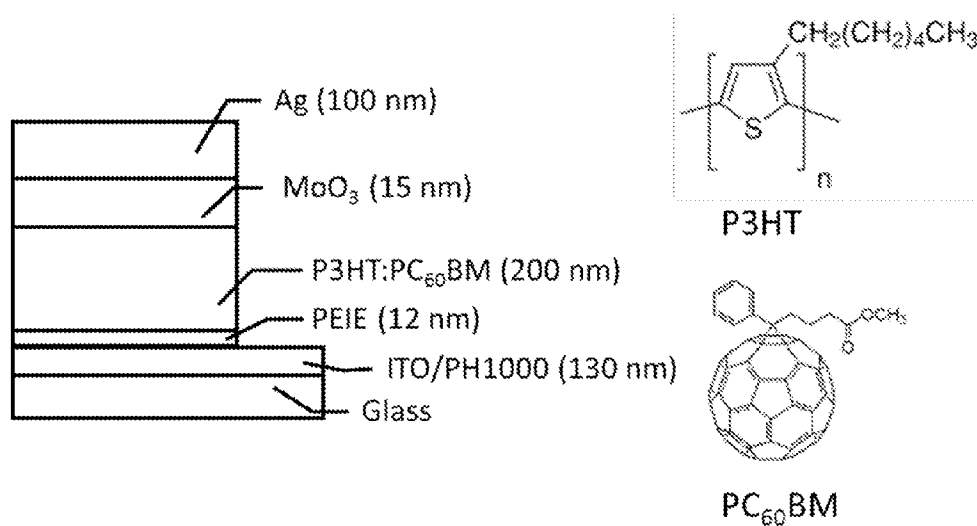


FIG. 59

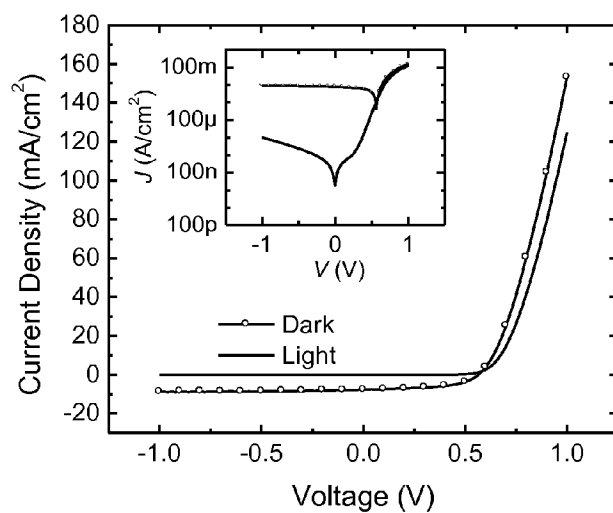


FIG. 60

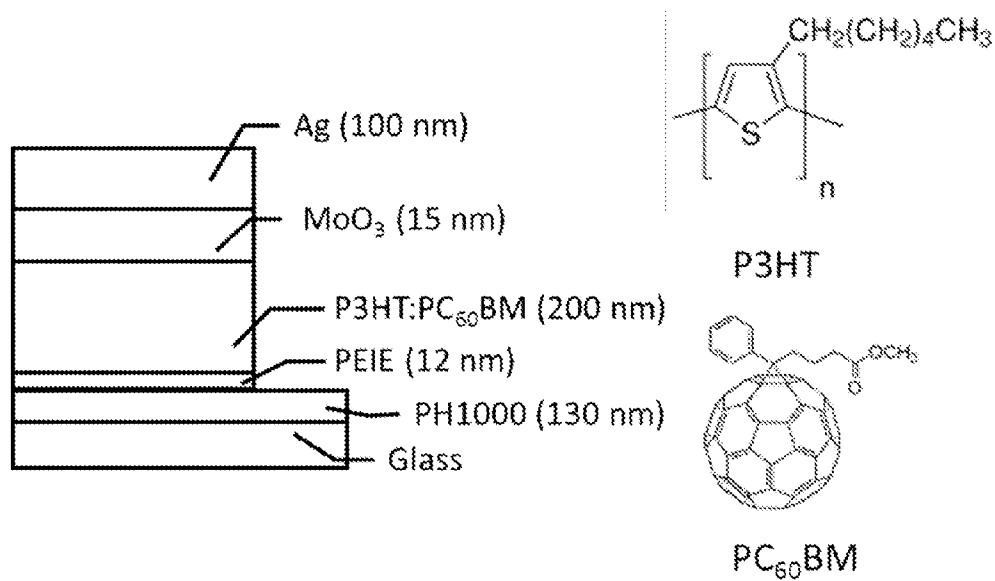


FIG. 61

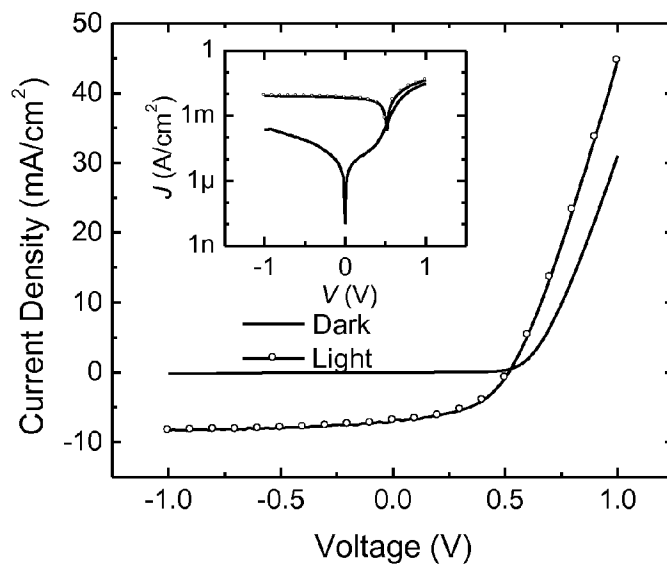


FIG. 62

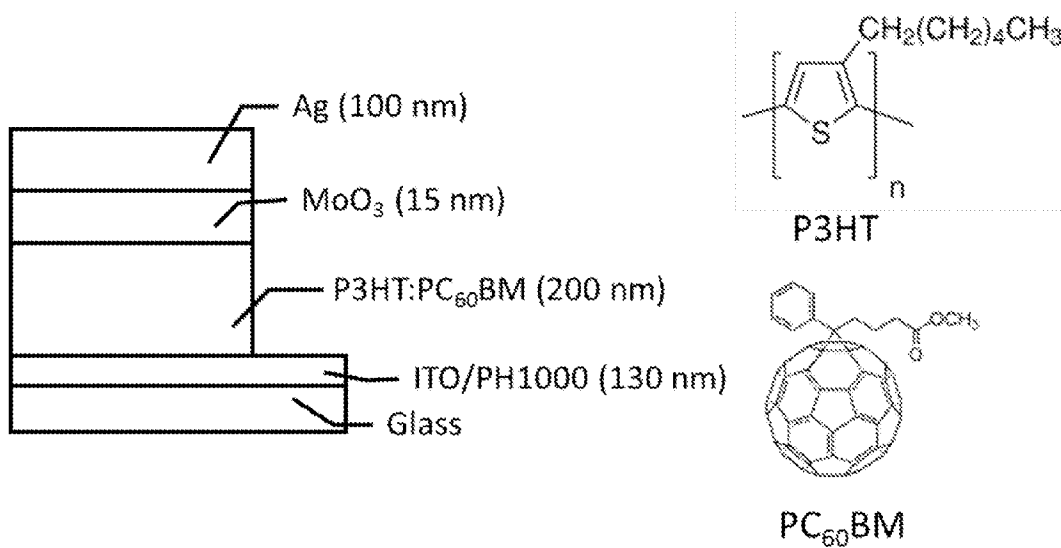


FIG. 63

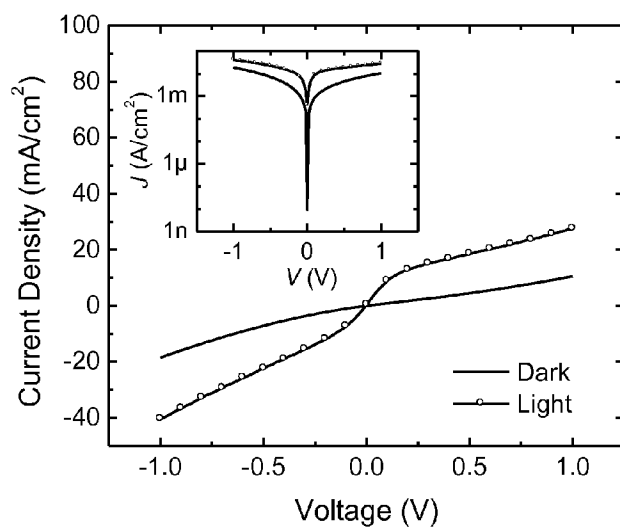


FIG. 64

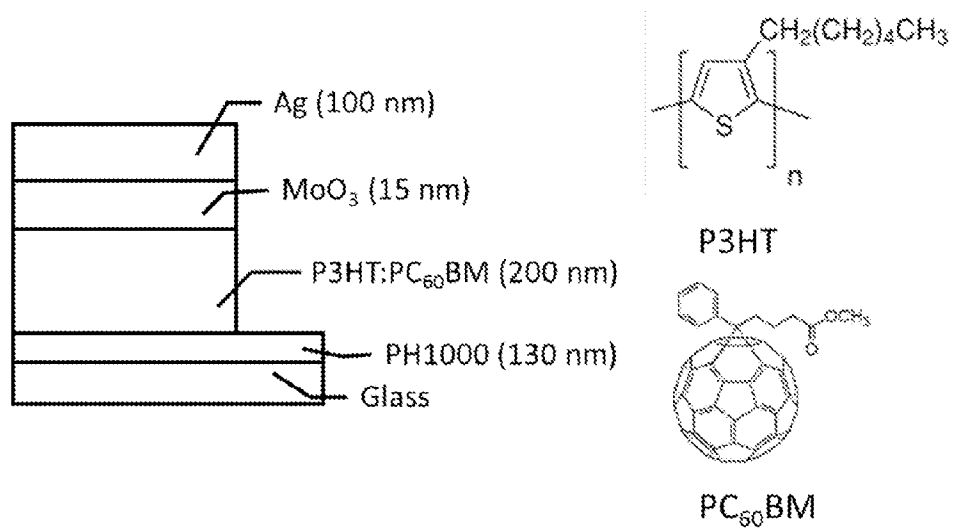


FIG. 65

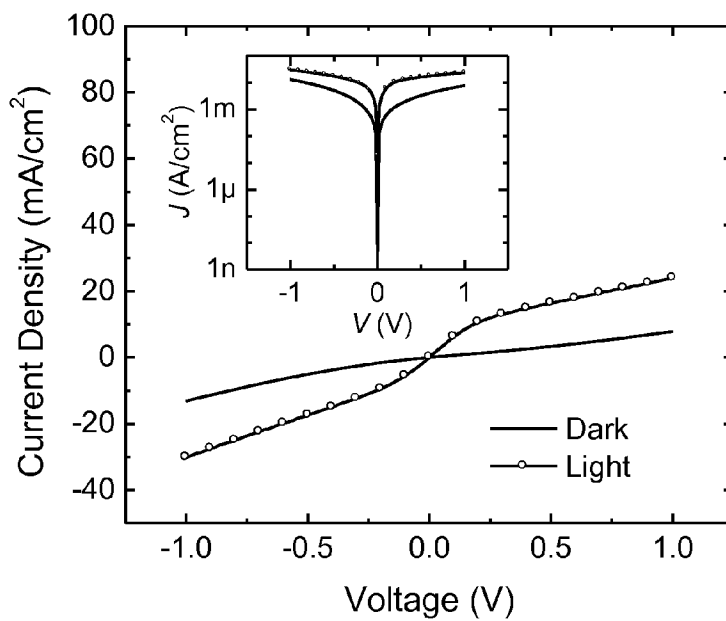


FIG. 66

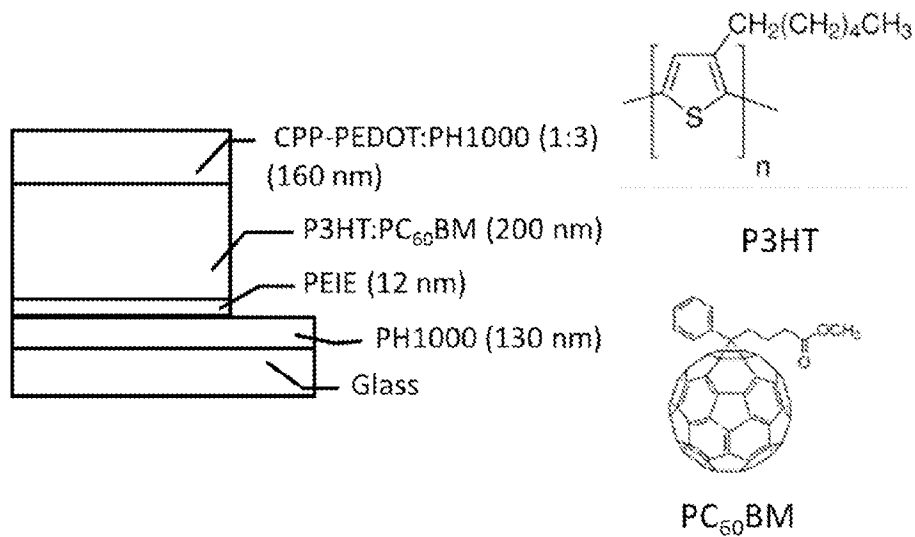


FIG. 67

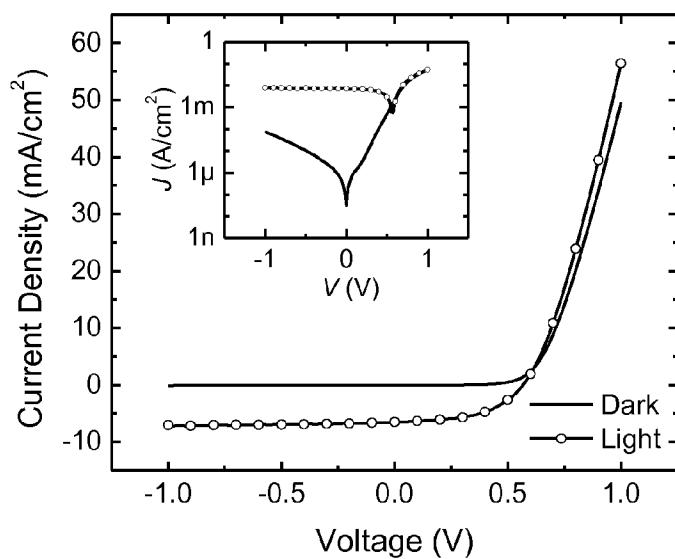


FIG. 68

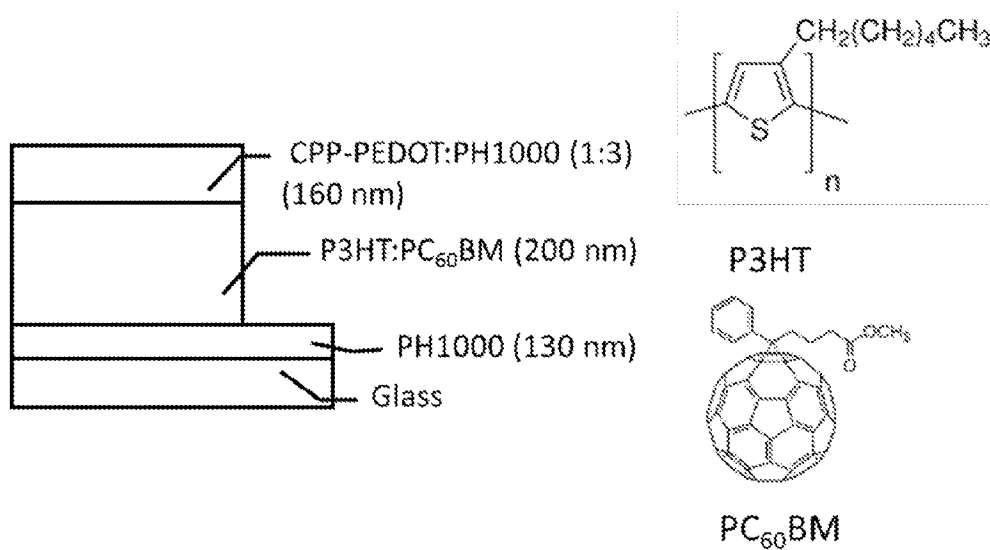


FIG. 69

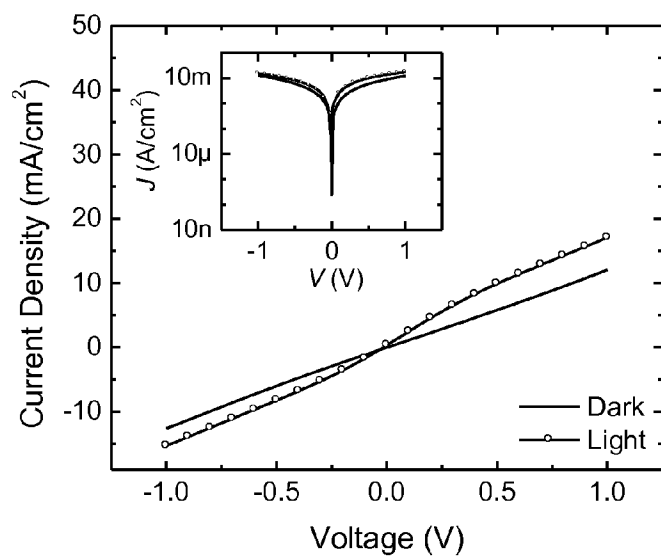


FIG. 70

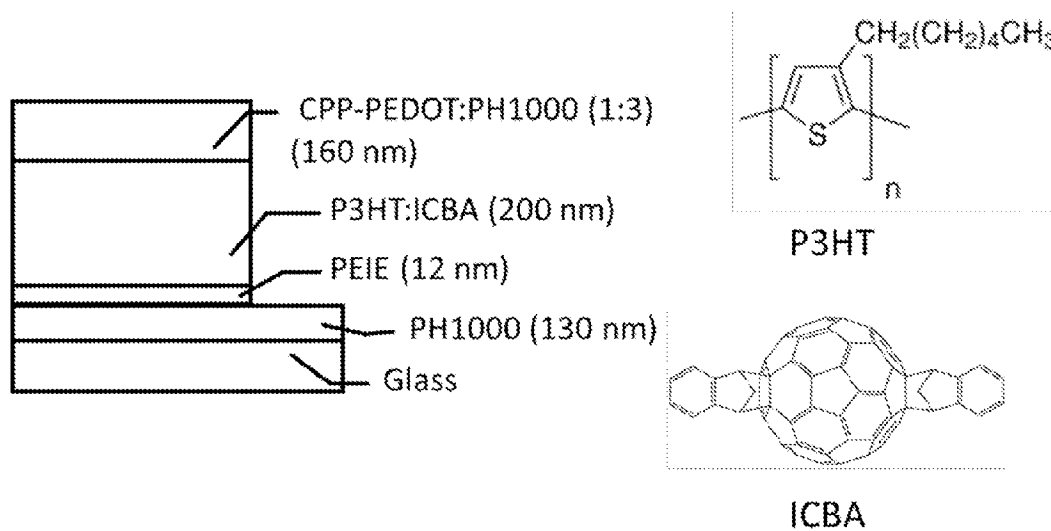


FIG. 71

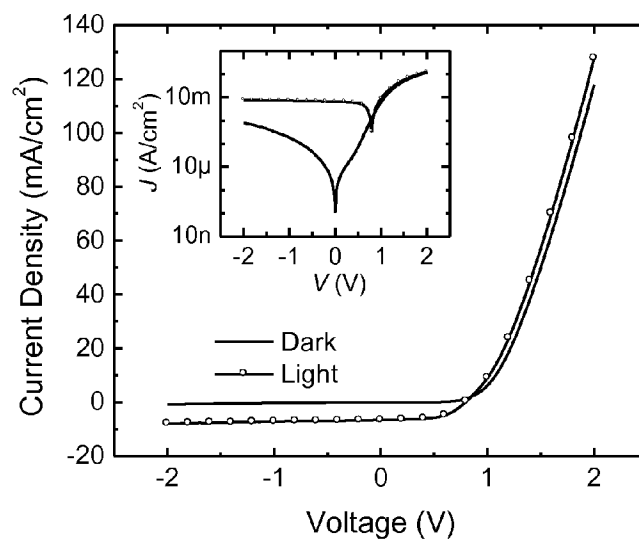


FIG. 72

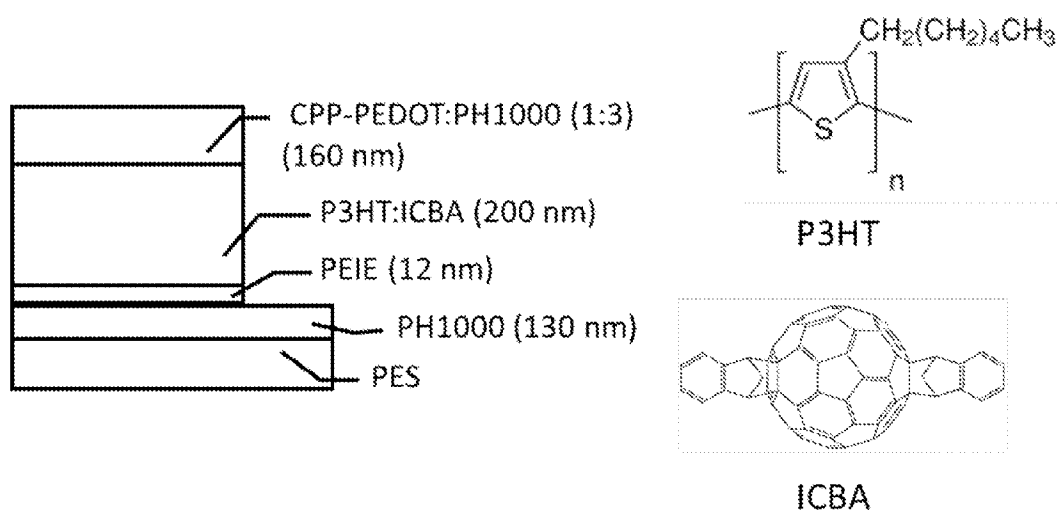


FIG. 73

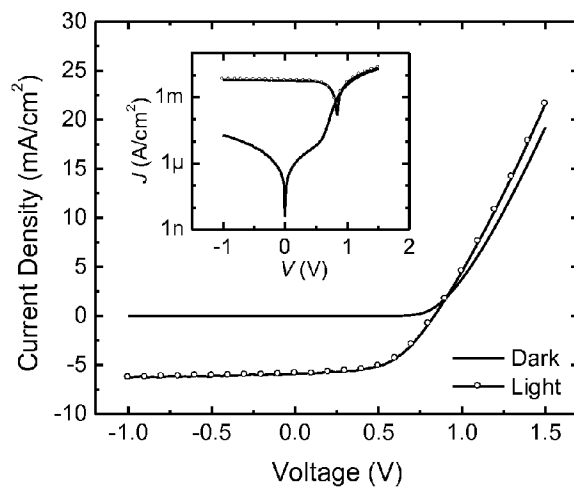


FIG. 74

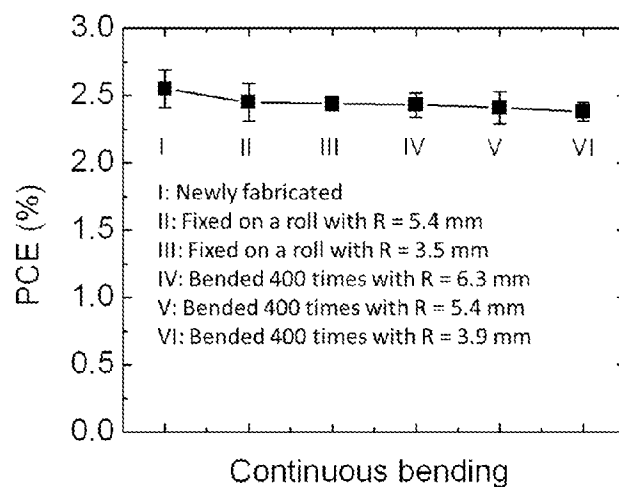


FIG. 75

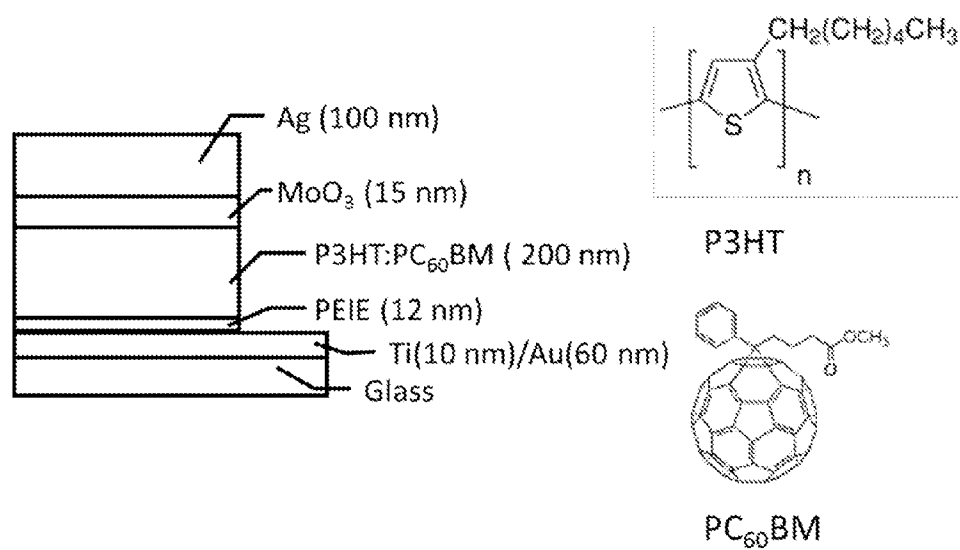


FIG. 76

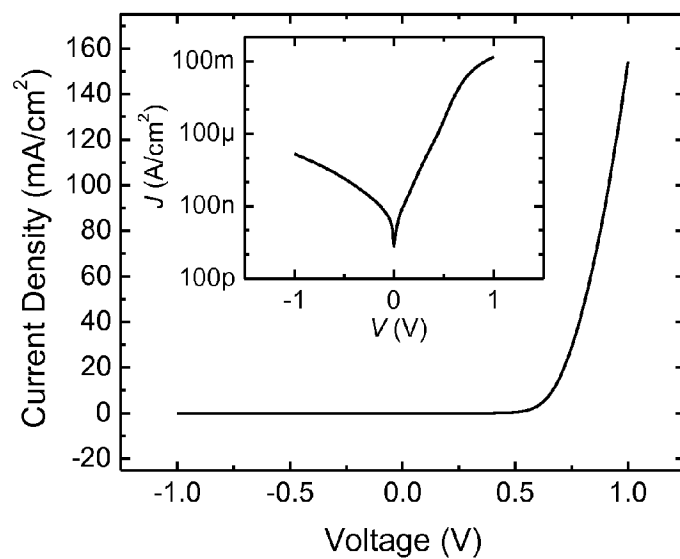


FIG. 77

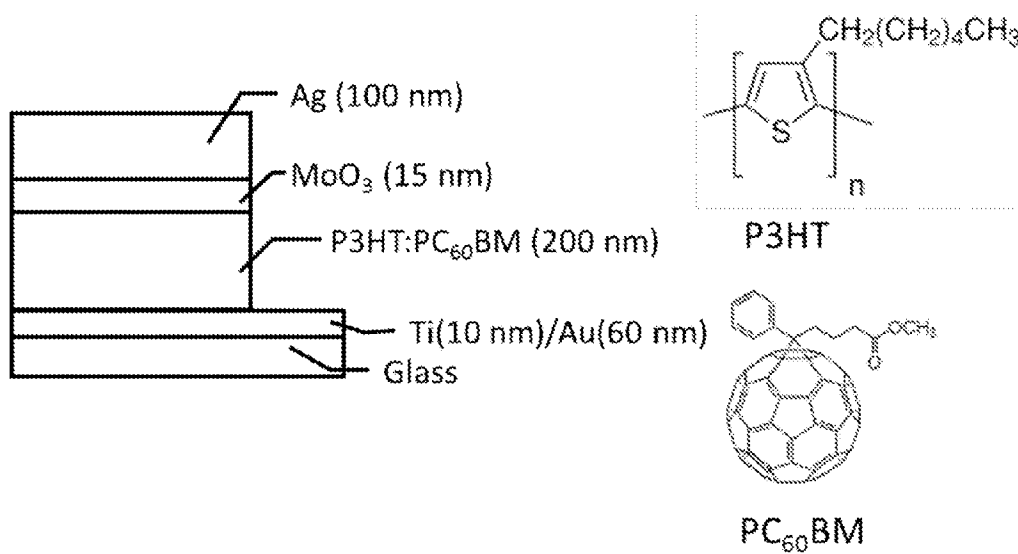


FIG. 78

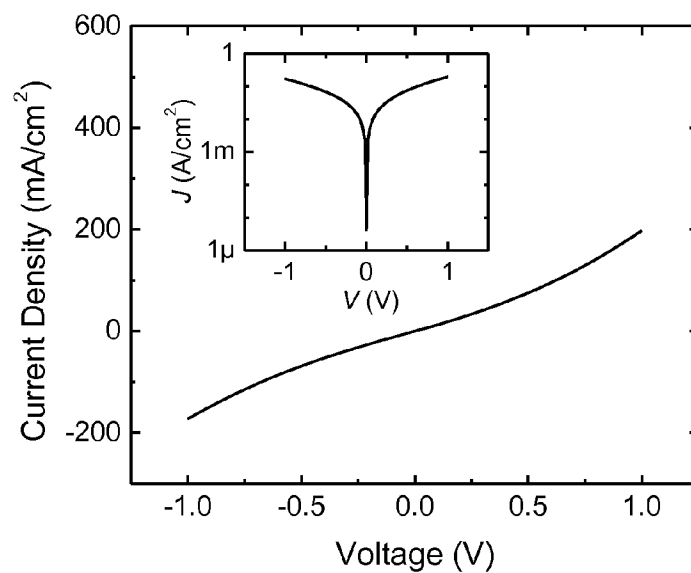


FIG. 79

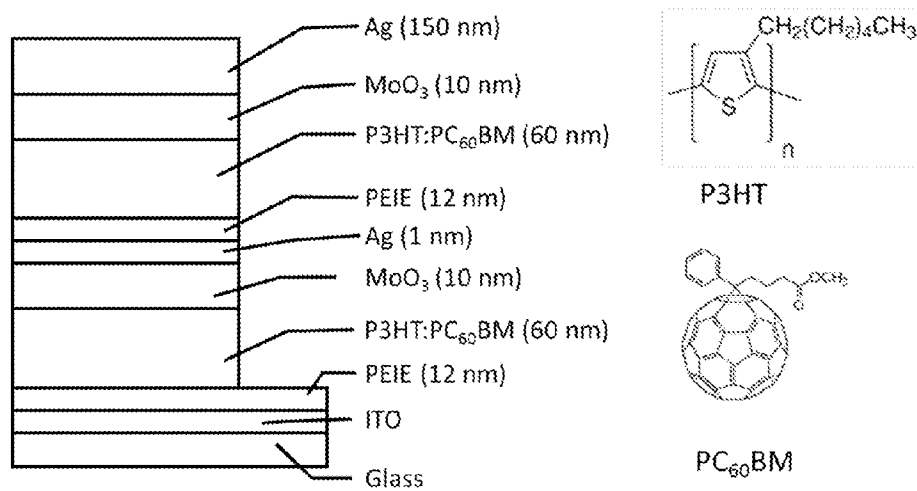


FIG. 80

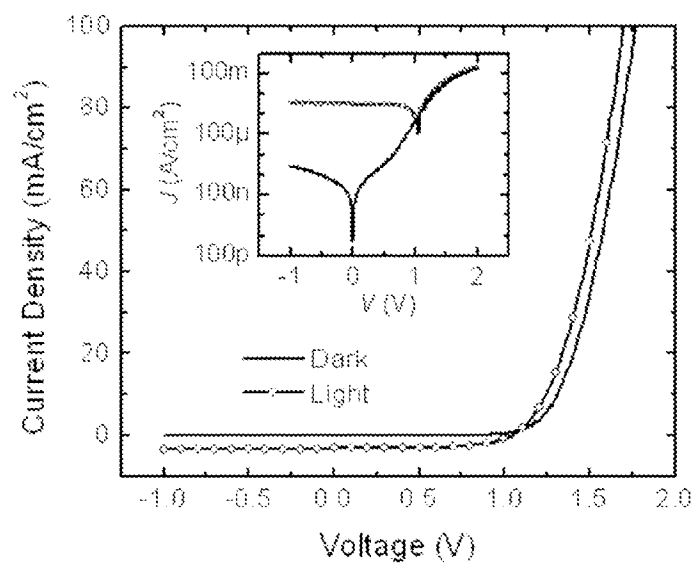


FIG. 81

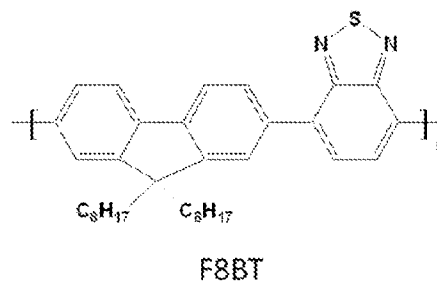
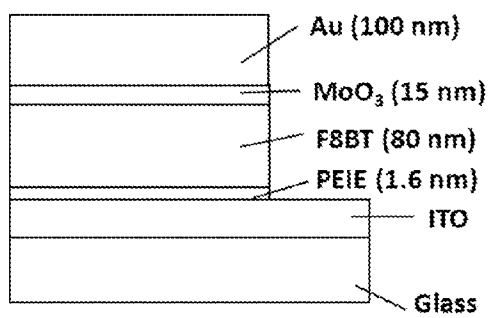


FIG. 82

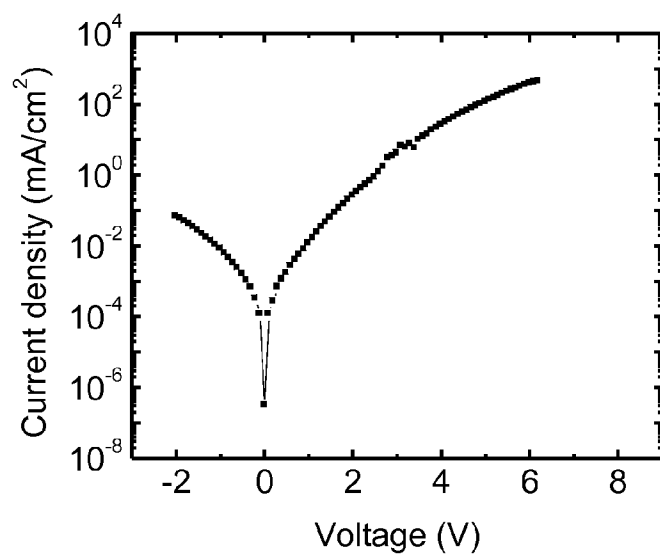


FIG. 83

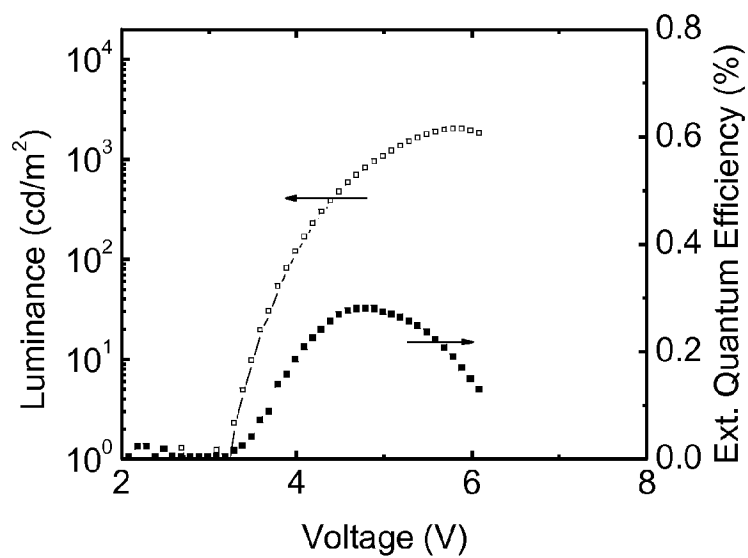


FIG. 84

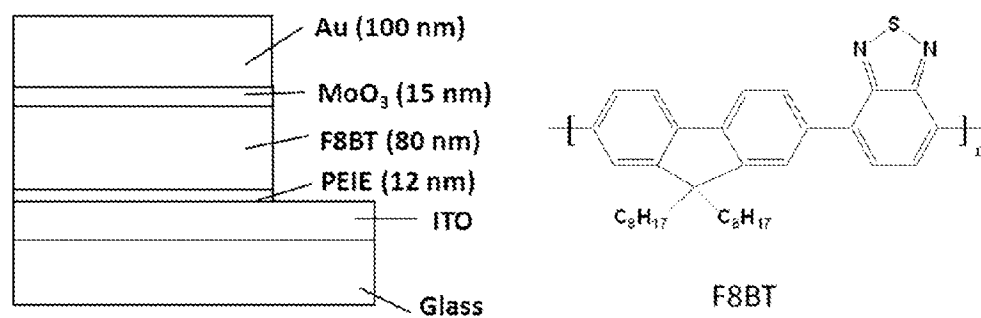


FIG. 85

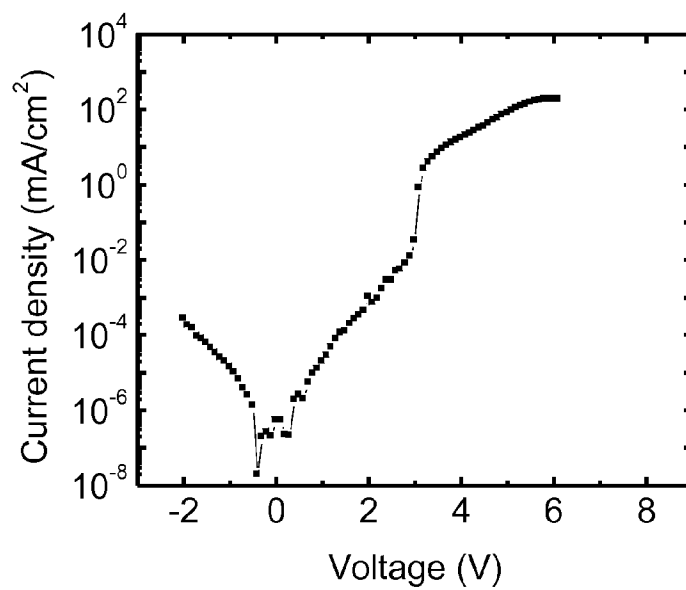


FIG. 86

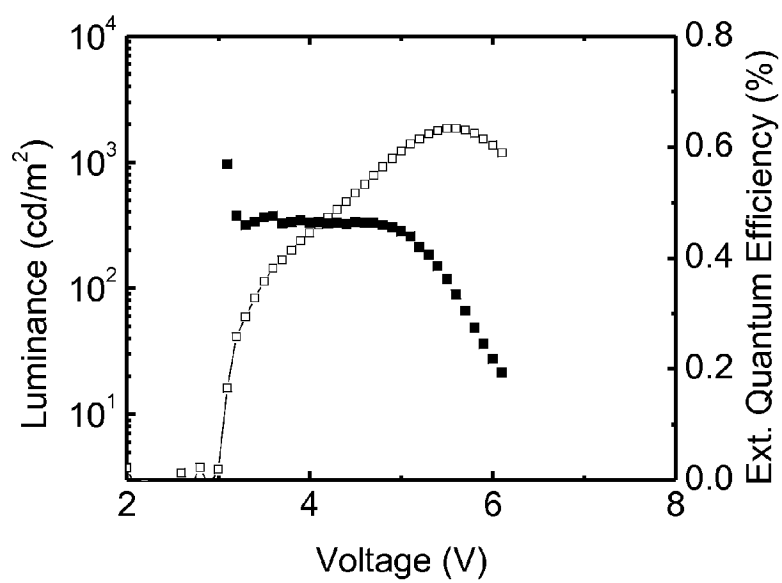


FIG. 87

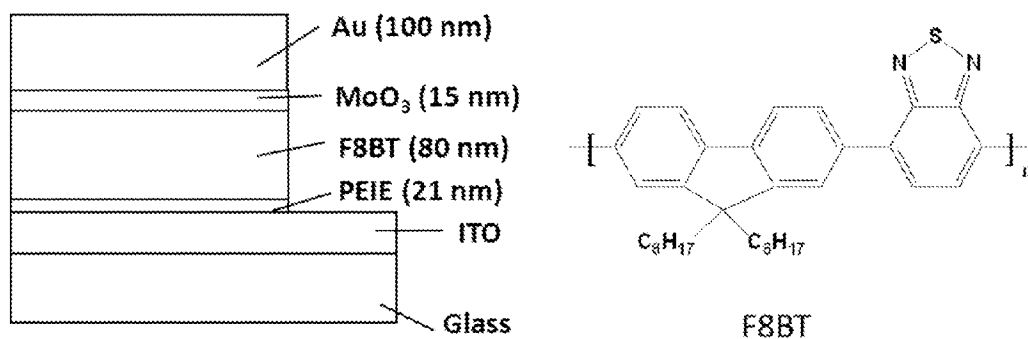


FIG. 88

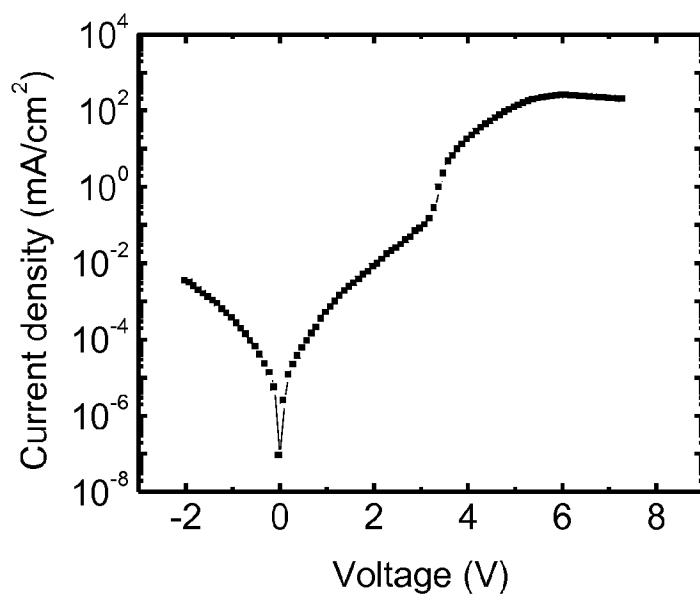


FIG. 89

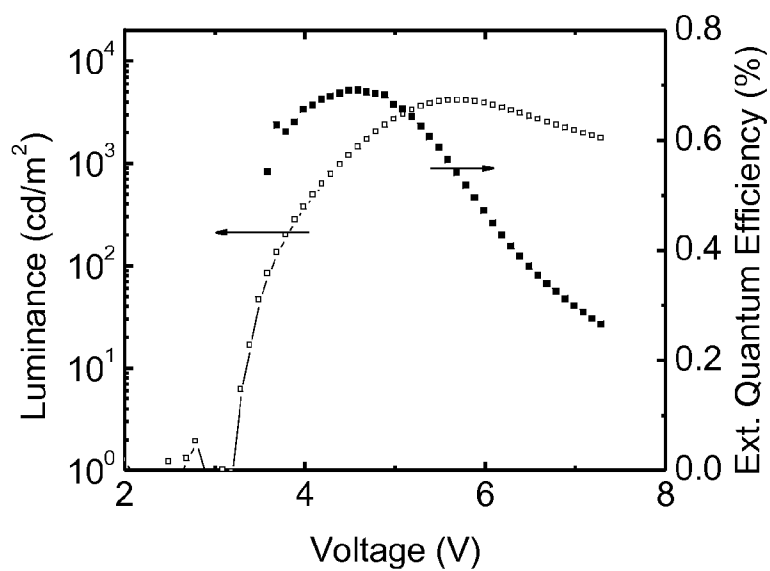


FIG. 90

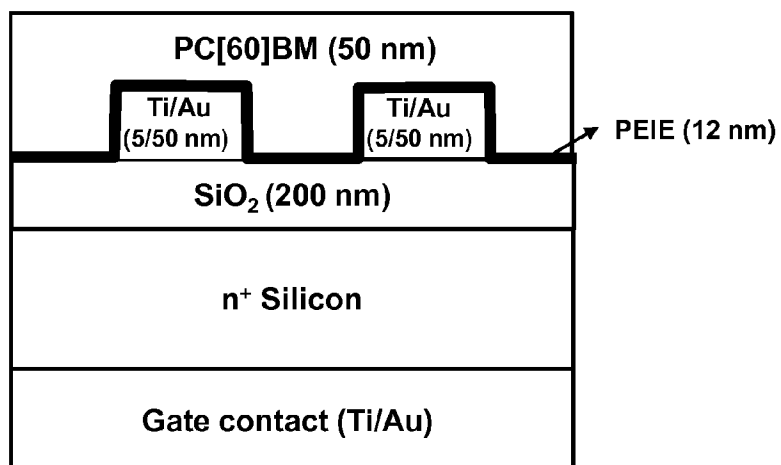


FIG. 91

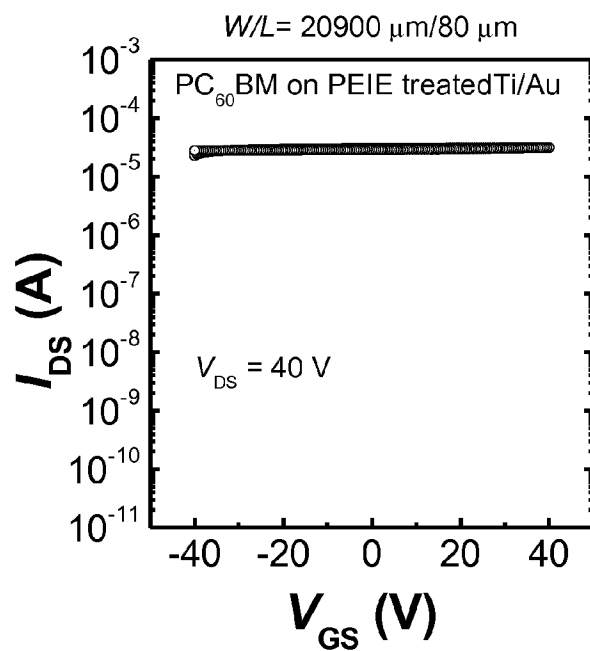


FIG. 92

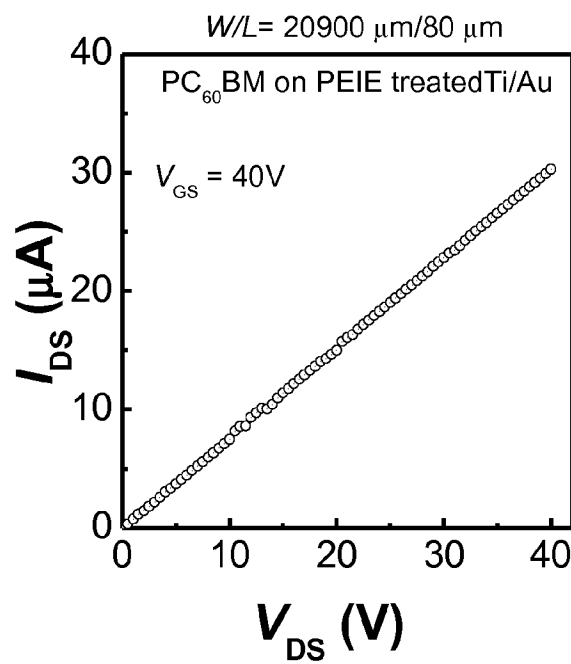


FIG. 93

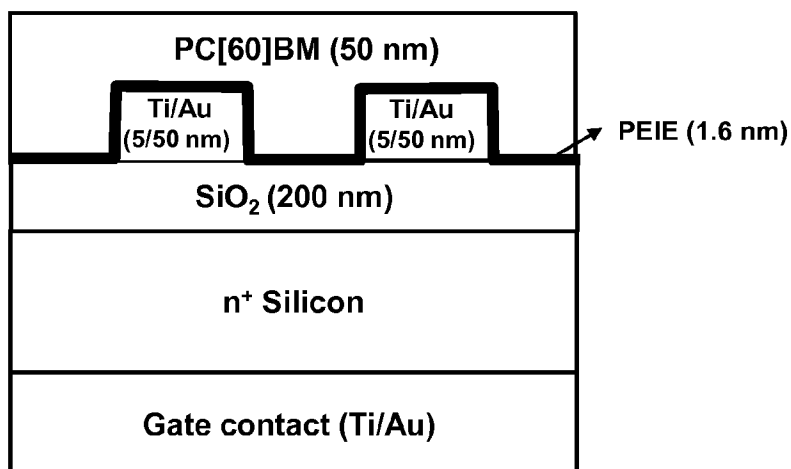


FIG. 94

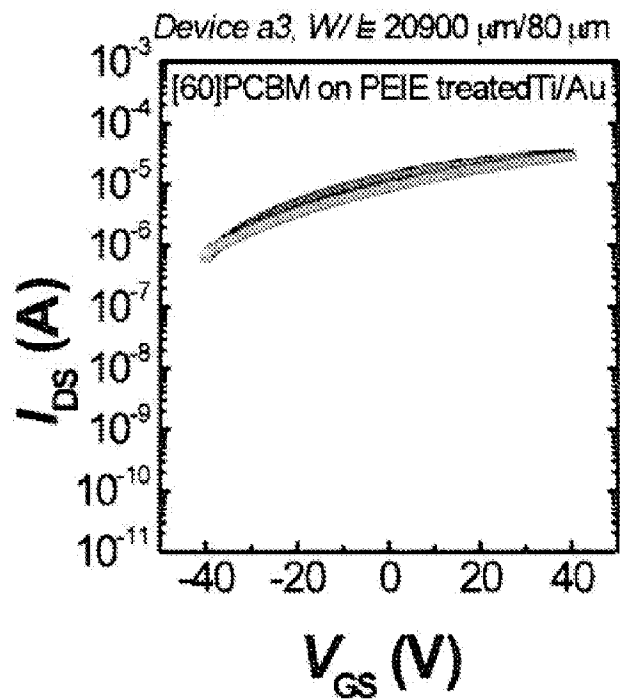


FIG. 95

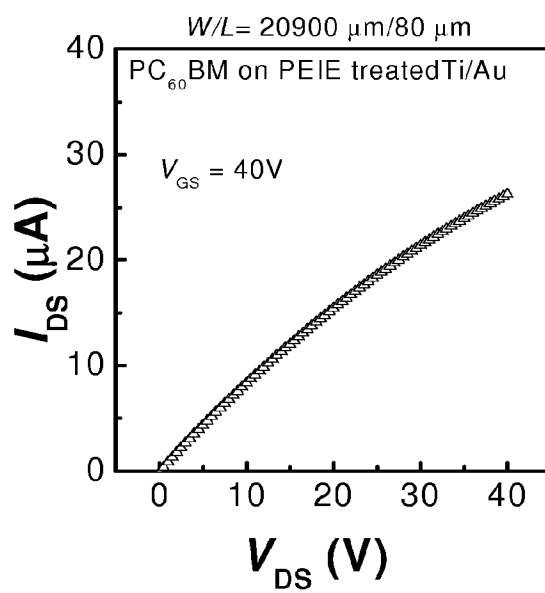


FIG. 96

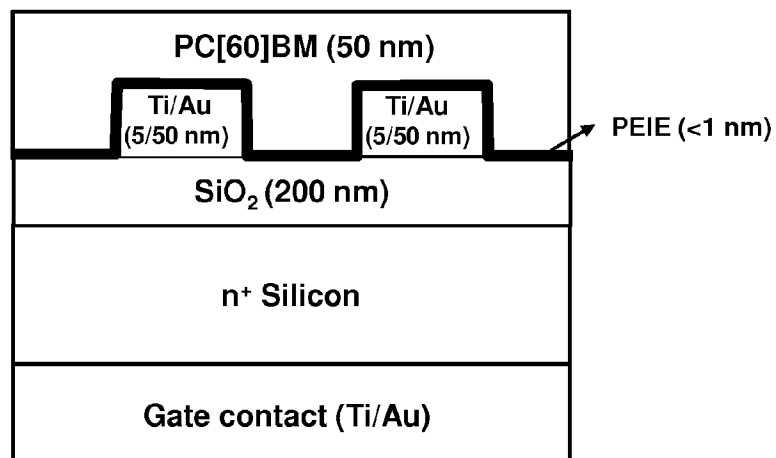


FIG. 97

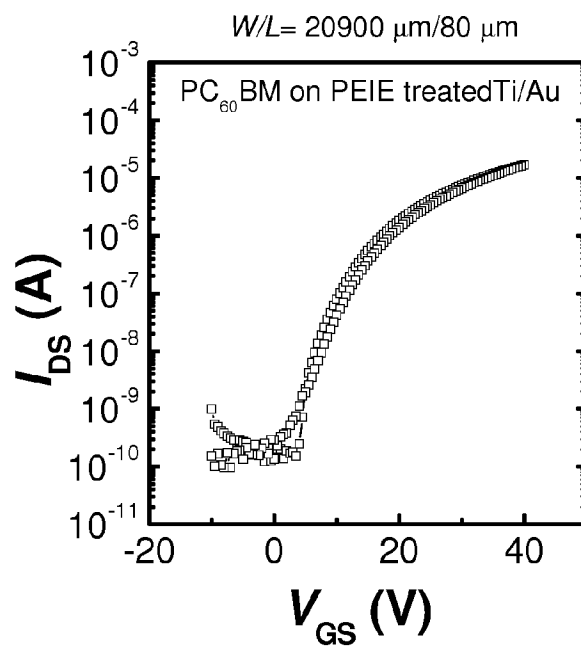


FIG. 98

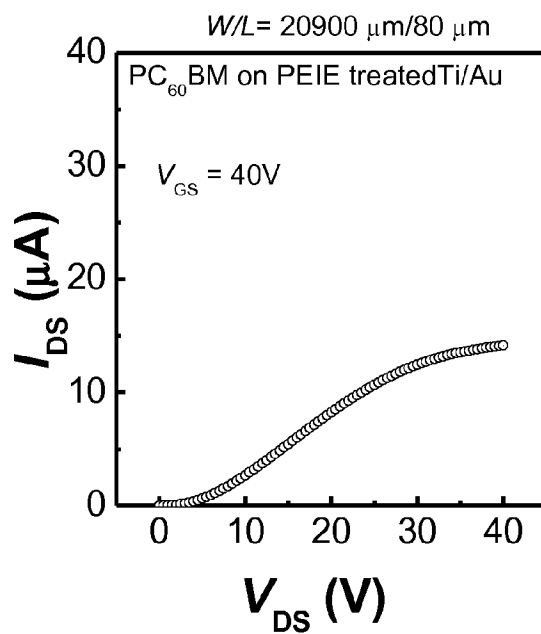


FIG. 99

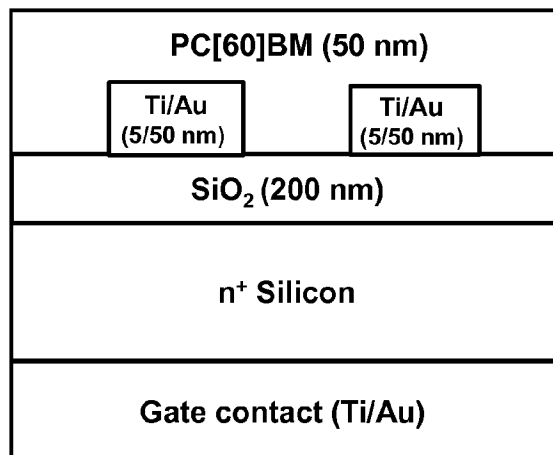


FIG. 100

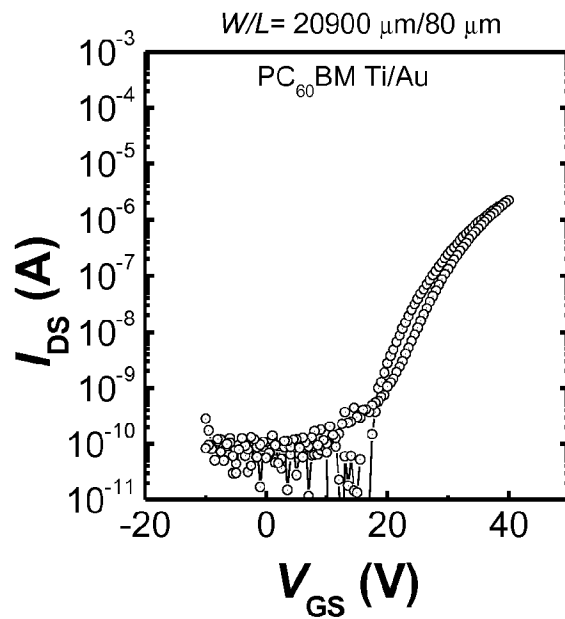


FIG. 101

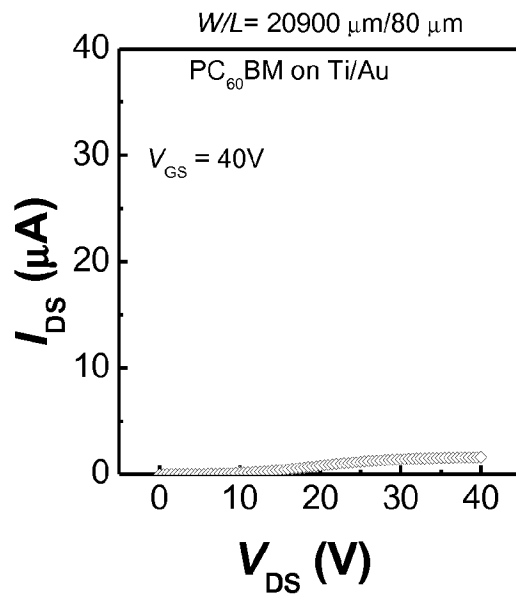


FIG. 102

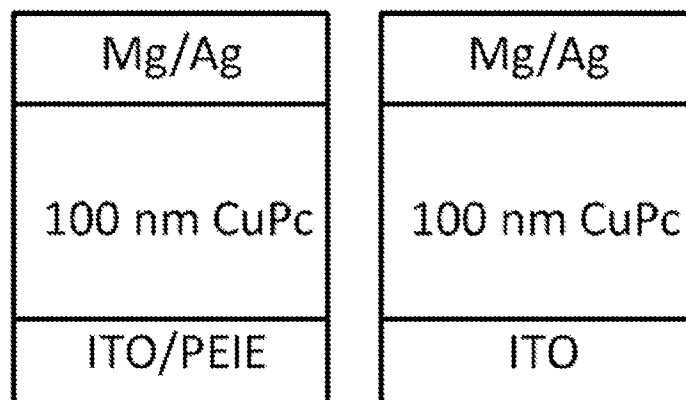


FIG. 103

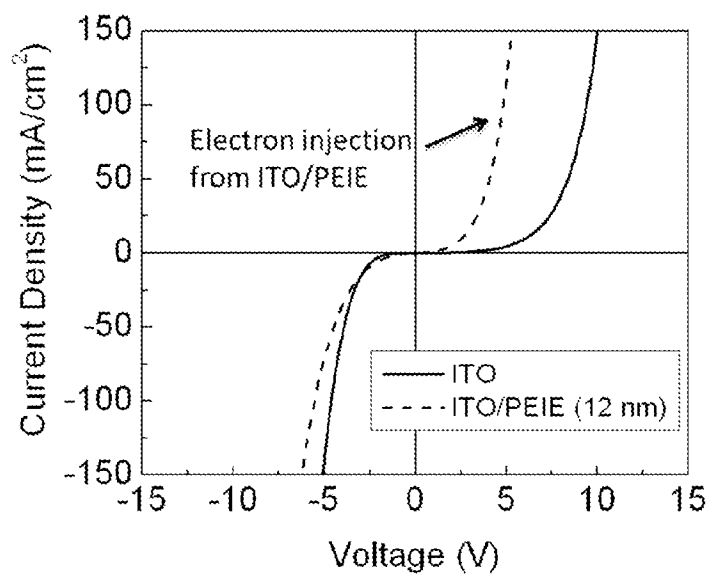


FIG. 104

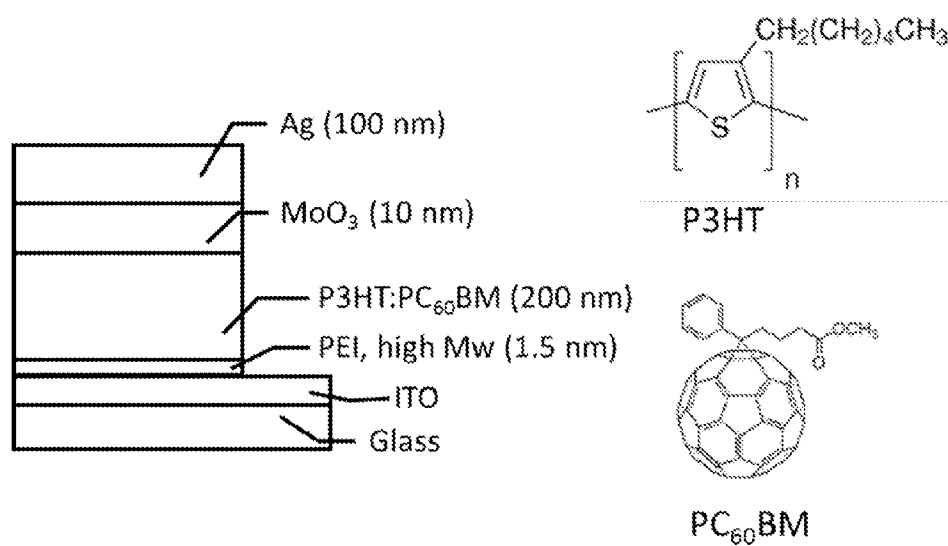


FIG. 105

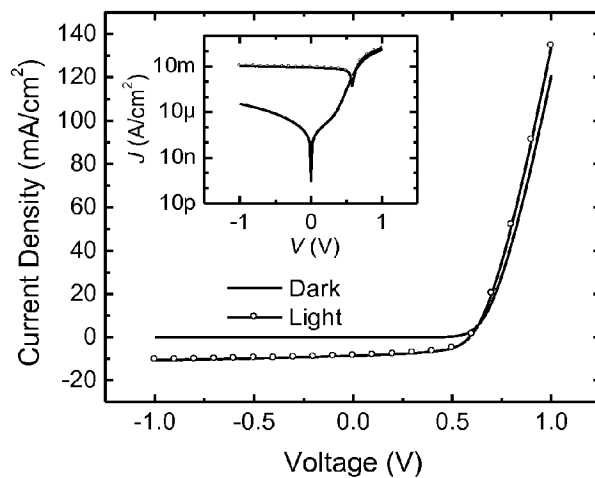


FIG. 106

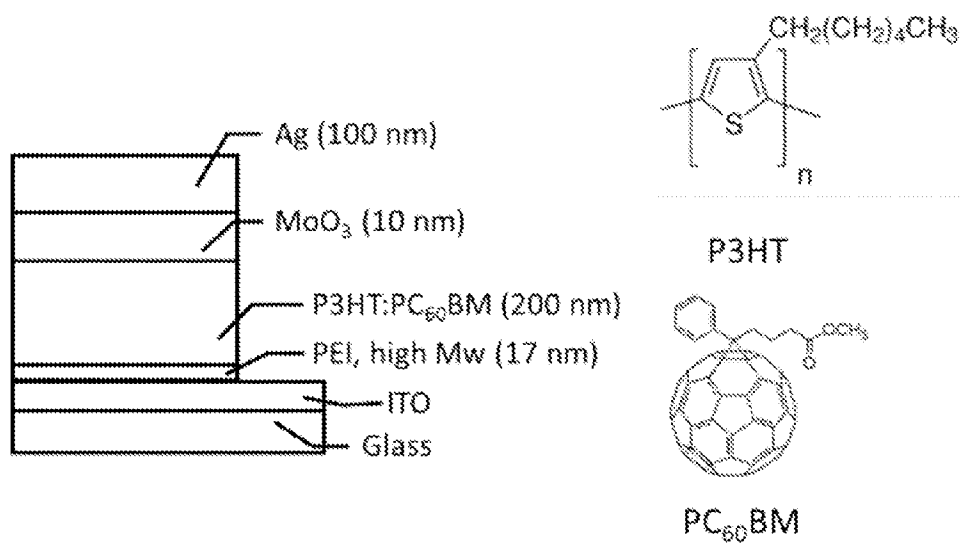


FIG. 107

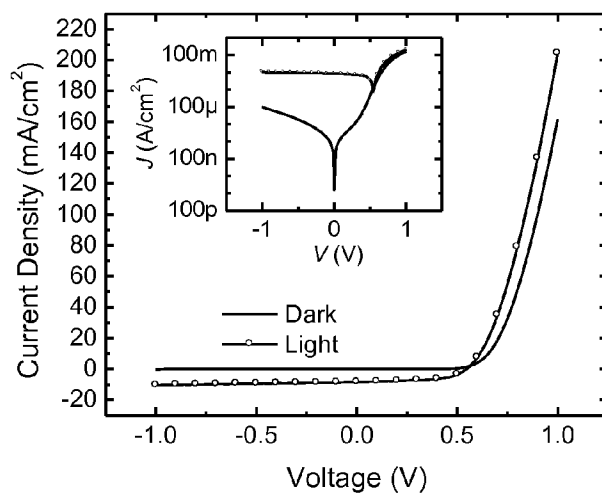


FIG. 108

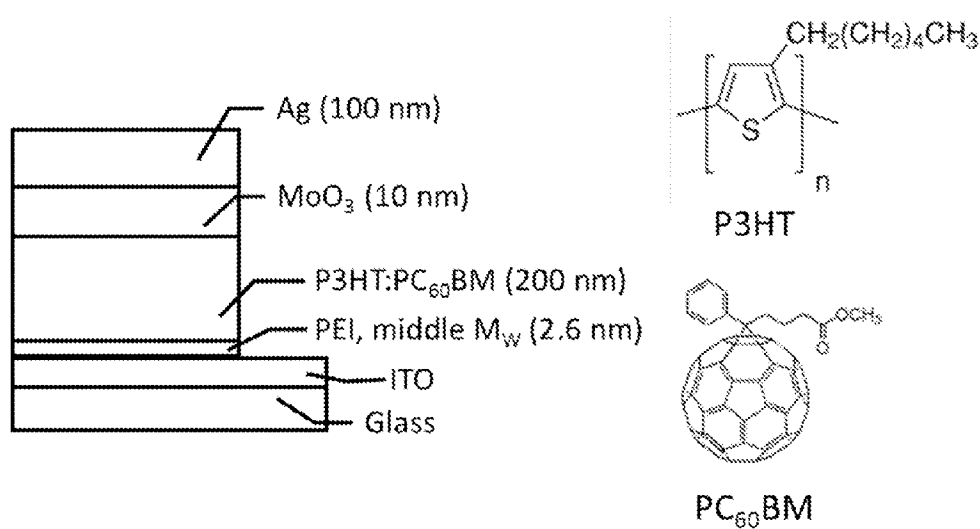


FIG. 109

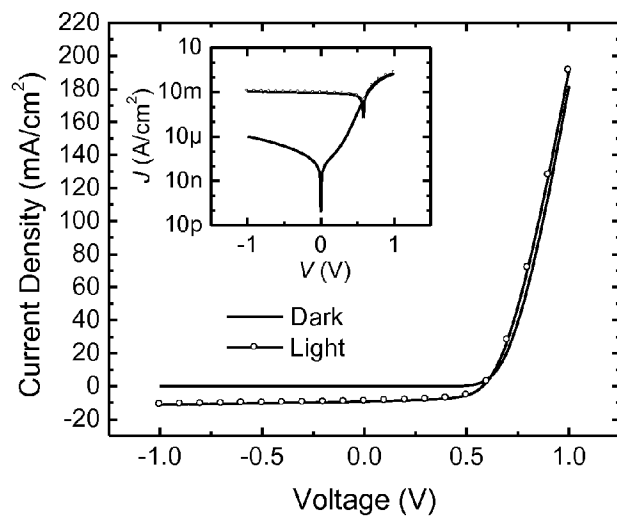


FIG. 110

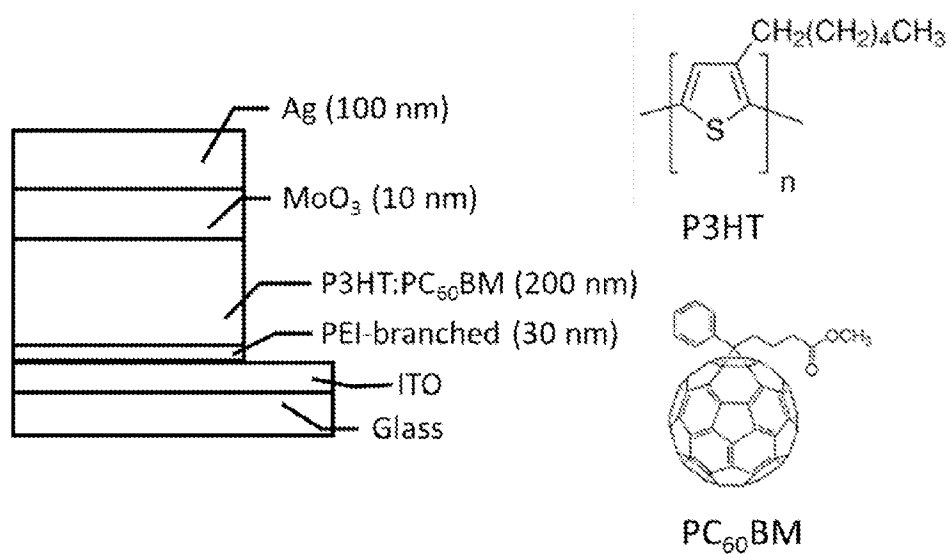


FIG. 111

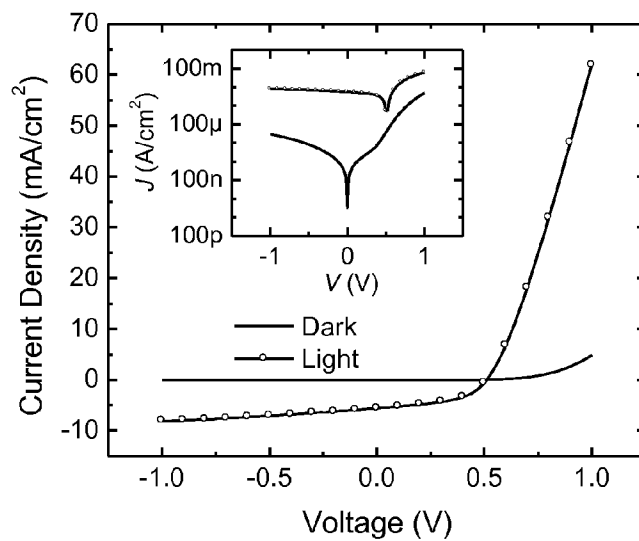


FIG. 112

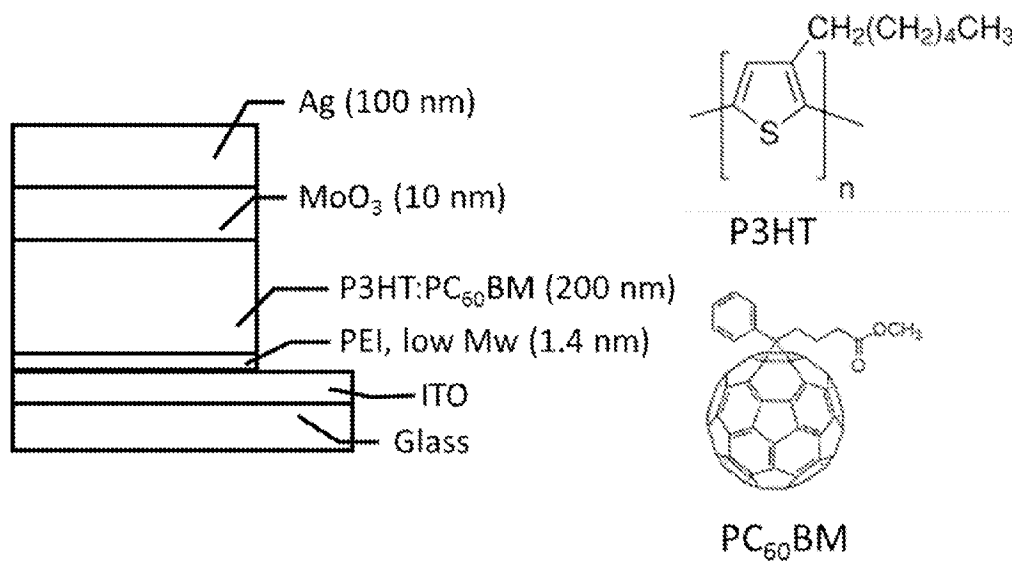


FIG. 113

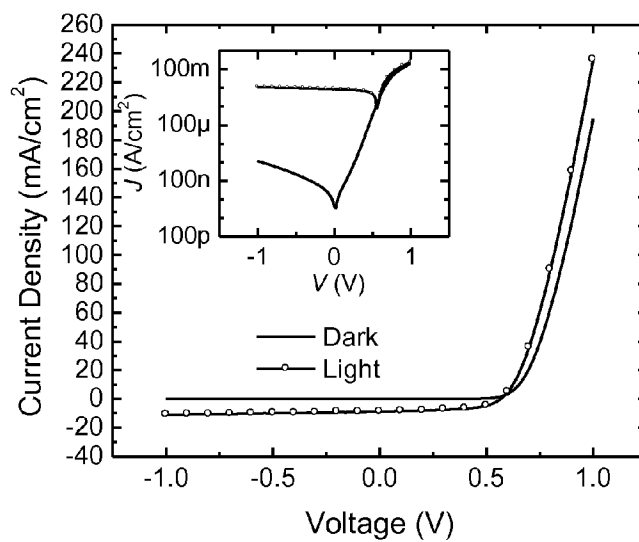


FIG. 114

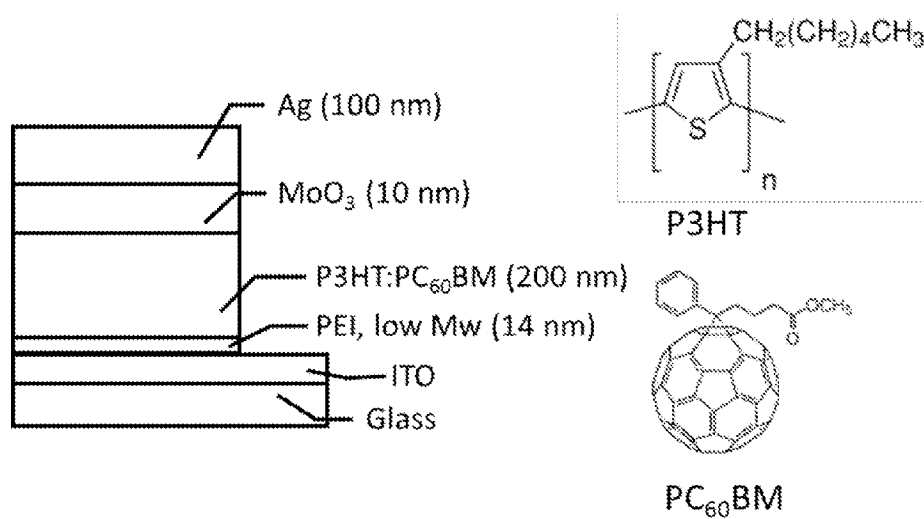


FIG. 115

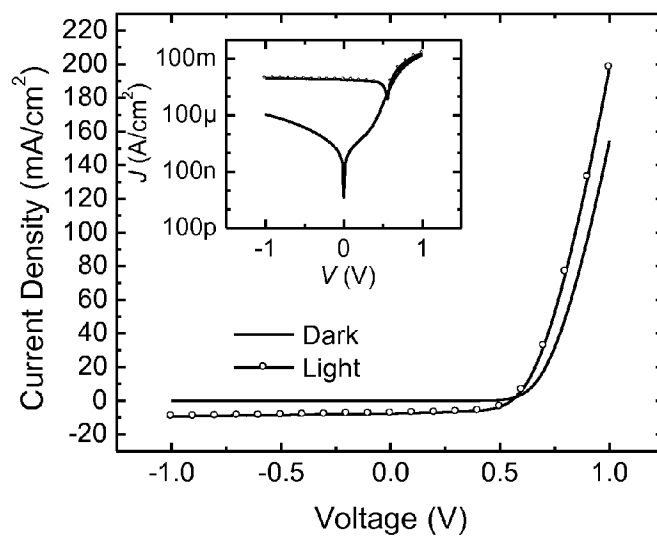


FIG. 116

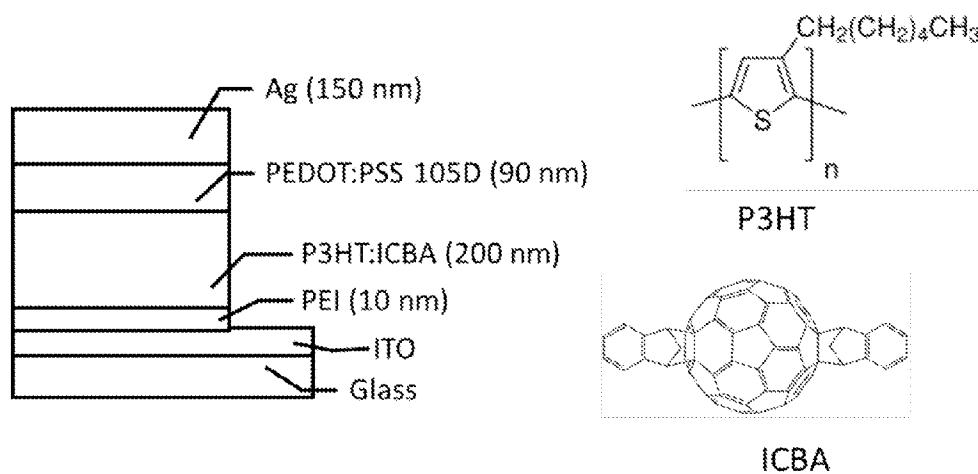


FIG. 117

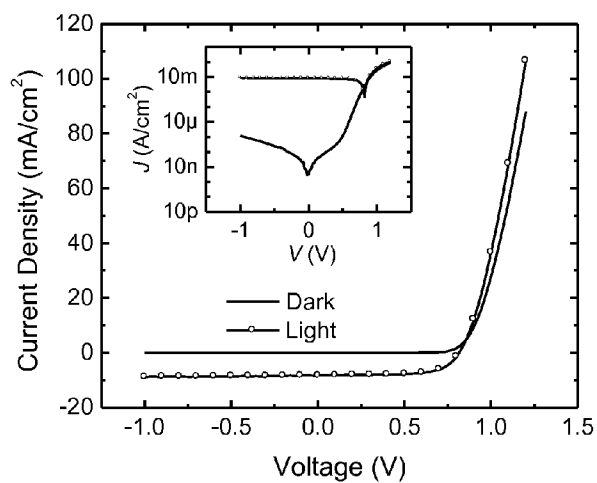


FIG. 118

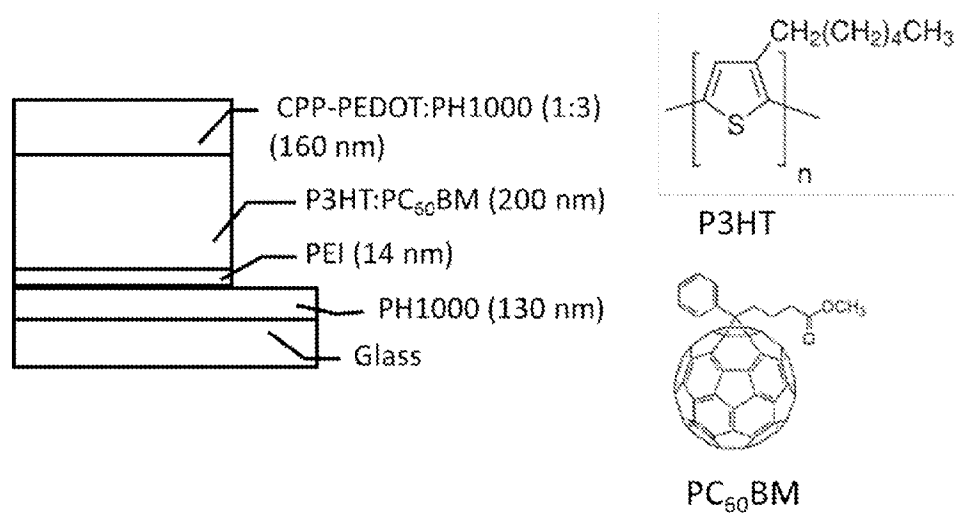


FIG. 119

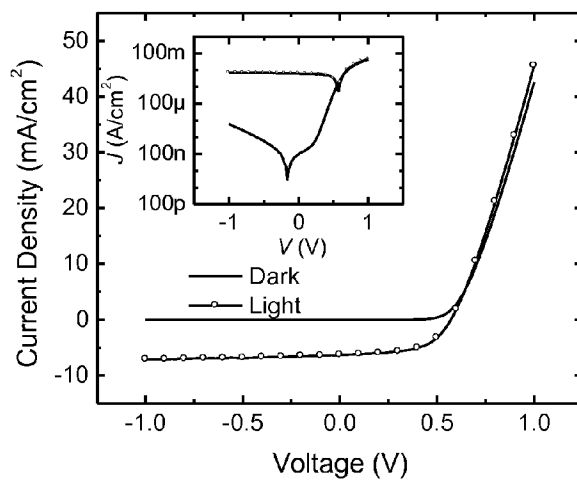


FIG. 120

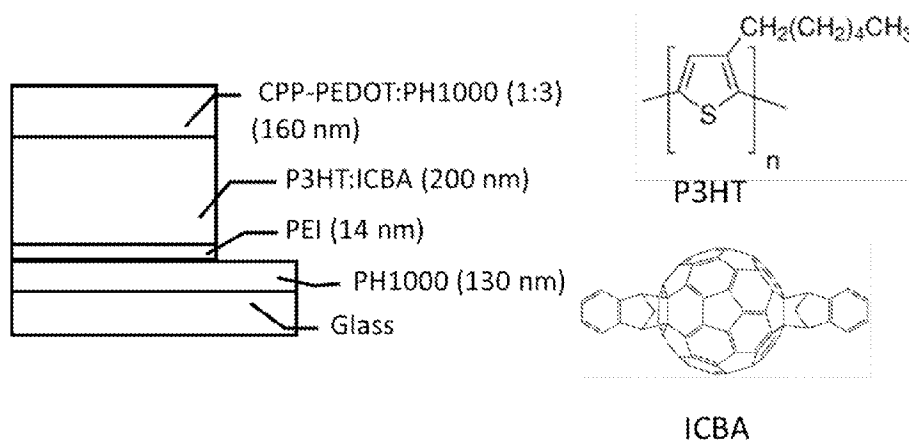


FIG. 121

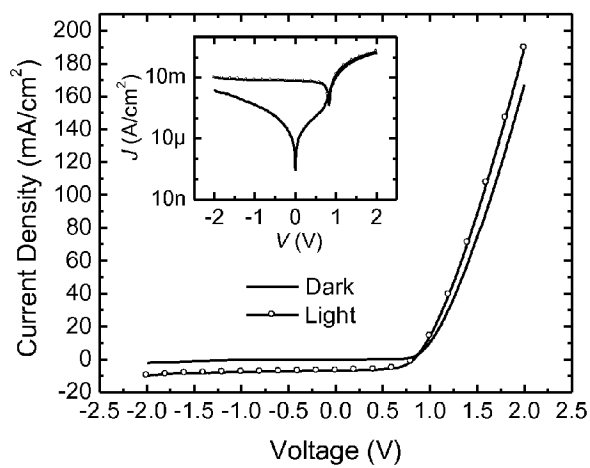


FIG. 122

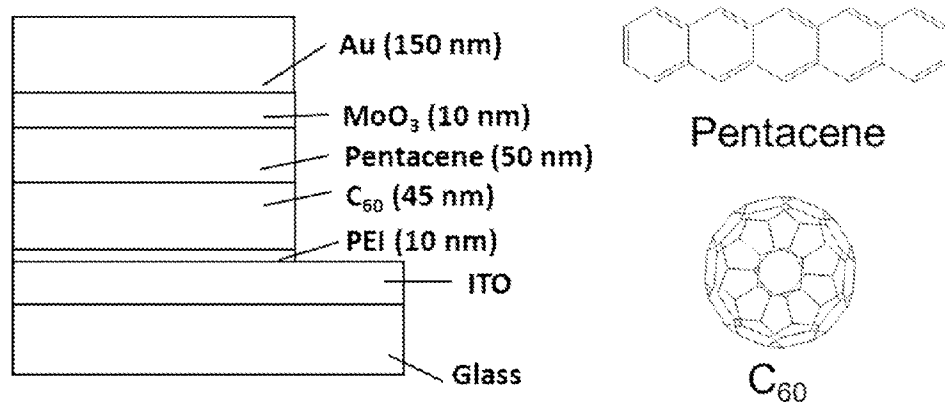


FIG. 123

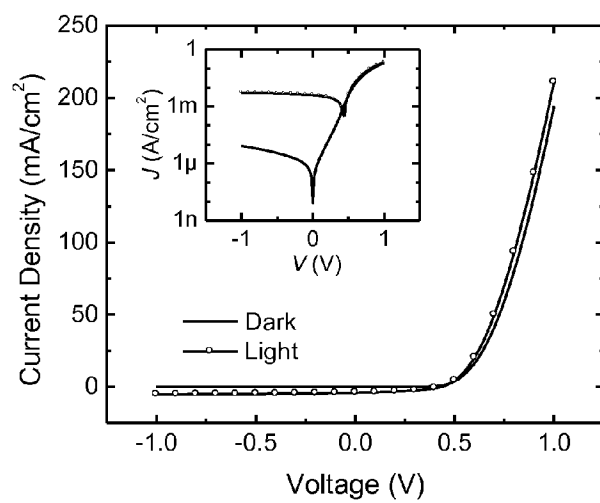


FIG. 124

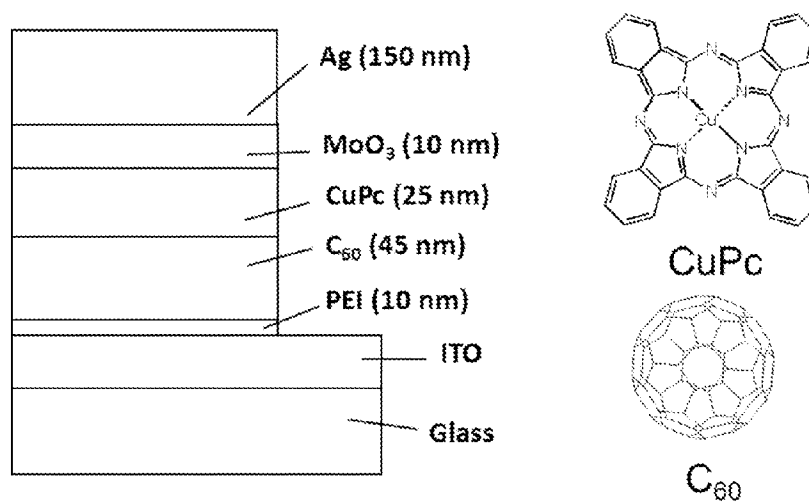


FIG. 125

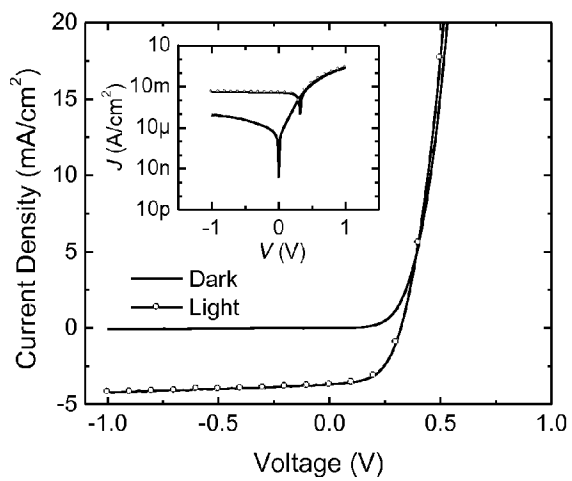


FIG. 126

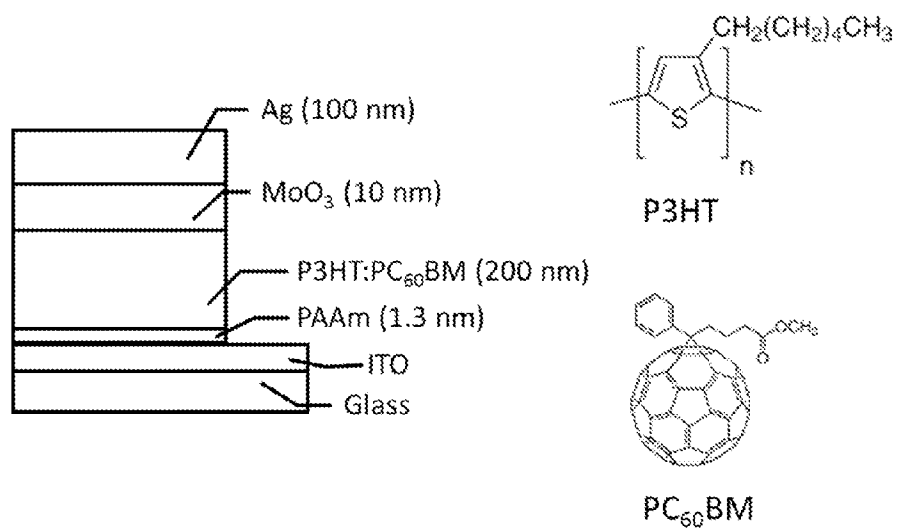


FIG. 127

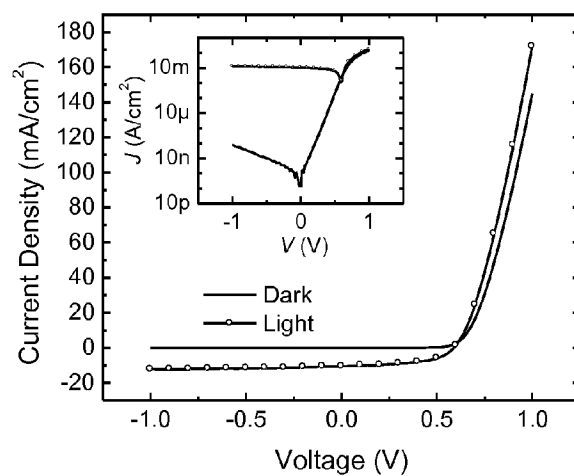


FIG. 128

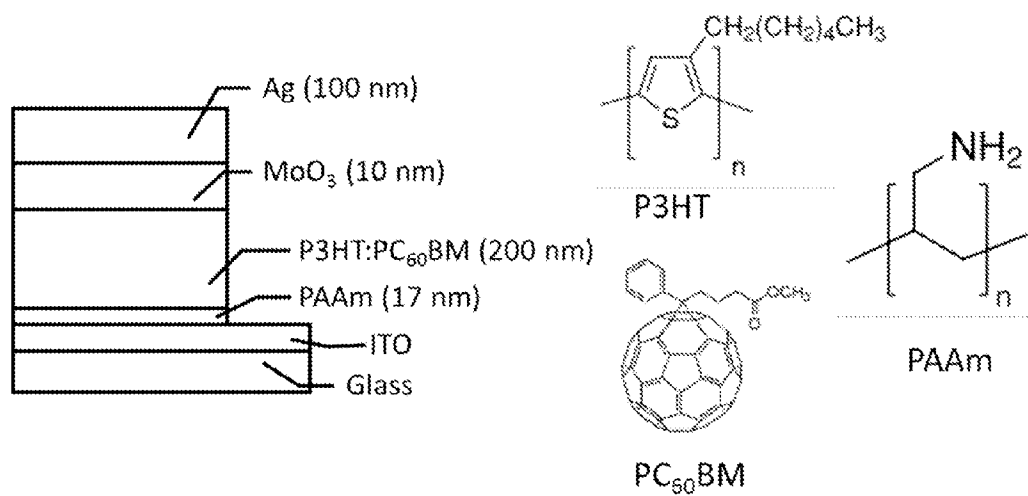


FIG. 129

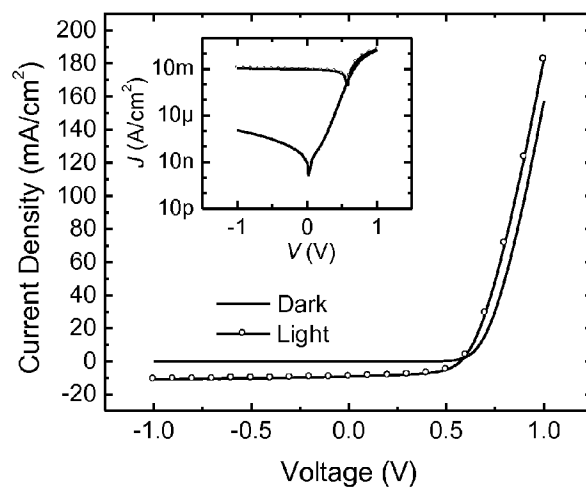


FIG. 130

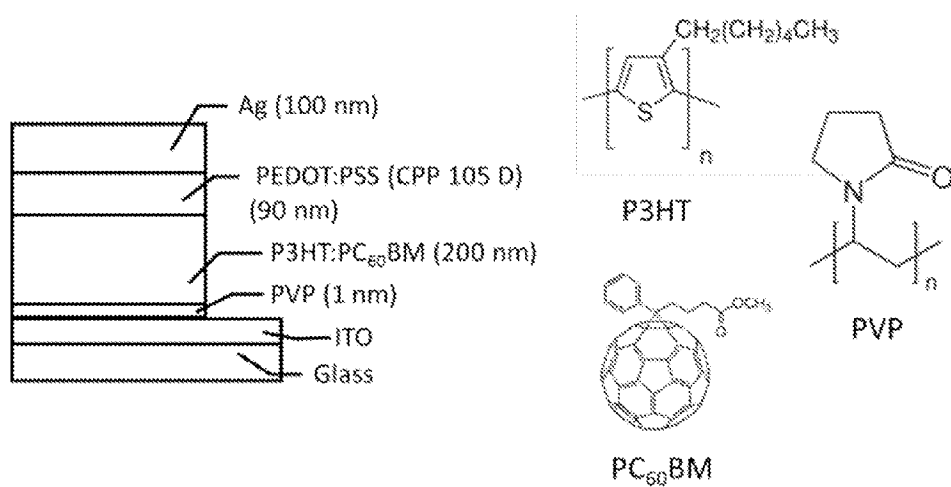


FIG. 131

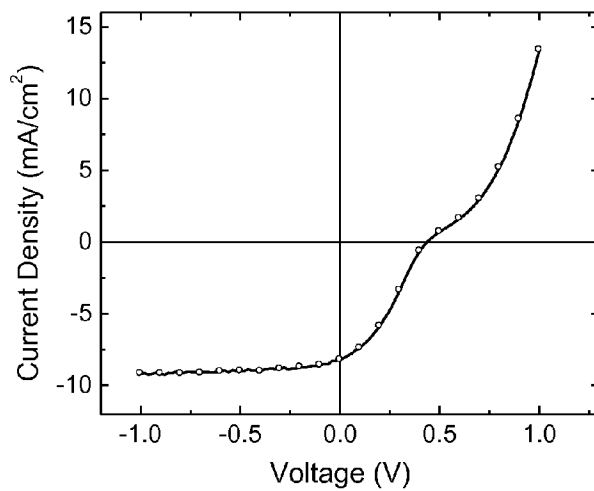


FIG. 132

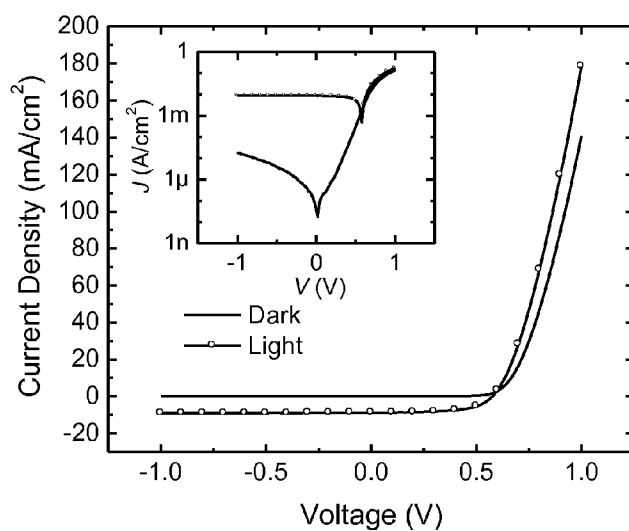


FIG. 133

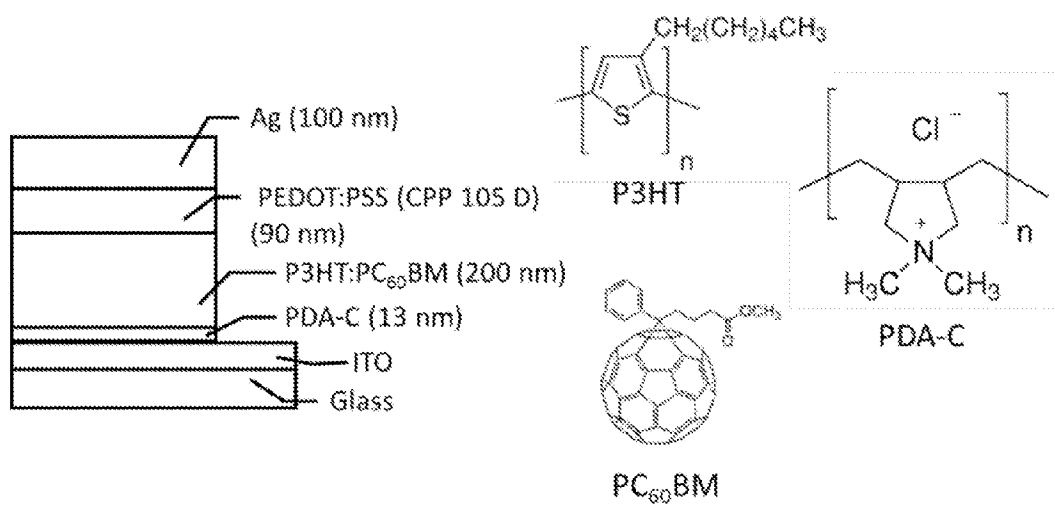


FIG. 134

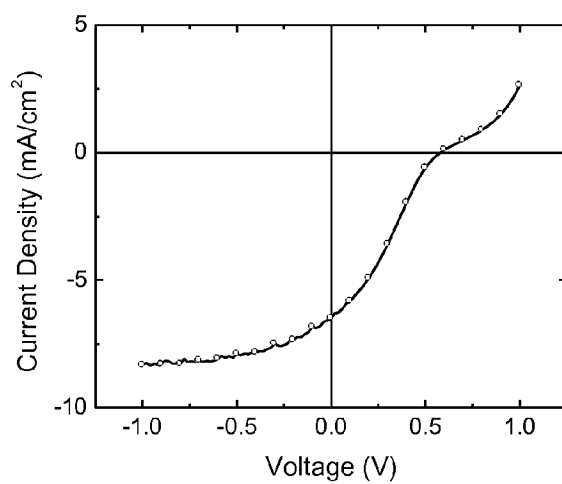


FIG. 135

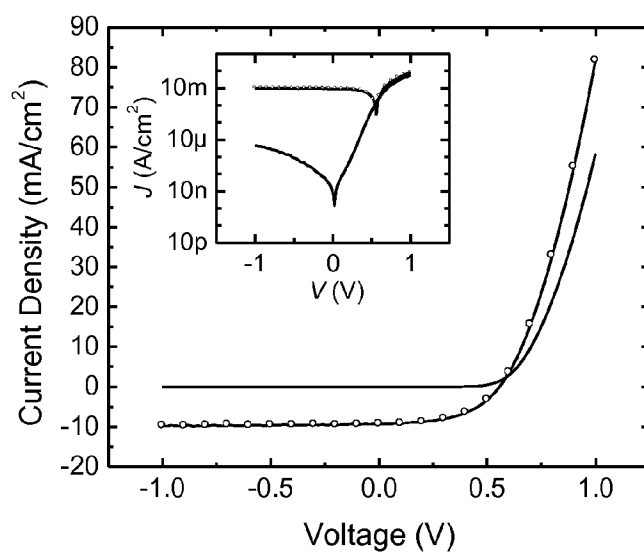


FIG. 136

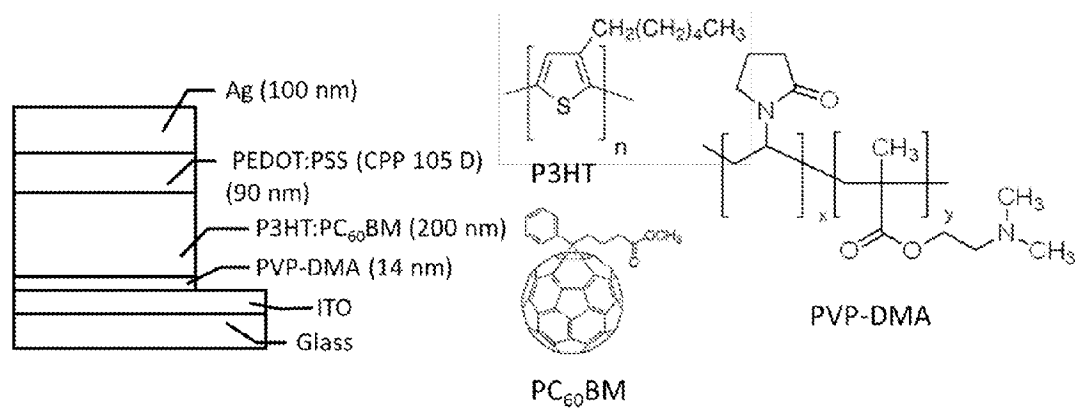


FIG. 137

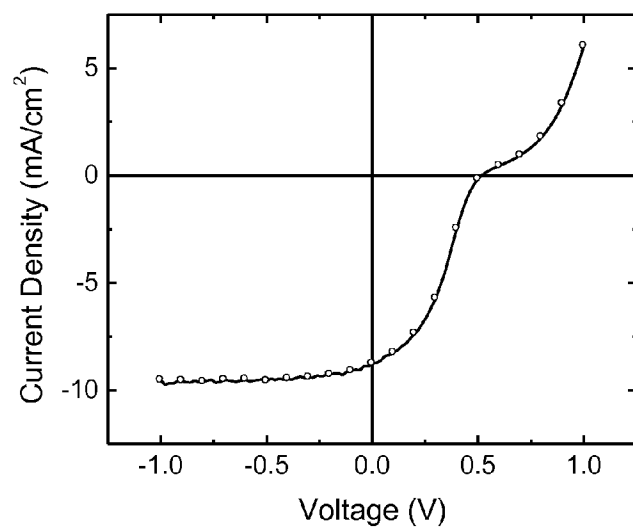


FIG. 138

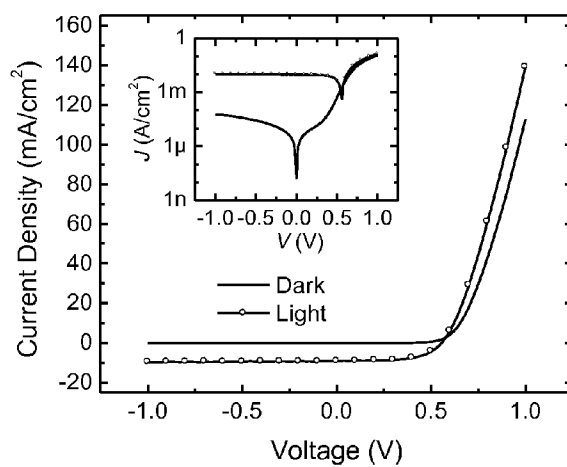


FIG. 139

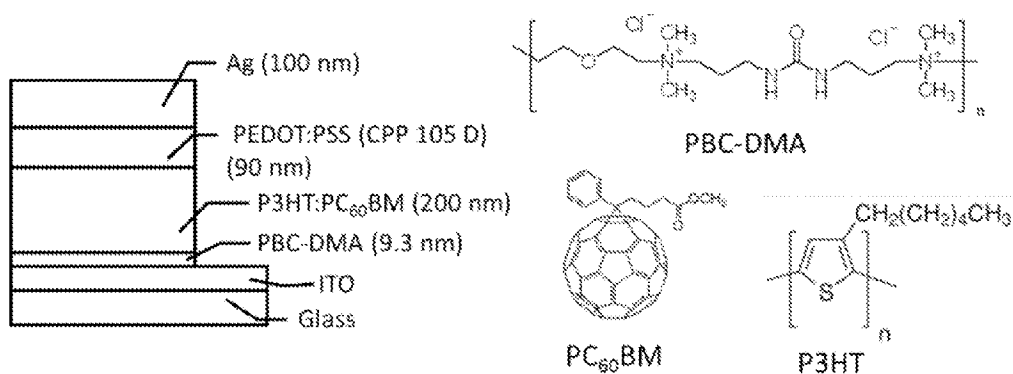


FIG. 140

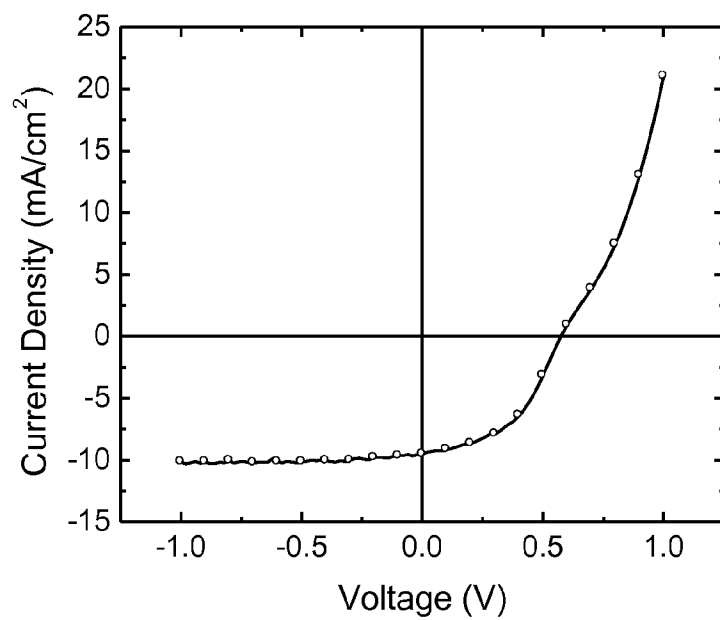


FIG. 141

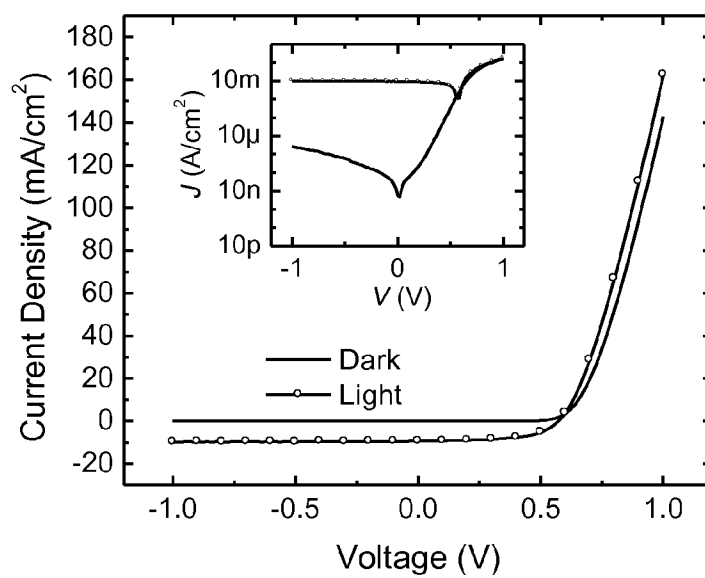


FIG. 142

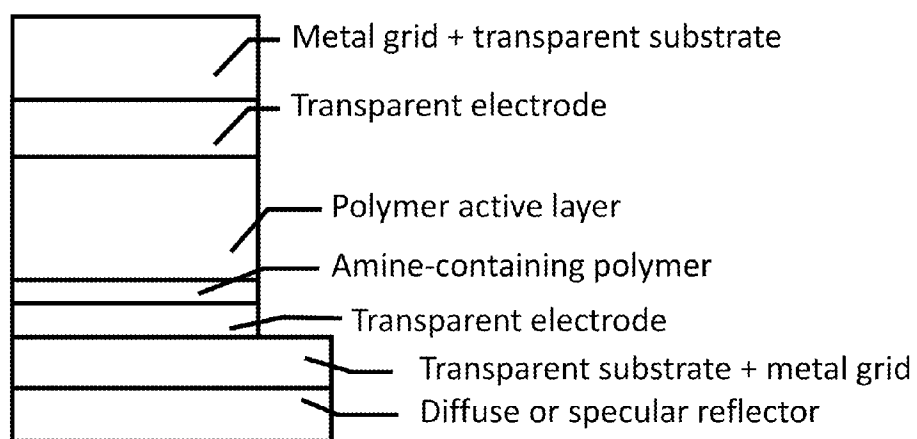


FIG. 143

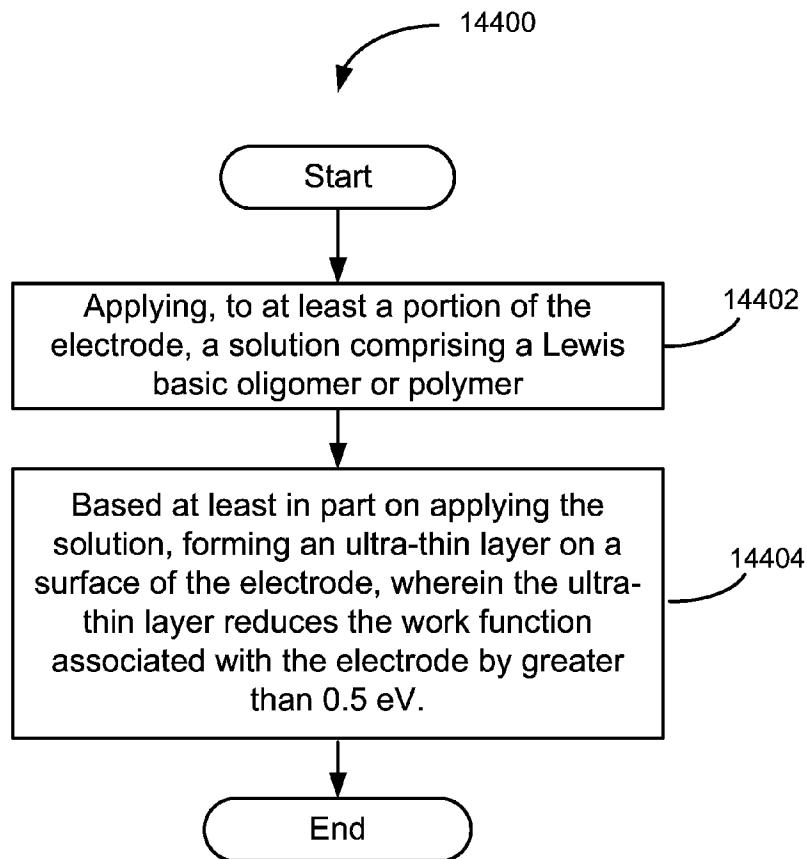


FIG. 144

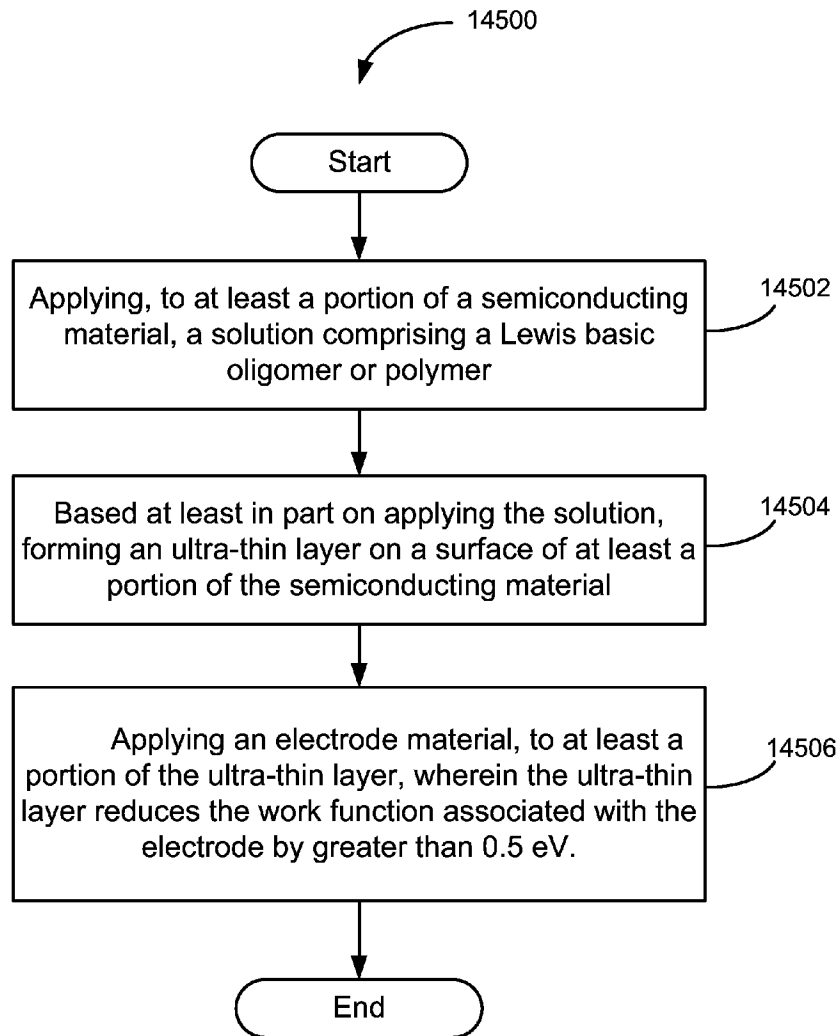


FIG. 145

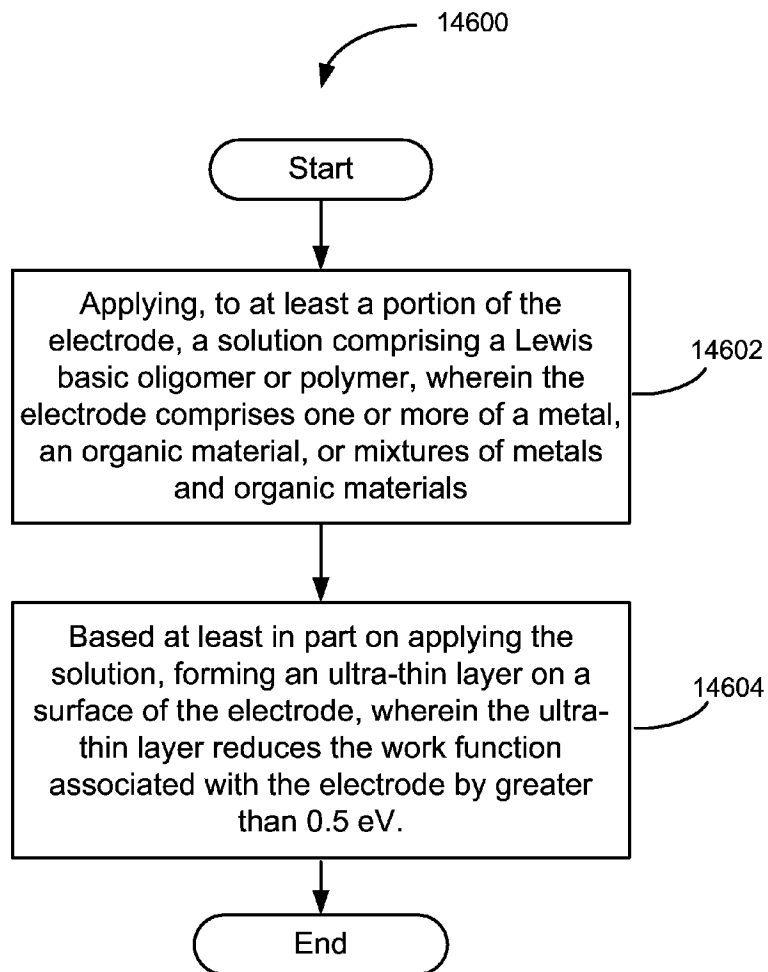


FIG. 146

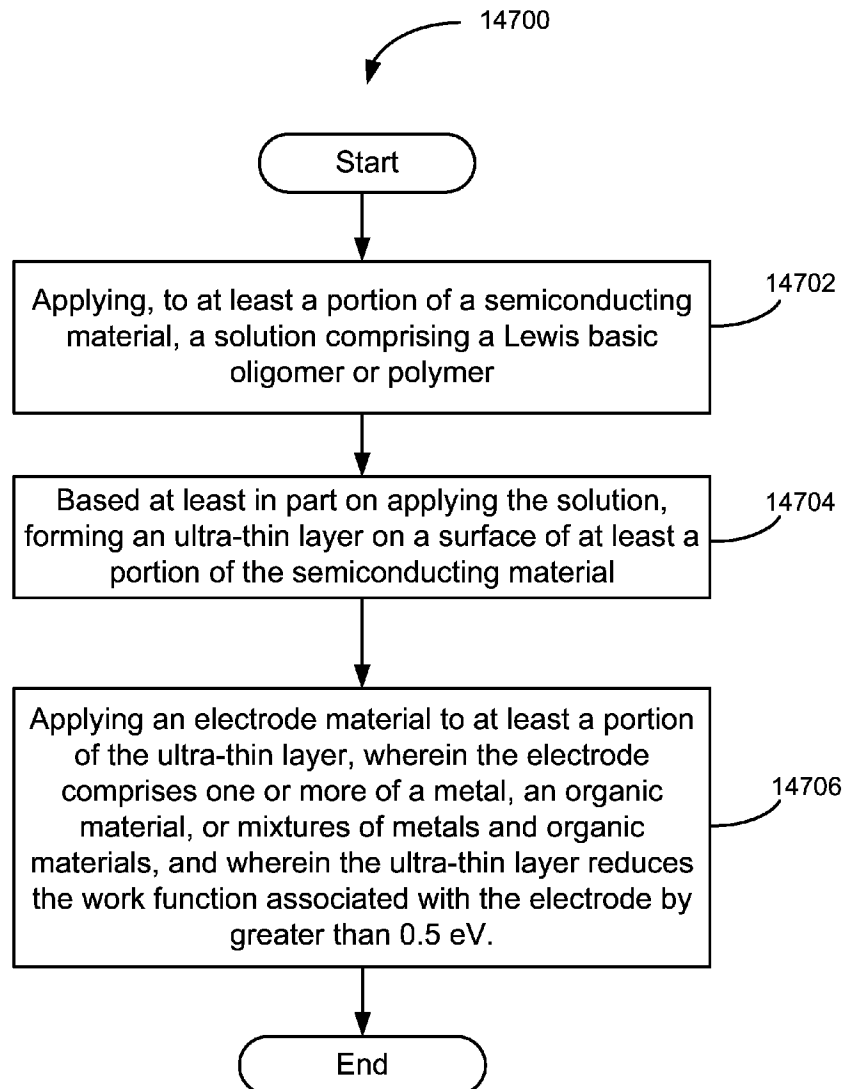


FIG. 147

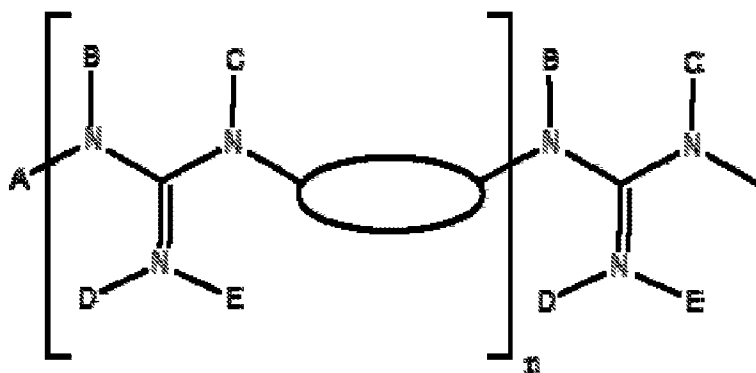


FIG. 148

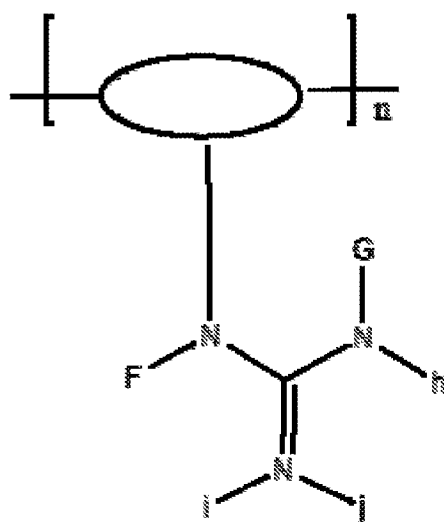


FIG. 149

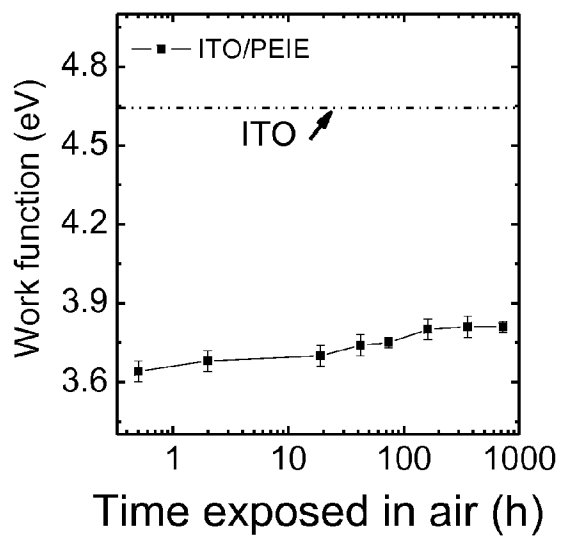


FIG. 150

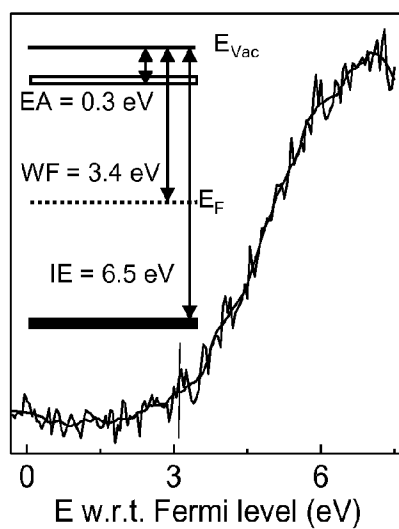


FIG. 151

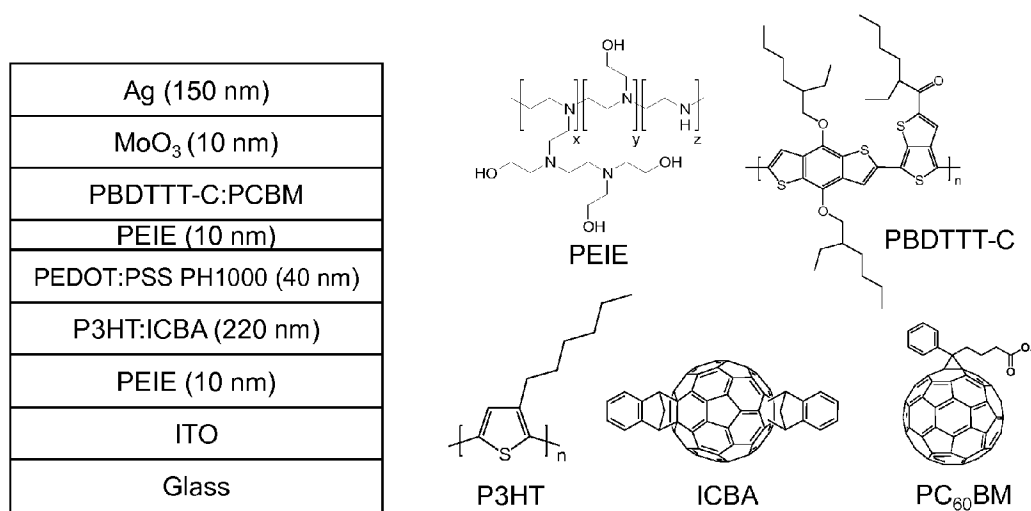


Fig. 152

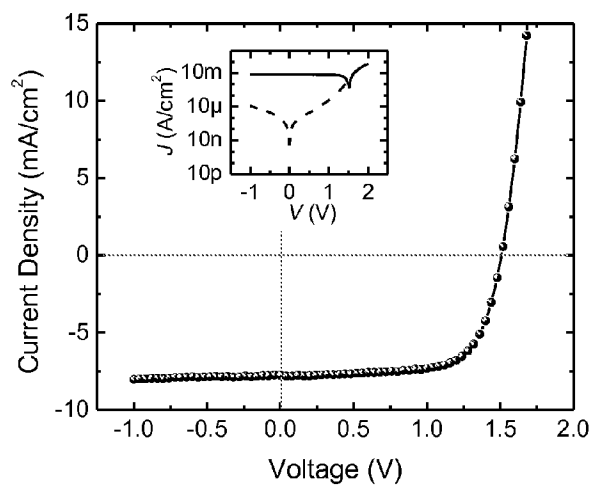
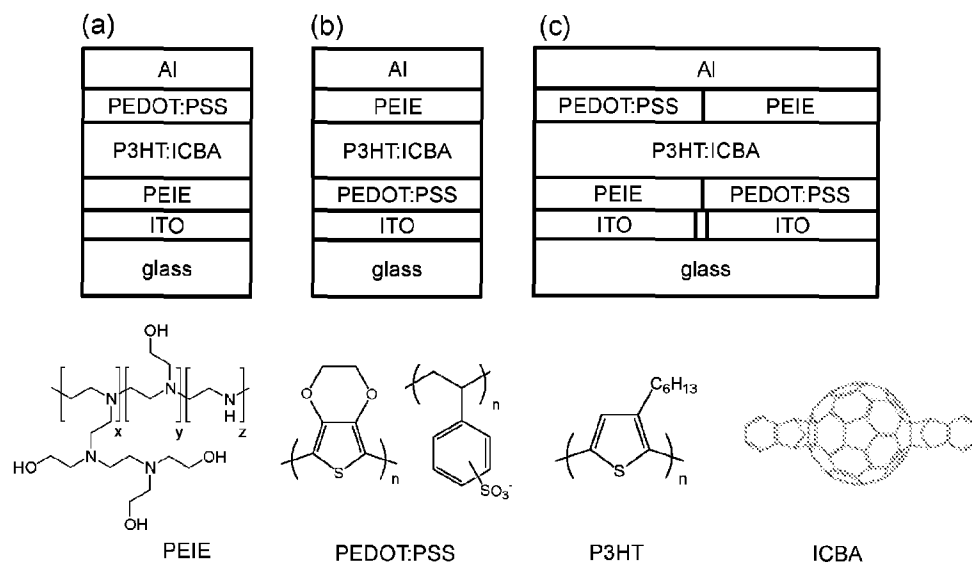


Fig. 153



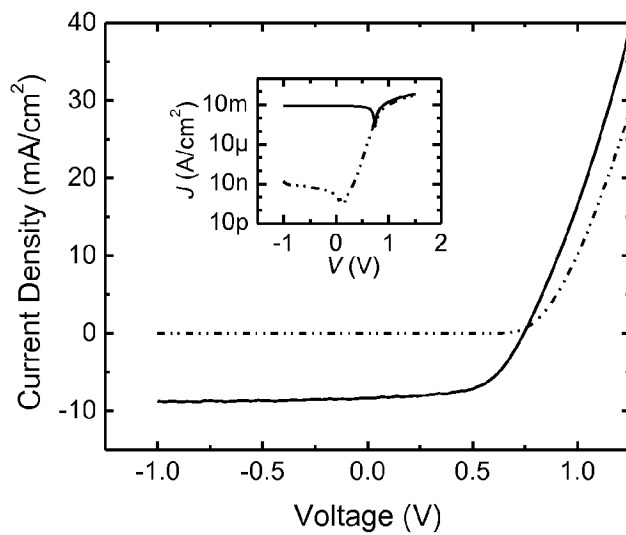


Fig.156

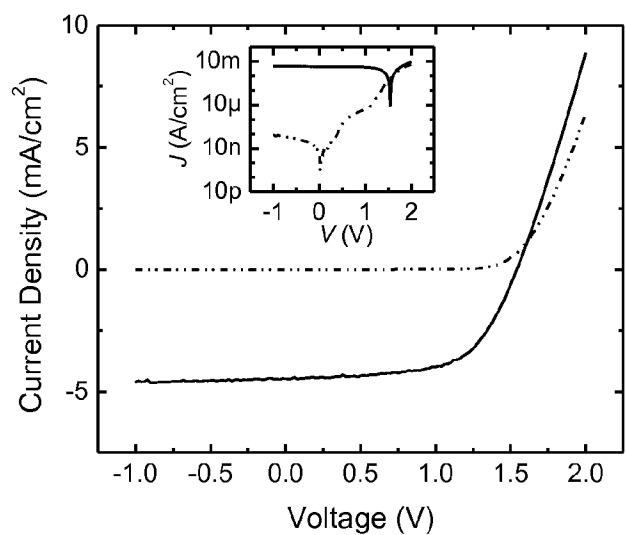


Fig.157

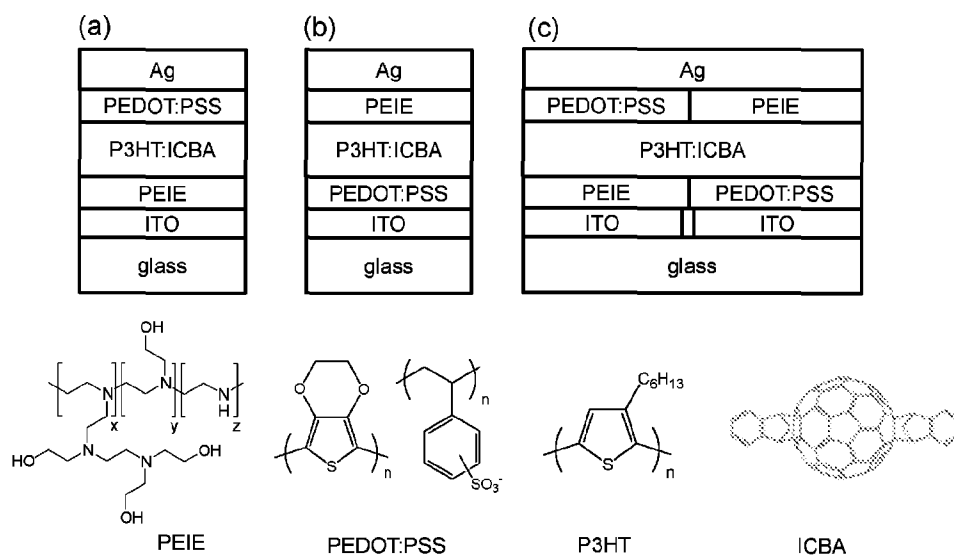


Fig.158

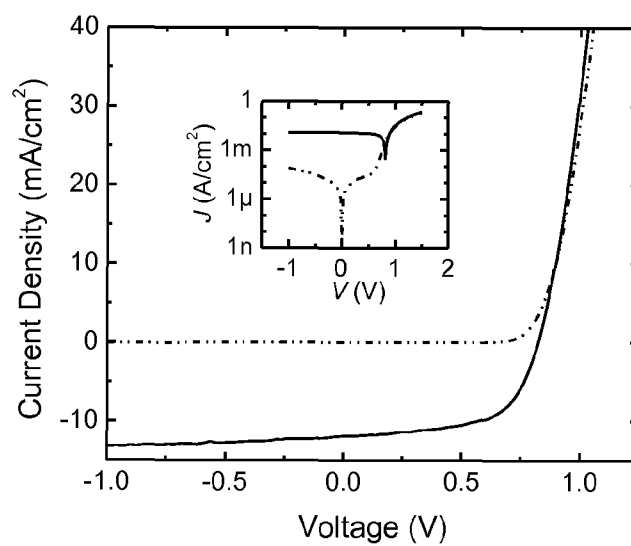


Fig.159

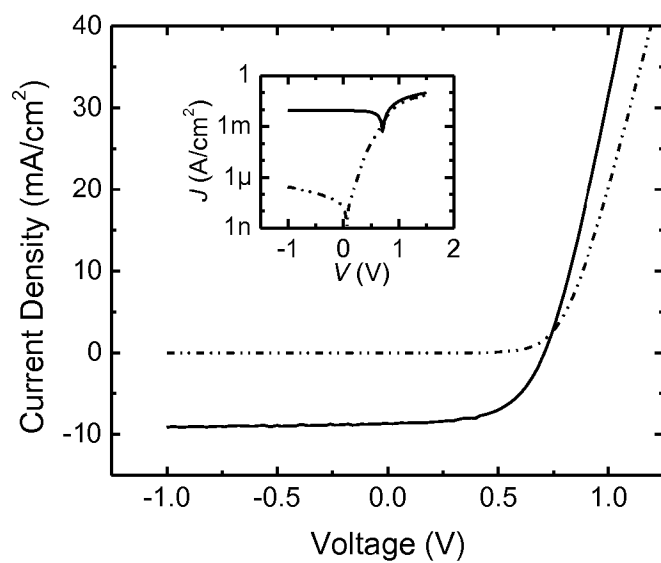


Fig.160

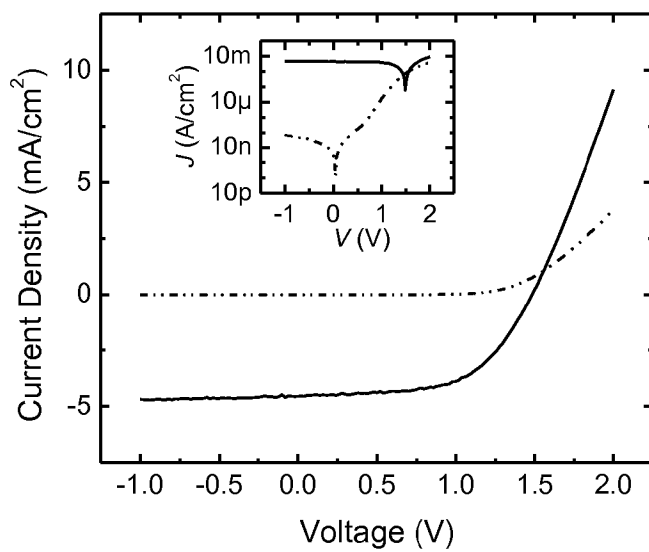


Fig.161

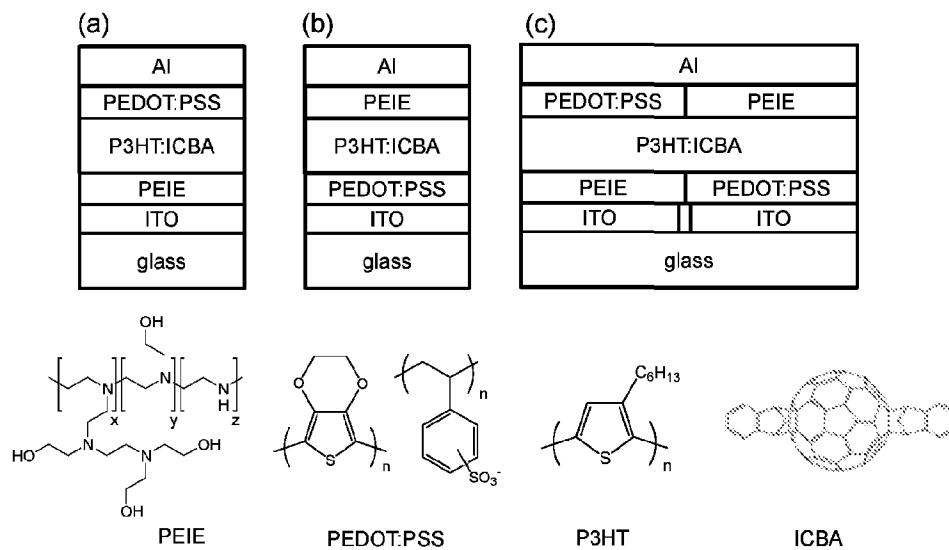


Fig.162

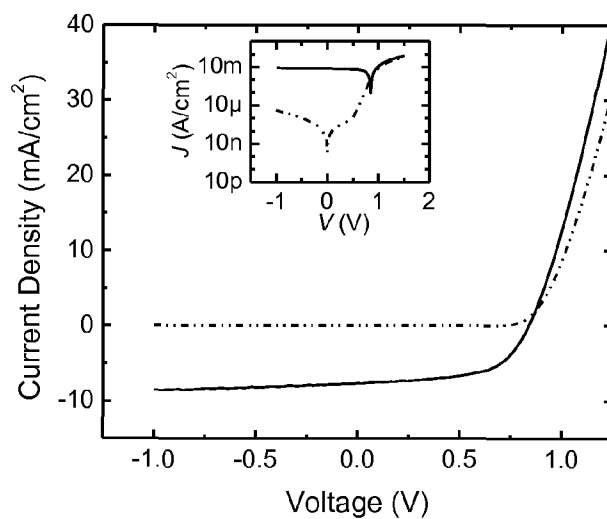


Fig.163

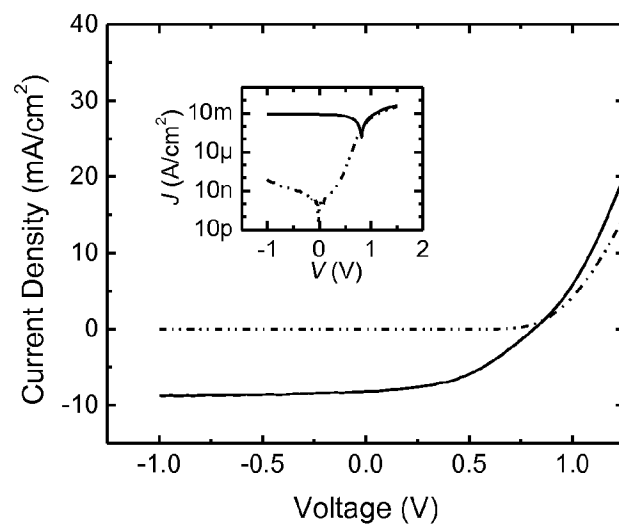


Fig.164

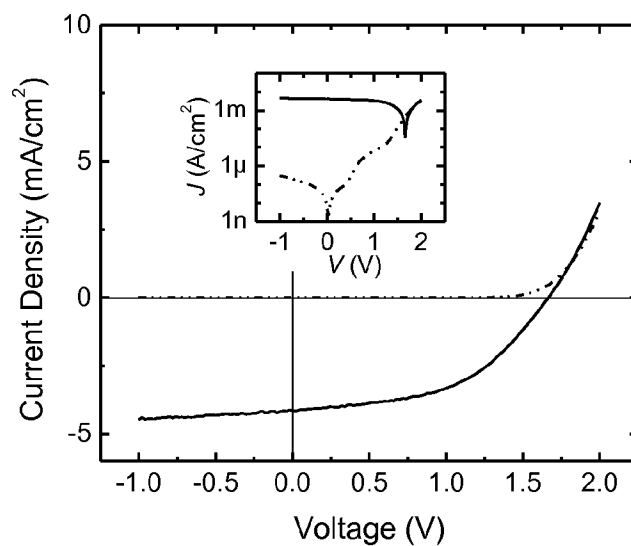


Fig.165

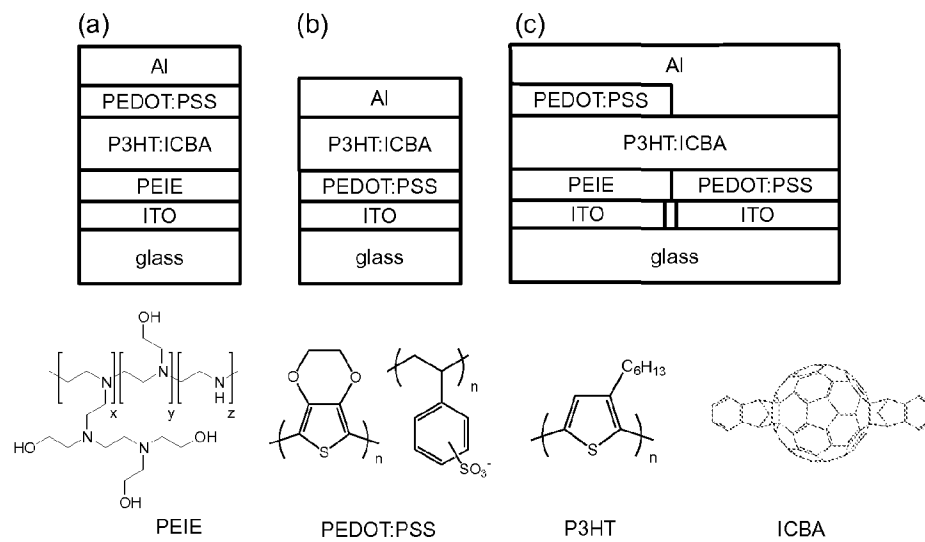


Fig.166

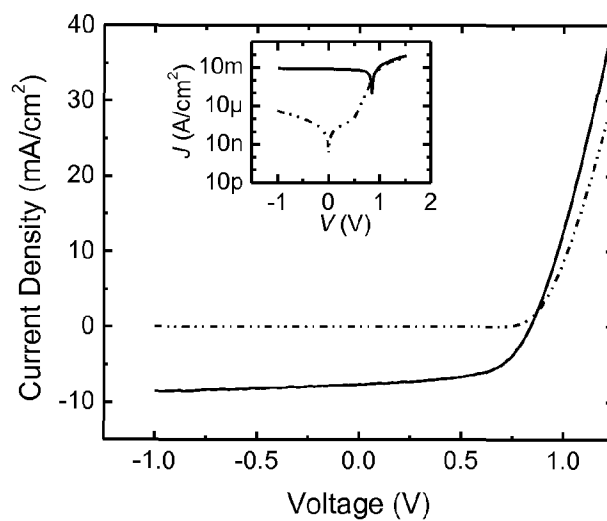


Fig.167

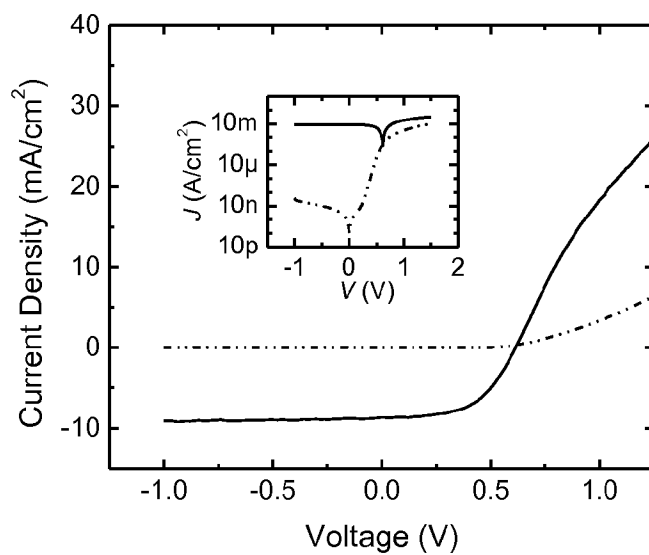


Fig.168

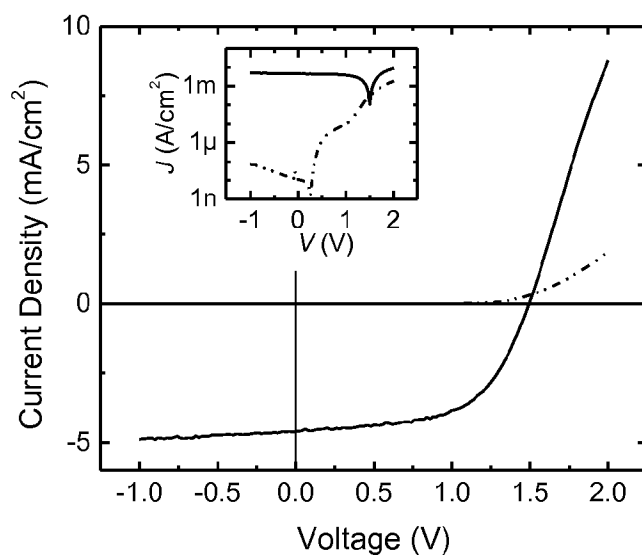


Fig.169

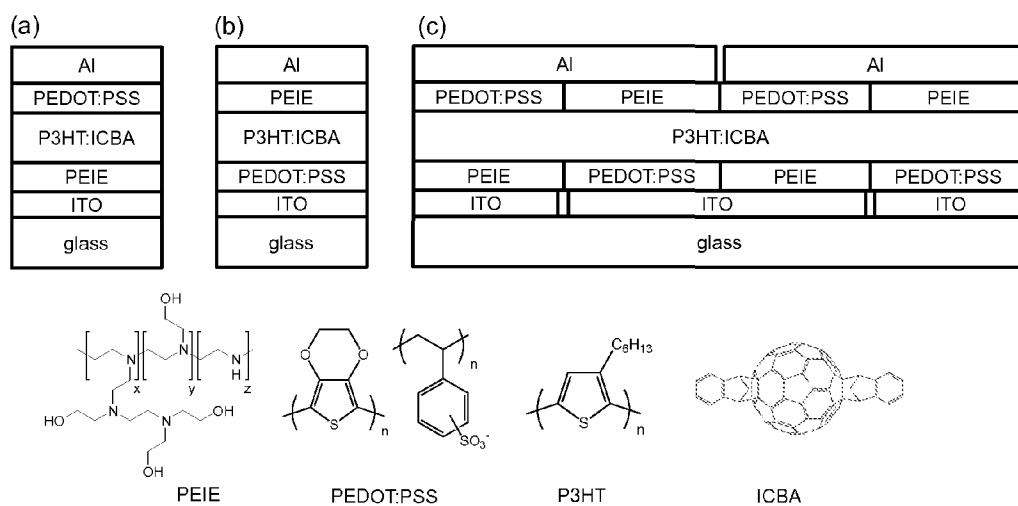


Fig.170

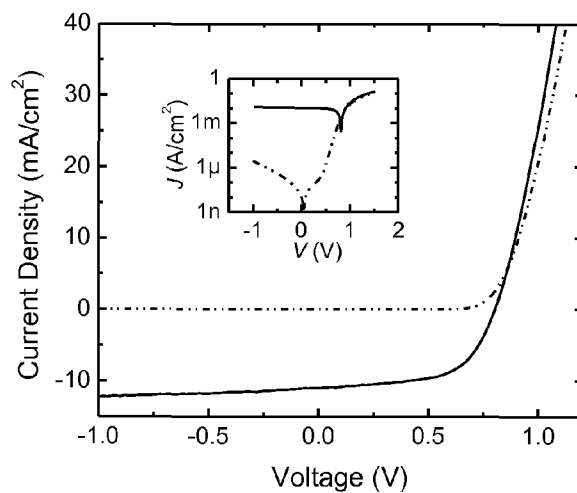


Fig.171

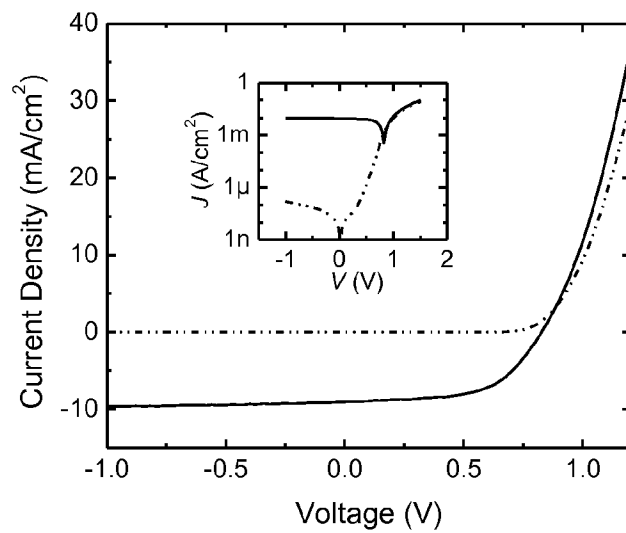


Fig.172

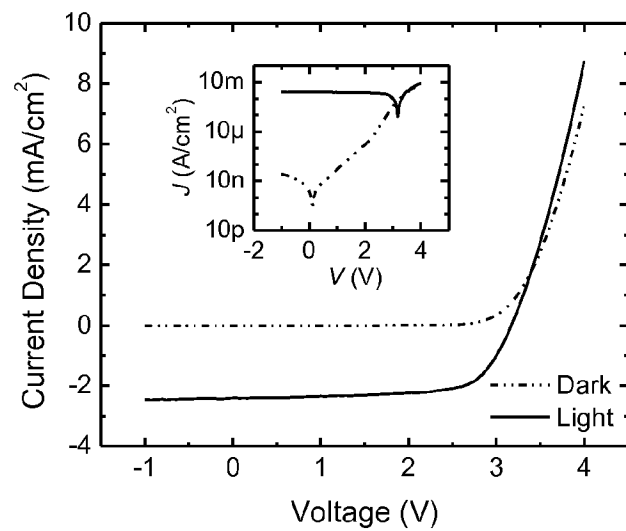


Fig.173

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SYSTEMS AND METHODS FOR PRODUCING LOW WORK FUNCTION ELECTRODES

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a U.S. National Stage of International Application No. PCT/US2012/038125, filed 12 May 2012, entitled "Systems and Methods for Producing Low Work Function Electrodes," which claims the benefit of the following U.S. provisional applications: Ser. No. 61/486,368, filed on 16 May 2011, entitled: "Reduction of the Work Function of Conductive Polymers, Metals, and Metal-Oxides by Water Soluble Polymeric Modifiers and their Application for Organic Electronics;" Ser. No. 61/591,370, filed on 27 Jan. 2012, entitled: "Photovoltaic Module with High Effective Area and Methods of Fabrication Thereof;" and Ser. No. 61/608,408, filed on 8 Mar. 2012, entitled: "Reduction of the Work Function of Conductive Polymers, Metals and Metal-Oxides by Water Soluble Polymeric Modifiers and their Applications for Organic Electronics."

The contents of each of the above-referenced applications are hereby incorporated by reference in their entirety as if presented in full.

STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH OR DEVELOPMENT

This invention was made with Government support under the following Grant Numbers: DMR-0120967, awarded by the National Science Foundation; N00014-11-1-0313, awarded by the US Navy; N00014-04-1-0120, awarded by the US Navy; and DE-SC0001084, awarded by the US Department of Energy. The Government has certain rights in the invention.

FIELD OF THE INVENTION

This invention generally relates to electrode materials, and in particular to systems and methods for producing low work function electrodes.

BACKGROUND OF THE INVENTION

Organic-based thin-film electrical and electro-optical devices, such as organic photovoltaics (OPV), organic light-emitting diodes (OLED) and organic field-effect transistors (OFET), sensors, memories, or photo-detectors, are technologies that hold great economic potential because they could lead to a new generation of electronics. Electronic devices made with these new technologies have the potential to be printed or roll processed in wide format, to have a very low-weight, and to conform to flexible substrates. However, such electronic devices often require at least one electrode having a work-function that is small enough to inject or collect electrons. In some cases, this electrode must also be optically transparent.

BRIEF SUMMARY OF THE INVENTION

Some or all of the above needs may be addressed by certain embodiments of the invention. Certain embodiments of the invention may include air-stable low-work-function electrodes and their manufacture.

According to an exemplary embodiment of the invention, a method is provided for reducing a work function of an electrode. The method includes applying, to at least a portion of

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the electrode, a solution comprising a Lewis basic oligomer or polymer; and based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

According to an exemplary embodiment of the invention, another method is provided for reducing a work function of an electrode. The method includes applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer; based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material; and applying an electrode material, to at least a portion of the ultra-thin layer, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

According to an exemplary embodiment of the invention, another method is provided for reducing a work function of an electrode. The method includes applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials; and based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

According to an exemplary embodiment of the invention, another method is provided for reducing a work function of an electrode. The method includes applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer; based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material; and applying an electrode material to at least a portion of the ultra-thin layer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials, and wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

According to an exemplary embodiment of the invention, a device is provided. The device includes a semiconductor; at least one electrode disposed adjacent to the semiconductor and configured to transport electrons in or out of the semiconductor; and an ultra-thin layer disposed between the semiconductor and the at least one electrode, the ultra-thin layer comprising an oligomer or polymer wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

Other embodiments, features, and aspects of the invention are described in detail herein and are considered a part of the claimed inventions. Other embodiments, features, and aspects can be understood with reference to the following detailed description, accompanying drawings, and claims.

BRIEF DESCRIPTION OF THE FIGURES

Reference will now be made to the accompanying figures and flow diagrams, which are not necessarily drawn to scale, and wherein:

FIG. 1 depicts the chemical structure of polyethylenimine ethoxylated (PEIE).

FIG. 2 shows the work function of indium tin oxide (ITO) modified by PEIE with different thicknesses, according to an exemplary embodiment of the invention.

FIG. 3 shows the work function of fluorine-doped tin oxide (FTO) modified by PEIE with different thicknesses, according to an exemplary embodiment of the invention.

FIG. 4 shows an ultraviolet photoelectron spectroscopy (UPS) spectra of ITO, ITO/PEIE (1.6 nm), and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention.

FIG. 5 shows X-ray photoelectron spectroscopy (XPS) spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention. The left panel shows the In 3d core level peaks and right panel shows the N 1s core level peaks

FIG. 6 shows an UPS spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention. The ITO substrate was pretreated with oxygen plasma at 600 W and 600 mTorr for 3 min.

FIG. 7 shows a XPS spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention. Left panel shows the In 3d core level peaks and right panel shows the N 1 s core level peaks. The ITO substrate was pretreated with oxygen plasma at 600 W and 600 mTorr for 3 min.

FIG. 8 show UPS spectra of ZnO and ZnO/PEIE (10 nm), according to an exemplary embodiment of the invention.

FIG. 9 show UPS spectra of PEDOT:PSS PH1000 and PEDOT:PSS PH1000/PEIE (10 nm), according to an exemplary embodiment of the invention.

FIG. 10 shows an UPS spectrum of Au/PEIE (12 nm), according to an exemplary embodiment of the invention.

FIG. 11 shows a XPS spectrum of Au/PEIE (12 nm), according to an exemplary embodiment of the invention.

FIG. 12 shows a work function of ITO/PEIE after annealed at different temperature for 30 min in air, according to an exemplary embodiment of the invention.

FIG. 13 shows a chemical structure of polyethylenimine (PEI), according to an exemplary embodiment of the invention.

FIG. 14 shows an UPS spectrum of ITO/PEI (750,000 g/mol; 10 nm), according to an exemplary embodiment of the invention.

FIG. 15 shows an UPS spectrum of ITO/PEI (25,000 g/mol; 10 nm), according to an exemplary embodiment of the invention.

FIG. 16 shows an UPS spectrum of ITO/PEI (2,000 g/mol; 10 nm), according to an exemplary embodiment of the invention.

FIG. 17 shows UPS spectra of ZnO and ZnO/PEI (25,000 g/mol; 10 nm), according to an exemplary embodiment of the invention.

FIG. 18 show UPS spectra of PEDOT:PSS PH1000 and PEDOT:PSS PH1000/PEI (25,000 g/mol), according to an exemplary embodiment of the invention.

FIG. 19 shows a work function of ITO/PEI after annealed at different temperature for 30 min in air, according to an exemplary embodiment of the invention.

FIG. 20 shows a chemical structure of PAAm, PVP, PDA-C, PVP-DMA and PBC-DMA, according to an exemplary embodiment of the invention.

FIG. 21 shows UPS spectra of ITO/PAAm (17,000 g/mol; 10 nm), according to an exemplary embodiment of the invention.

FIG. 22 shows a structure of the inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 23 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 24 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 25 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 26 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM.

FIG. 27 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 28 shows a device performances under AM 1.5 100 mW/cm² illumination after stored in ambient air in dark for different time, according to an exemplary embodiment of the invention.

FIG. 29 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 30 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 31 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 32 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 33 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 34 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 35 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 36 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 37 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 38 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 39 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 40 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 41 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 42 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 43 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 44 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 45 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 46 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 68 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 92 shows transfer characteristics of the OFET devices, according to an exemplary embodiment of the invention.

FIG. 117 shows a device structure of inverted solar cells and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

FIG. 138 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 139 shows a J-V characteristics of solar cells exposed under solar simulator for 36 min under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 140 shows a device structure of solar cells and chemical structure of PBC-DMA, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 141 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination.

FIG. 142 shows a J-V characteristics of solar cells exposed under solar simulator for 5 min under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 143 shows OPV structures, according to exemplary embodiments of the invention.

FIG. 144 depicts a flow-diagram of a method, according to an exemplary embodiment of the invention.

FIG. 145 depicts flow-diagram of another method, according to an exemplary embodiment of the invention.

FIG. 146 depicts a flow-diagram of another method, according to an exemplary embodiment of the invention.

FIG. 147 depicts a flow-diagram of another method, according to an exemplary embodiment of the invention.

FIG. 148 depicts polymer scheme for containing a guanidine group, according to an exemplary embodiment of the invention.

FIG. 149 depicts another polymer scheme containing a guanidine group, according to an exemplary embodiment of the invention.

FIG. 150 shows a work function of ITO/PEIE (10 nm) after exposed in ambient air for various cumulative exposure times, according to an exemplary embodiment of the invention.

FIG. 151 shows IPES spectrum of a layer of PEIE (10 nm) on top of Au; inset shows the energy levels of PEIE.

FIG. 152 shows a structure of tandem solar cells and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 153 shows a J-V characteristics of devices in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 154 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 155 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 156 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 157 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 158 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 159 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Ag) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 160 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/

PEIE/Ag) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 161 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 162 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 163 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 164 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 165 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 166 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 167 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 168 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 169 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 170 shows a structure of inverted and conventional reference single solar cells, a four-cell solar module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention.

FIG. 171 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 172 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 173 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

DETAILED DESCRIPTION OF THE INVENTION

Embodiments of the invention will be described more fully hereinafter with reference to the accompanying drawings, in which embodiments of the invention are shown. This invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein; rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art.

In the following description, numerous specific details are set forth. However, it is to be understood that embodiments of the invention may be practiced without these specific details. In other instances, well-known methods, structures and techniques have not been shown in detail in order not to obscure

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an understanding of this description. The term “exemplary” herein is used synonymous with the term “example” and is not meant to indicate excellent or best. References to “one embodiment,” “an embodiment,” “exemplary embodiment,” “various embodiments,” etc., indicate that the embodiment(s) of the invention so described may include a particular feature, structure, or characteristic, but not every embodiment necessarily includes the particular feature, structure, or characteristic. Further, repeated use of the phrase “in one embodiment” does not necessarily refer to the same embodiment, although it may.

As used herein, unless otherwise specified the use of the ordinal adjectives “first,” “second,” “third,” etc., to describe a common object, merely indicate that different instances of like objects are being referred to, and are not intended to imply that the objects so described must be in a given sequence, either temporally, spatially, in ranking, or in any other manner.

Certain embodiments of the invention may enable methods and devices for producing devices with electrodes that have low-work functions. Currently, so called low-work-function metals (such as calcium, magnesium, barium) may be used as electron-collecting or electrode-injection electrodes, but they easily oxidize when exposed to air. This severely limits the device stability in a regular atmosphere and hinders the potential of these technologies. On the other hand, despite having better air stability, noble metals, transparent conducting oxides and conductive polymers, typically do not have a work function that is low enough to make them efficient electron injection or collection electrodes. Hence, there is a need for new materials and processes that allow the development of low-work-function electrodes which can be processed at low cost, do not hinder the potential for good optical transparency and which have good air stability.

Exemplary embodiments of the invention relate to the use and processing of ultra-thin polymeric and other types of layers to reduce the work function of metals, noble metals, transparent metal oxides, and conducting polymers. For example, water-soluble polymeric modifiers can be processed from solution and can reduce the work function of high-work-function electrodes by up to 1.3 eV, making them good electron collecting or injecting electrodes. The modified electrodes can be used for the fabrication of organic photovoltaics (OPV), organic light-emitting diodes (OLED) and organic field-effect transistors (OFET), which show good performance as well as good air stability. Exemplary embodiments of the invention may be utilized for reducing the work function of electrodes that include one or more of an organic material, one or more polymers, a noble metal, a transparent conductive metal-oxide, graphene, metal nanorods, metal particles, metal oxide particles, or mixtures thereof.

Exemplary embodiments of the invention include methods for applying a thin-film work function modifying layer such that a device's electrode is adjacent to the thin-film work function modifying layer. In one embodiment, the thin-film work function modifying layer is applied to an electrode layer first, and then subsequent layers may be added to the thin-film. In other exemplary embodiments of the invention, the thin-film modifying layer may be applied to a semiconductor material first, and then an electrode may be applied to the thin-film work function modifying layer. In certain exemplary embodiments, the electrode may be either metal, organic material, or a combination of both. According to certain exemplary embodiments a device is provided with an electrode modified by the thin-film work function modifying layer.

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Exemplary embodiments include a method for depositing a solution of an amine polymer layer on a first electrode, thereby reducing the work function of the first electrode, and depositing at least one organic semiconducting layer on the amine polymer layer. The organic semiconducting layer may be solution or vapor deposited. In certain exemplary embodiments, the amine polymer surface modifiers are water-soluble and may be solution deposited by methods known in the art including spin-coating, dip coating, ink-jet printing, screen printing, brushing, etc. In some embodiments, the first electrode may be a conductive material chosen from, for example, noble metals, transparent conducting oxides, or organic conductors (e.g., graphene or conducting polymers). In some embodiments, the amine polymer contains only aliphatic amine functional groups. In other embodiments, the amine polymer comprises primary amine pendant groups and a second or tertiary amine backbone.

According to exemplary embodiment of the invention, the reduction of the work function of several classes of conductive materials may be up to 1.8 eV, which is superior to other methods known in the art. In some embodiments, the work function achieved by the amine polymer surface modification is stable in air at temperatures of up to 190° C., which makes it ideal for the processing of electronic and opto-electronic devices on flexible substrates. Other embodiments are organic diodes, sensors, memories, photodetectors, OPVs, OLEDs, or OFETs made by the methods as described herein.

Exemplary embodiments of the invention include an organic electronic device having a first electrode, an amine polymer layer, at least one organic semiconductor layer, and a second electrode, where the work function of the first electrode is about 1 eV lower than without the amine polymer layer. In some embodiments, the work function of the first electrode modified by the amine polymer layer is less than 4 eV. In other embodiments, the work function is less than 3.6 eV. In some embodiments, the first electrode is a noble metal, a transparent conducting oxide, graphene, or an organic conductor and the amine layer has only aliphatic amine (e.g., primary, secondary, or tertiary amine) functional groups. In certain exemplary embodiments, the organic semiconductor layer may be, for example, a vapor deposited small molecule, a solution or vapor deposited oligomer, or a solution deposited polymer.

Other embodiments include a article having: a substrate; a conducting layer comprising a noble metal, a transparent conducting metal oxide, graphene, or an organic conductor; and an amine polymer layer, where the work function of the conducting layer is at least 1 eV lower than without the amine polymer layer. The amine polymer may have primary, secondary, or tertiary amines.

Certain exemplary embodiments include an organic electronic device comprising a first organic conductor electrode, an amine polymer layer, at least one organic semiconductor layer, and a second organic conductor electrode. In other embodiments, an organic electronic device comprises a polymer substrate, a first organic conductor electrode, at least one organic semiconductor, and a second organic conductor electrode. In some embodiments, the organic electronic device further comprises an amine polymer layer between the first organic conductor electrode and the at least one organic semiconductor, where the first organic conductor electrode has a work function lower than without the amine polymer layer. The organic electronic device may be, for example, a sensor, memory, photodetector, OLED, OPV, or OFET. Other embodiments include a conformable organic photovoltaic device. The conformable device may be conformed, for example, to a roll with radius of at least 3.5 mm without

significant reduction in power conversion efficiency (PCE). The composition of the organic semiconductor layer in organic photovoltaic devices can be modified, for example, to select the optical wavelength/s of light that is/are absorbed as is known in the art.

Over the past decade, it has been recognized that the nature of the contact between molecular or polymeric semiconductors and conductive materials is complex, often difficult to understand and optimize. The work function of a conductive material can be altered by molecular adsorption which modifies the work function of the conductor through what is commonly known as the "pillow effect", making the work function dependent on the device processing conditions. Organic semiconductors typically have electron affinities with low values, typically in the range of 2-4 eV, which makes the fabrication of ohmic contacts difficult with metals and conductors that have good environmental stability. Furthermore, during the formation of an interface, chemical reactions, the diffusion of molecular species and other physical or chemical interactions can lead to the formation of reacted or diffuse interfaces where interface states and interface dipoles can severely alter the energetic alignment of the molecular orbitals of the organic semiconductors. The complexity of these interfaces underscore the difficulty of finding reliable ways to modify the work function of air-stable conducting materials that at the same time, provide an electrical interface for either the efficient collection or injection of carriers and which can be processed at low-cost.

In general, noble metals, transparent conducting oxides and conductive polymers do not have a work function that is low enough to make them efficient electron injection or collection electrodes. To date, low-work function electrodes have been realized by following two approaches. In the first approach, conductive metal-oxides with a relatively low work function are used, such as ZnO, In₂O₃, aluminum doped zinc oxide or indium zinc oxide. OPVs and metal-oxide thin-film transistors have been demonstrated following this approach, but OLEDs have not been demonstrated because common electron transport materials used have low value electron affinities compared with the typical work functions of these conductive metal-oxide electrodes.

According to exemplary embodiments of the invention, conductive layers can be modified by using an ultrathin layer of a molecule or a polymer. The ultrathin layer may create surface dipoles that, if pointing in the proper direction, can induce vacuum level shifts that reduce the work function of the underneath conductive material. One approach for reducing an electrode work function is to chemically link such dipolar molecules by using self-assembled monolayer's (SAMs). Following this approach, the work function of ITO has been increased or decreased. However, while SAM's offer a route to improve the stability of the work function modification, their processing is very slow, require specific surface chemistry that enable the reaction with the SAM molecules and their coverage density is very sensitive to the surface roughness of the conductive materials.

In another approach it was demonstrated that the work function of indium tin oxide (ITO) could be increased from 4.4 eV to 5.1 eV by treating the ITO with an acidic material such as H₃PO₄ or decreased to 3.9 eV when treated with a base such as N(C₄H₉)₄OH. Amine-containing small molecules have been used to show up to 0.9 eV reductions of the work function of ITO, Au and conducting polymers [Poly(3, 4-ethylenedioxythiophene):poly(styrenesulfonate), PEDOT: PSS]. However, in these examples, modification of the work function was either achieved with small molecules that are generally processed by physical vapor deposition techniques

that require high vacuum, or by exposing the conductors to saturated vapors of small molecules. These processing conditions are limiting and present challenges for the manufacturing of devices over large areas at low production cost. In addition, these small molecules are soluble in common organic solvents which may prevent the solution-processing on organic layers on top of them. Coverage, reproducibility and stability of the work function modification following these approaches where small-molecules are adsorbed at the surface of the conductive material remain challenging issues and are addressed by certain exemplary embodiments of the invention.

According to exemplary embodiments of the invention, a polymer may be utilized as a backbone for an electrode work-function modifying material. In an exemplary embodiment, the material may contain a guanidine group that is oligomeric or polymeric where the polymer may be linear or branched. A polymer backbone, according to this exemplary embodiment, is illustrated in FIG. 148. FIG. 149 depicts the use of as a pendent group for attaching the guanidine group, according to an exemplary embodiment of the invention. In certain exemplary embodiment, the nitrogen atoms with the guanidine group not specifically involved in bonding to the polymer may themselves be substituted with a linear, cyclic or branched alkyl or aryl or hetero aryl group, or hydrogen. Therefore A, B, C, D, E, F, G, H, I, and J may independently be selected from H, a linear cyclic, or branched alkyl group containing between 1 and 2 carbon atoms, or an aryl or heteroaryl group.

As used herein, "alkyl" refers to a straight-chain or branched saturated hydrocarbon group. Examples of alkyl groups include methyl (Me), ethyl (Et), propyl (e.g., n-propyl and iso-propyl), butyl (e.g., n-butyl, iso-butyl, sec-butyl, tert-butyl), pentyl groups (e.g., n-pentyl, iso-pentyl, neopentyl), and the like. In various embodiments, an alkyl group can have 1 to 30 carbon atoms, for example, 1-20 carbon atoms (i.e., C₁-20 alkyl group). In some embodiments, an alkyl group can have 1 to 6 carbon atoms, and can be referred to as a "lower alkyl group." Examples of lower alkyl groups include methyl, ethyl, propyl (e.g., n-propyl and iso-propyl), and butyl groups (e.g., n-butyl, iso-butyl, sec-butyl, tert-butyl). In some embodiments, alkyl groups can be substituted with 1-5 R₁ groups and R₁ is as defined herein.

As used herein, "heteroatom" refers to an atom of any element other than carbon or hydrogen and includes, for example, nitrogen, oxygen, silicon, sulfur, phosphorus, and selenium.

As used herein, "heteroaryl" refers to an aromatic monocyclic ring system containing at least one ring heteroatom selected from oxygen (O), nitrogen (N), sulfur (S), silicon (Si), and selenium (Se), or a polycyclic ring system wherein at least one of the rings present in the ring system is aromatic and contains at least one ring heteroatom. A heteroaryl group, as a whole, can have, for example, from 5 to 16 ring atoms and contain 1-5 ring heteroatoms (i.e., 5-16 membered heteroaryl group). In some embodiments, heteroaryl groups can be substituted with one or more terminal R₁ groups, where R₁ is as defined herein. Both substituted and unsubstituted heteroaryl groups described herein can comprise between 1-30, or 1-20 carbon atoms, including the R₁ substituents.

Exemplary embodiments of the invention include a method for reducing a work function of an electrode by applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer; and based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

Those skilled in the art will recognize that a Lewis base is an atomic or molecular species where the highest occupied molecular orbital (HOMO) is highly localized. Typical Lewis bases are conventional amines such as ammonia and alkyl amines. Other common Lewis bases include pyridine and its derivatives. Some of the main classes of Lewis bases include, but are not limited to: (1) amines of the formula $\text{NH}_3\text{-xRx}$ where R=alkyl or aryl; (2) pyridine and its derivatives; (3) phosphines of the formula $\text{PR}_3\text{-xAx}$, where R=alkyl, A=aryl; and (4) compounds of O, S, Se and Te in oxidation state 2, including water, ethers, and ketones.

The most common Lewis bases are anions. The strength of Lewis basicity correlates with the pKa of the parent acid. For example, acids with high pKa's give good Lewis bases, and weaker acid have a stronger conjugate base.

Examples of Lewis bases based on the general definition of electron pair donor include, but are not limited to (1) simple anions, such as H^- and F^- ; (2) other lone-pair-containing species, such as H_2O , NH_3 , HO^- , and CH_3^- ; (3) complex anions, such as sulfate; and (3) electron rich π -system Lewis bases, such as ethyne, ethene, and benzene.

Other embodiments include a method for reducing a work function of an electrode by applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer, and based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material; and applying an electrode material, to at least a portion of the ultra-thin layer, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

Other embodiments include a method for reducing a work function of an electrode by applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials, and, based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

Other embodiments include a method for reducing a work function of an electrode by applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer, and based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material; and applying an electrode material to at least a portion of the ultra-thin layer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials, and wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV.

In certain exemplary embodiments, forming the ultra-thin layer from the solution reduces the work function associated with the electrode, wherein the work function is stable in ambient air and varies by less than 20 percent over a period of greater than 10 hours after forming the ultra thin layer. In certain exemplary embodiments, forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 100 nm, preferably less than 50 nm and more preferably less than 25 nm. According to exemplary embodiments, the ultra-thin layer includes forming, on the electrode, an insulating layer having a thickness less than 10 nm and preferably less than 5 nm. According to certain exemplary embodiments, applying the solution includes applying a Lewis basic oligomer or polymer comprising nitrogen in a trivalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, applying the solution includes applying a Lewis basic oligomer or polymer comprising oxy-

gen in a divalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, applying the solution comprises applying a Lewis basic oligomer or polymer comprising sulfur in a divalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, applying the solution comprises applying the Lewis basic oligomer or polymer, wherein the Lewis basic oligomer or polymer comprises molecules having molecular weight greater than 0.1 kDa and less than 1000 kDa. In certain exemplary embodiments, applying the solution to at least a portion of the electrode comprises applying the solution to one or more of an organic material, one or more polymers, a metal, a transparent conductive metal-oxide, graphene, metal nanorods, metal particles, or metal oxide particles, or a mixture thereof. In accordance with exemplary embodiments of the invention, forming the ultra-thin layer reduces the work function associated with the electrode by forming an interfacial dipole at the interface between a surface of the electrode and a surface of the ultra-thin layer.

In an exemplary embodiment of the invention, a device is provided that includes a semiconductor; at least one electrode disposed adjacent to the semiconductor and configured to transport electrons in or out of the semiconductor; and an ultra-thin layer disposed between the semiconductor and the at least one electrode, the ultra-thin layer comprising an oligomer or polymer wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. In certain exemplary embodiments, the device's electrode work function is stable in ambient air and varies by less than 20 percent over a period of greater than 10 hours.

In certain exemplary embodiments, the device comprises one or more of a diode, a photovoltaic, a light-emitting diode, a field-effect transistor, a sensor, a memory, or a photodetector. In certain exemplary embodiments, the device comprises an organic material. In certain exemplary embodiments, the semiconductor comprises a metal-oxide. In certain exemplary embodiments, the semiconductor is an organic semiconductor. In certain exemplary embodiments, the semiconductor and the at least one electrode comprise organic material. In certain exemplary embodiments, all materials and layers of the device are organic-based.

In accordance with certain exemplary embodiments of the invention, the at least one electrode comprises one or more of an organic material, one or more polymers, a metal, a transparent conductive metal-oxide, graphene, metal nanorods, metal particles, or metal oxide particles, or a mixture thereof. In certain exemplary embodiments, the ultra-thin layer comprises an amine polymer. In certain exemplary embodiments, the amine polymer comprises aliphatic amine functional groups. In certain exemplary embodiments, the amine polymer comprises primary amine pendant groups and a second or tertiary amine backbone. In certain exemplary embodiments, the device is flexible and conformable with a bend radius of less than 8 mm. In certain exemplary embodiments, the ultra-thin layer comprises an insulating layer having a thickness less than 50 nm and preferably less than 25 nm. In other exemplary embodiments, the ultra-thin layer comprises an insulating layer having a thickness less than 10 nm and preferably less than 5 nm. In certain exemplary embodiments, the ultra-thin layer comprises nitrogen in a trivalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, the ultra-thin layer comprises oxygen in a divalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, the ultra-thin layer comprises sulfur in a divalent state bonded to carbon in a tetravalent state. In certain exemplary embodiments, the ultra-thin layer comprises an oligomer or polymer comprising molecules having molecular

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weight greater than 0.1 kDa and less than 1000 kDa. In certain exemplary embodiments, the ultra-thin layer reduces the work function associated with the at least one electrode by forming an interfacial dipole at the interface between a surface of the at least one electrode and a surface of the ultra-thin layer.

Various processes and materials may be utilized for reducing a work-function of an electrode material, according to example embodiments of the invention, and will now be described with reference to the accompanying examples, figures and tables.

An example method **14400** for reducing a work function of an electrode will now be described with reference to the flowchart of FIG. **144**. The method **14400** starts in block **14402**, and according to an example embodiment of the invention, includes applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer. In block **14404**, the method **14400** includes, based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. The method **14400** ends after block **14404**.

An example method **14500** for reducing a work function of an electrode will now be described with reference to the flowchart of FIG. **145**. The method **14500** starts in block **14502**, and according to an example embodiment of the invention, includes applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer. In block **14504**, the method **14500** includes, based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material. In block **14506**, the method **14500** includes applying an electrode material, to at least a portion of the ultra-thin layer, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. The method **14500** ends after block **14506**.

An example method **14600** for reducing a work function of an electrode will now be described with reference to the flowchart of FIG. **146**. The method **14600** starts in block **14602**, and according to an example embodiment of the invention, includes applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials. In block **14604**, the method **14600** includes, based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. The method **14600** ends after block **14604**.

An example method **14700** for reducing a work function of an electrode will now be described with reference to the flowchart of FIG. **147**. The method **14700** starts in block **14702**, and according to an example embodiment of the invention, includes applying, to at least a portion of a semiconducting material, a solution comprising a Lewis basic oligomer or polymer. In block **14704**, the method **14700** includes, based at least in part on applying the solution, forming an ultra-thin layer on a surface of at least a portion of the semiconducting material. In block **14706**, the method **14700** includes applying an electrode material to at least a portion of the ultra-thin layer, wherein the electrode comprises one or more of a metal, an organic material, or mixtures of metals and organic materials, and wherein the ultra-thin layer

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reduces the work function associated with the electrode by greater than 0.5 eV. The method **14700** ends after block **14706**.

Technical Effects

According to example embodiments, certain technical effects can be provided, such as creating certain systems and methods that reduce a work function associated with an electrode. Example embodiments of the invention can provide the further technical effects of providing systems and methods for manufacturing electronic devices that are partially or totally made from organic materials.

EXAMPLES

Examples A1-A8

Use of PEIE to Reduce the Work Function of High Work-Function Electrodes

FIG. **1** depicts the chemical structure of polyethylenimine ethoxylated (PEIE), which may be utilized to reduce the work function of high work-function electrodes, according to exemplary embodiments of the invention.

Example A1

Work Function Reduction of Indium Tin Oxide (ITO) by PEIE

FIG. **2** shows the measured work function reduction of indium tin oxide (ITO) modified by different thickness of PEIE, according to exemplary embodiments of the invention.

In experiments, Indium tin oxide (ITO)-coated glass substrates (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. For some ITO substrates, O_2 plasma treatment was applied for three minutes.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000 \text{ g/mol}$), which was dissolved in H_2O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to weight concentrations of 0.05%, 0.1%, 0.2%, 0.5% and 1%. Then these solutions were spin coated onto cleaned ITO substrates and plasma-treated ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 120°C . for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thicknesses were measured to be 1.6, 2.2, 3.8, 12, 21 nm by spectroscopic ellipsometry (J. A. Woollam Co.). The work function of the ITO/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample.

Example A2

Work Function Reduction of ITO/ZnO by PEIE

FIG. **3** shows the work function of ITO/ZnO modified by PEIE with different thicknesses, according to exemplary

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embodiments of the invention. In a study of reducing the work function of ITO/ZnO by PEIE, indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. ZnO films (200 cycles) were deposited on the cleaned ITO substrates with pulses of H_2O for 15 ms and diethylzinc for 15 ms at 200°C . using an ALD system (Savannah 100, Cambridge NanoTech, Cambridge, Mass.). The thickness of ZnO was 25 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine, 80% ethoxylated (PEIE) ($\text{Mw}=70,000 \text{ g/mol}$), which was dissolved in H_2O with a concentration of 35-40 wt % when received from Aldrich, was diluted into methoxyethanol to weight concentrations of 0.05%, 0.5% and 1%. Then these solutions were spin coated onto the ITO/ZnO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 120°C . for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO/ZnO substrates. Thicknesses were measured to be 1.4, 14 and 21 nm using spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/ZnO/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample.

Example A3

Work Function Reduction of Fluorine-Doped Tin Oxide (FTO) by PEIE

Fluorine-doped tin oxide (FTO) glass substrates (TEC-15, Hartford Glass Co. Inc) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. For some FTO substrates, O_2 plasma treatment was applied for three minutes.

Polyethylenimine, 80% ethoxylated (PEIE) ($\text{Mw}=70,000 \text{ g/mol}$), which was dissolved in H_2O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to weight concentrations of 0.05% and 0.5%. Then these solutions were spin coated onto cleaned FTO substrates and plasma-treated ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 120°C . for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thicknesses were measured to be 1.6 and 12 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the FTO/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of FTO modified by PEIE is summarized in Table 1.

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TABLE 1

Work function reduction of Fluorine-doped tin oxide (FTO) by PEIE	
Samples	Work function (eV)
Clean FTO	4.68 ± 0.04
FTO with O_2 plasma treatment	5.34 ± 0.06
FTO/PEIE (1.6 nm)	3.98 ± 0.06
FTO/PEIE (12 nm)	3.80 ± 0.06

Example A4

Work Function Reduction of Conducting Polymer PEDOT:PSS by PEIE

Microscope glasses and indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ were used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O_2 for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated microscope glass substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140°C . for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Low conductivity PEDOT:PSS 4083 (CLEVIOSTTM P VP AI 4083) was spin coated on ITO glass substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 140°C . for 10 min on a hot plate in air. Its thickness was 40 nm.

Polyethylenimine, 80% ethoxylated (PEIE) ($\text{Mw}=70,000$), which was dissolved in H_2O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to a weight concentration of 0.5%. The solution was spin coated onto glass/PH1000 and ITO glass/PEDOT:PSS 4083 samples at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 120°C . for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thicknesses were measured to be 12 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of all the samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of PEDOT:PSS modified by PEIE is summarized in Table 2.

TABLE 2

Work function reduction of PEDOT:PSS by PEIE	
Samples	Work function (eV)
PH1000	4.90 ± 0.06
PH1000/PEIE (12 nm)	3.58 ± 0.06
ITO/PEDOT:PSS 4083	5.00 ± 0.06
ITO/PEDOT:PSS 4083/PEIE (12 nm)	3.60 ± 0.06

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Example A5

Work Function Reduction of Au by PEIE

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Ti (10 nm)/Au (60 nm) was deposited on glass substrates by e-beam deposition (AXXIS, Kurt J. Lesker).

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. Then the solution was spin coated onto glass/Ti/Au at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Work function of the Au/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of Au modified by PEIE is summarized in Table 3.

TABLE 3

Work function reduction of Au by PEIE	
Samples	Work function (eV)
Au	5.26 ± 0.06
Au/PEIE(12 nm)	3.90 ± 0.06

Example A6

Work Function Reduction of Ag by PEIE

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Ag (150 nm) was deposited on glass substrates using a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker).

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. It was spin coated onto the substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. Its thickness was measured to be 10 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

Work function of the Ag/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of Ag modified by PEIE is summarized in Table 4.

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TABLE 4

Work function reduction of Ag by PEIE	
Samples	Work function (eV)
Ag	4.60 ± 0.06
Ag/PEIE(10 nm)	3.70 ± 0.06

Example A7

Work Function Reduction of Graphene by PEIE

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. It was spin coated onto the substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. Its thickness was measured to be 10 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

Work function of the Ag/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of graphene modified by PEIE is summarized in Table 5.

TABLE 5

Work function reduction of graphene by PEIE	
Samples	Work function (eV)
Graphene	4.54 ± 0.06
Graphene/PEIE(10 nm)	3.80 ± 0.10

Example A8-A12

Characterization of PEIE-Modified Electrodes by UPS and XPS

Example A8

ITO (without Plasma Treatment) Modified by PEIE

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5% or 0.05%. It was spin coated onto the ITO substrates at a speed of 5000 rpm for 1 min, yielding a thickness of 1.6 nm and 12 nm, respectively. Then these samples were transferred into an ultra-high vacuum (UHV) analysis chamber to conduct UPS and XPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV. For composition and chemical analysis the films were measured by XPS using the Al K α (1486.6 eV) photon line with a spectral resolution of 0.8 eV.

FIG. 4 shows an ultraviolet photoelectron spectroscopy (UPS) spectra of ITO, ITO/PEIE (1.6 nm), and ITO/PEIE (12 nm, according to an exemplary embodiment of the invention. FIG. 4 shows that the deposition a PEIE layer onto ITO leads to a shift of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The

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resulting work function of a 1.6 nm and 12 nm thick PEIE layers on ITO is 3.7 eV and 3.3 eV, respectively.

FIG. 5 shows XPS spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm). The left panel of FIG. 5 shows the In 3d core level peaks and right panel shows the N 1s core level peaks. When PEIE was deposited onto ITO no significant shift of the In 3d core level peak was observed as shown in FIG. 5 indicating that there is only a weak or no interaction with the ITO substrate. The N 1s core level peak at around 400 eV (FIG. 5) verifies the thin films deposition of PEIE on ITO.

Example A9

Plasma-Treated ITO Modified by PEIE

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5% or 0.05%. It was spin coated onto oxygen plasma-treated (600 W, 600 mTorr, 3 min) ITO substrates at a speed of 5000 rpm for 1 min, yielding a thickness of 1.6 nm and 12 nm, respectively. Then these samples were transferred into an UHV analysis chamber to conduct UPS and XPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV. For composition and chemical analysis the films were measured by XPS using the Al K α (1486.6 eV) photon line with a spectral resolution of 0.8 eV.

FIG. 6 shows an UPS spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention. The ITO substrate was pretreated with oxygen plasma at 600 W and 600 mTorr for 3 min. FIG. 6 shows that the deposition a PEIE layer onto ITO leads to a shifts of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The resulting work function of a 1.6 nm and 12 nm thick PEIE layers on oxygen plasma treated ITO is 3.8 eV and 3.3 eV, respectively. When PEIE was deposited onto ITO no significant shift of the In 3d core level peak was observed as shown in FIG. 7 indicating that there is only a weak or no interaction with the ITO substrate.

FIG. 7 shows a XPS spectra of ITO, ITO/PEIE (1.6 nm) and ITO/PEIE (12 nm), according to an exemplary embodiment of the invention. Left panel shows the In 3d core level peaks and right panel shows the N 1s core level peaks. The ITO substrate was pretreated with oxygen plasma at 600 W and 600 mTorr for 3 min. The N 1s core level peak at around 400 eV (FIG. 7) verifies the thin films deposition of PEIE on oxygen plasma treated ITO.

Example A10

ZnO Modified by PEIE (10 nm)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

ZnO films (200 cycles) were deposited on the cleaned ITO substrates with pulses of H₂O for 15 ms and diethylzinc for 15 ms at 200° C. using an ALD system (Savannah 100, Cam-

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bridge NanoTech, Cambridge, Mass.). The thickness of ZnO was 25 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt % when received from Aldrich, was diluted into methoxyethanol to weight concentrations of 0.5%. Then these solutions were spin coated onto the ITO/ZnO substrates at a speed of 5000 rpm for 1 min. Then these samples were annealed at 120° C. for 10 min on hotplate in nitrogen. Then these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 8 show UPS spectra of ZnO and ZnO/PEIE (10 nm), according to an exemplary embodiment of the invention. FIG. 8 shows that the deposition a PEIE layer onto ZnO leads to a shift of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The resulting work function of ZnO is 3.96 eV and ZnO/PEIE is 3.55 eV.

Example A11

PEDOT:PSS PH1000 Modified by PEIE (10 nm)

Microscope glasses and indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq were used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O₂ for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOS™ PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated on microscope glass substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to a weight concentration of 0.5%. The solution was spin coated onto glass/PH1000 at a speed of 5000 rpm for 1 min. Then these samples were annealed at 120° C. for 10 min on hotplate in nitrogen. Then these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 9 show UPS spectra of PEDOT:PSS PH1000 and PEDOT:PSS PH1000/PEIE (10 nm), according to an exemplary embodiment of the invention. FIG. 9 shows that the deposition a PEIE layer onto PEDOT:PSS PH1000 leads to a shifts of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The resulting work function of PEDOT:PSS PH1000 is 4.95 eV and PEDOT:PSS PH1000/PEIE is 3.32 eV.

Au Modified by PEIE

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. It was spin coated onto Au coated Si substrates at a speed of 5000 rpm for 1 min. Then these samples were transferred into an UHV analysis chamber to conduct UPS and XPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV. For composition and chemical analysis the films were measured by XPS using the Al K α (1486.6 eV) photon line with a spectral resolution of 0.8 eV.

FIG. 10 shows an UPS spectrum of Au/PEIE (12 nm), according to an exemplary embodiment of the invention. FIG. 10 shows that the UPS spectrum of Au/PEIE (12 nm). The photoemission onset at 17.8 eV corresponds to a work function of 3.4 eV.

FIG. 11 shows a XPS spectrum of Au/PEIE (12 nm), according to an exemplary embodiment of the invention. The XPS analysis, as shown in FIG. 11, reveals the present of Au which stems from the substrate and O, N and C which corresponds to the PEIE film.

Example A13

Thermal Stability of PEIE on ITO in Air

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq was used as the substrates. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol), which was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. PEIE films were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at different temperatures of 24, 50, 120, 140, 160, 180, 190, 200, 300, 370° C. for 30 min on hotplate in ambient air.

FIG. 12 shows a work function of ITO/PEIE after annealed at different temperature for 30 min in air, according to an exemplary embodiment of the invention. The work function of these annealed ITO/PEIE samples was measured in air using a Kelvin probe (Besocke Delta Phi). A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample.

Examples B1-B7

Use of PEI to Reduce the Work Function of High Work-Function Electrodes

FIG. 13 shows a chemical structure of polyethylenimine (PEI), according to an exemplary embodiment of the invention. The following examples show the work function reduction of and electrode coated with PEI, according to exemplary embodiments of the invention.

Work Function Reduction of ITO by PEI with Different Molecular Weight

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, from Aldrich) with different molecular weight of 2000 g/mol, 25000 g/mol and 750000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then these solutions were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thicknesses were measured to be 14, 16 and 17 nm of PEI with molecular weight of 2000 g/mol, 25000 g/mol and 750000 g/mol respectively, by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/PEI samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO by PEI with different molecular weight is summarized in Table 6.

TABLE 6

Work function reduction of ITO by PEI with different molecular weight	
Samples	Work function (eV)
ITO	4.62 \pm 0.06
ITO/PEI (Mw = 750,000 g/mol) (17 nm)	3.50 \pm 0.06
ITO/PEI (Mw = 25,000 g/mol) (16 nm)	3.40 \pm 0.06
ITO/PEI 1 (Mw = 20,000 g/mol) (14 nm)	3.40 \pm 0.06

Example B2

Work Function Reduction of ITO/ZnO by PEI (Mw=25,000 g/mol)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

ZnO films (200 cycles) were deposited on the cleaned ITO substrates with pulses of H₂O for 15 ms and diethylzinc for 15 ms at 200° C. using an ALD system (Savannah 100, Cambridge NanoTech, Cambridge, Mass.). The thickness of ZnO was 25 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then the solution

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was spin coated onto the glass/ITO/ZnO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 16 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of ITO/ZnO and ITO/ZnO/PEIE samples were measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO/ZnO by PEI is shown in Table 7.

TABLE 7

Work function reduction of ITO/ZnO by PEI (Mw = 25,000 g/mol)	
Samples	Work function (eV)
ITO/ZnO	4.30 ± 0.06
ITO/ZnO/PEI (16 nm)	3.10 ± 0.06

Example B3

Work Function Reduction of Fluorine-Doped Tin Oxide (FTO) by PEI (Mw=25,000 g/mol)

Fluorine-doped tin oxide (FTO) glass substrates (TEC-15, Hartford Glass Co. Inc) with a sheet resistivity of ~15 Ω/sq were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, Mw=25,000 g/mol, from Aldrich) with a molecular weight of 25000, was diluted into methoxyethanol to a weight concentration of 0.5%. Then the solution was spin coated onto cleaned FTO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 120° C. for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thickness of PEI was measured to be 16 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the FTO/PEI samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of FTO by PEI is shown in Table 8.

TABLE 8

Work function reduction of FTO by PEI (Mw = 25,000 g/mol)	
Samples	Work function (eV)
Clean FTO	4.66 ± 0.04
FTO/PEI (16 nm)	3.60 ± 0.06

Example B4

Work Function Reduction of Conducting Polymer PEDOT:PSS by PEI (M_w=25,000 g/mol)

Glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then

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cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O₂ for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOS™ PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated microscope glass substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. The solution was spin coated onto glass/PH1000 samples at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. Thickness of PEI was measured to be 16 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of PEDOT:PSS by PEI is shown in Table 9.

TABLE 9

Work function reduction of PEDOT:PSS by PEI (Mw = 25,000 g/mol)	
Samples	Work function (eV)
PH1000	4.90 ± 0.06
PH1000/PEI (16 nm)	3.88 ± 0.06

Example B5

Work Function Reduction of Au by PEI (Mw=25,000 g/mol)

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Ti (10 nm)/Au (60 nm) was deposited on glass substrates by e-beam deposition (AXXIS, Kurt J. Lesker).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then the solution was spin coated onto glass/Ti/Au at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEI was 16 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the Au/PEI samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of Au by PEI is shown in Table 10.

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TABLE 10

Work function reduction of Au by PEI (Mw = 25,000 g/mol)	
Samples	Work function (eV)
Au	5.20 ± 0.06
Au/PEI (16 nm)	3.94 ± 0.06

Example B6

Work Function Reduction of Ag by PEI
(Mw=25,000 g/mol)

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Ag (150 nm) was deposited on glass substrates using a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. It was spin coated onto the substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. Its thickness was measured to be 16 nm by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the Ag/PEI samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of Ag by PEI is shown in Table 11.

TABLE 11

Work function reduction of Ag by PEI (Mw = 25,000 g/mol)	
Samples	Work function (eV)
Ag	4.60 ± 0.06
Ag/PEI (16 nm)	3.60 ± 0.06

Examples B7-B11

Characterization of PEI-Modified Electrodes by UPS

Example B7

ITO Modified by PEI (Mw=750,000 g/mol)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and methanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 750,000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then these solutions were spin coated onto cleaned ITO substrates at a

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speed of 5000 rpm for 1 min. Then the samples were annealed at 100° C. for 10 min on a hotplate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 14 shows an UPS spectrum of ITO/PEI (750,000 g/mol; 10 nm), according to an exemplary embodiment of the invention. The photoemission onset at 18.07 eV corresponds to a work function of 3.15 eV.

Example B8

ITO Modified by PEI (Mw=25,000 g/mol)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and methanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25,000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then these solutions were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min. Then these samples were annealed at 100° C. for 10 min on hotplate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 15 shows an UPS spectrum of ITO/PEI (25,000 g/mol; 10 nm), according to an exemplary embodiment of the invention. The photoemission onset at 17.95 eV corresponds to a work function of 3.27 eV.

Example B9

ITO Modified by PEI (Mw=2,000 g/mol)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and methanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 2,000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then these solutions were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min. Then these samples were annealed at 100° C. for 10 min on hotplate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 16 shows an UPS spectrum of ITO/PEI (2,000 g/mol; 10 nm), according to an exemplary embodiment of the invention. The photoemission onset at 17.96 eV corresponds to a work function of 3.26 eV.

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Example B10

ZnO Modified by PEI (Mw=25,000 g/mol)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

ZnO films (200 cycles) were deposited on the cleaned ITO substrates with pulses of H_2O for 15 ms and diethylzinc for 15 ms at 200°C . using an ALD system (Savannah 100, Cambridge NanoTech, Cambridge, Mass.). The thickness of ZnO was 25 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25,000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. Then the solution was spin coated onto the glass/ITO/ZnO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100°C . for 10 min on hot plate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 17 shows UPS spectra of ZnO and ZnO/PEI (25,000 g/mol; 10 nm), according to an exemplary embodiment of the invention. FIG. 17 shows that the deposition PEI onto ZnO leads to a shifts of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The resulting work function of a ZnO is 3.96 eV and ZnO/PEI (25,000 g/mol; 10 nm) is 3.17 eV.

Example B11

PEDOT:PSS PH1000 Modified by PEI (Mw=25,000 g/mol)

Glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O_2 for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated microscope glass substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140°C . for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine (PEI, branched, from Aldrich) with a molecular weight of 25,000 g/mol, was diluted into methoxyethanol to a weight concentration of 0.5%. The solution was spin coated onto glass/PH1000 samples at a speed of 5000 rpm for 1 min. Then these samples were annealed at 100°C . for 10 min on hotplate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

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FIG. 18 show UPS spectra of PEDOT:PSS PH1000 and PEDOT:PSS PH1000/PEI (25,000 g/mol), according to an exemplary embodiment of the invention. FIG. 18 shows that the deposition PEI onto PEDOT:PSS PH1000 leads to a shifts of the photoemission onset towards lower binding energy, corresponding to a downward shift of the vacuum level, and therefore a reduction of the work function. The resulting work function of a PEDOT:PSS PH1000 is 4.95 eV and PEDOT:PSS PH1000/PEI (25,000 g/mol) is 3.16 eV.

Example B12

Thermal Stability of PEI (Mw=25,000 g/mol) on ITO in Air

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ was used as the substrates. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, Mw 25,000 g/mol, Aldrich) was diluted into methoxyethanol to the weight concentration of 0.5%. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEI was 16 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.). To test thermal stability of PEI in air, Then these samples were annealed at different temperatures of 24, 50, 120, 150, 160, 180, 200, 300°C . for 30 min on hotplate in ambient air.

FIG. 19 shows a work function of ITO/PEI after annealed at different temperature for 30 min in air, according to an exemplary embodiment of the invention.

The work function of these annealed ITO/PEI samples was measured in air using a Kelvin probe (Besocke Delta Phi). A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample.

Examples C1-H1

Use of Other Amine Containing Polymers (FIG. 20) to Reduce the Work Function of ITO

Examples C1-G1

Work Function of ITO/Modifiers Measured by Kelvin Probe

FIG. 20 shows a chemical structure of PAAm, PVP, PDA-C, PVP-DMA and PBC-DMA, according to an exemplary embodiment of the invention.

Example C1

Work Function Reduction of ITO by Poly(Allylamine) (PAAm)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water,

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acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(allylamine) (PAAm) solution (Mw=17,000 g/mol), which was dissolved in H₂O with a concentration of 20 wt. % as received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.05% and 0.5%. Then the solutions were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100° C. for 10 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thicknesses were measured to be 1.3 and 17 nm by using spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/PAAm samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO by PAAm is shown in Table 12.

TABLE 12

Work function reduction of ITO by PAAm	
Samples	Work function (eV)
ITO	4.62 ± 0.06
ITO/PAAm (1.3 nm)	3.96 ± 0.06
ITO/PAAm (17 nm)	3.80 ± 0.06

Example D1

Work Function Reduction of ITO by Polyvinylpyrrolidone (PVP)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyvinylpyrrolidone (PVP) was dissolved into deionized water with the weight concentration of 0.07%. Then the solutions were spin coated onto cleaned ITO substrates at a speed of 3000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 80° C. for 5 min on hotplate in ambient air. For thicknesses measurement, another set of samples were prepared on silicon wafer substrates prepared under the same condition on ITO substrates. Thickness of PVP was measured to be 1.0 nm by using ellipsometry.

The work function of the ITO/PVP samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function of ITO modified by PVP is shown in Table 13.

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TABLE 13

Work function reduction of ITO by PVP	
Samples	Work function (eV)
ITO	4.62 ± 0.06
ITO/PVP (1 nm)	4.20 ± 0.06

Example E1

Work Function Reduction of ITO by Poly(Diallyldimethylammonium Chloride) (PDA-C)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(diallyldimethylammonium chloride) (PDA-C), was dissolved in H₂O with a concentration of 35 wt. % when received from Aldrich. Then, it was further diluted with methoxyethanol to a concentration of 0.5 wt. %. This diluted solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PDA-C was 13 nm, as determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/PDA-C samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO by PDA-C is shown in Table 14.

TABLE 14

Work function reduction of ITO by PDA-C	
Samples	Work function (eV)
ITO	4.62 ± 0.06
ITO/PDA-C (13 nm)	4.44 ± 0.06

Example F1

Work Function Reduction of ITO by Poly(1-Vinylpyrrolidone-Co-2-Dimethylaminoethyl Methacrylate) (PVP-DMA)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(1-vinylpyrrolidone-co-2-dimethylaminoethyl methacrylate) (PVP-DMA) was dissolved in H₂O with a concentration of 19 wt. % when received from Aldrich. Then it was diluted with methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in

ambient air. The thickness of PVP-DMA was 14 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/PVP-DMA samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO by PVP-DMA is shown in Table 15.

TABLE 15

Work function reduction of ITO by PVP-DMA	
Samples	Work function (eV)
ITO	4.62 ± 0.06
ITO/PVP-DMA (14 nm)	4.20 ± 0.06

Example G1

Work Function Reduction of ITO by Poly[Bis(2-Chloroethyl) Ether-Alt-1,3-Bis[3-(Dimethylamino)Propyl]Urea] Quaternized (PBC-DMA)

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly[bis(2-chloroethyl) ether-alt-1,3-bis[3-(dimethylamino)propyl]urea] quaternized (PBC-DMA), was dissolved in H₂O with a concentration of 62 wt. % as received from Aldrich, and then diluted with methoxyethanol to a concentration of 0.5 wt. %. Then, the diluted solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 9.3 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The work function of the ITO/PBC-DMA samples was measured in air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample. Work function reduction of ITO by PBC-DMA is shown in Table 16.

TABLE 16

Work function reduction of ITO by PBC-DMA	
Samples	Work function (eV)
ITO	4.62 ± 0.06
ITO/PBC-DMA (9.3 nm)	4.16 ± 0.06

Example H1

Work Function of ITO/PAAm (10 nm) Measured by UPS

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water,

acetone, and methanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(allylamine) (PAAm) solution (Mw=17,000 g/mol), which was dissolved in H₂O with a concentration of 20 wt. % as received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. Then the solutions were spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min. Then these samples were annealed at 100° C. for 10 min on hotplate in nitrogen. Afterwards these samples were transferred into an UHV analysis chamber to conduct UPS measurements. He I (21.22 eV) radiation line from a discharge lamp was used in UPS, with an experimental resolution of 0.15 eV.

FIG. 21 shows UPS spectra of ITO/PAAm (17,000 g/mol; 10 nm), according to an exemplary embodiment of the invention. The photoemission onset at 17.73 eV corresponds to a work function of 3.49 eV.

Examples a1-a37

Use of PEIE Modified Electrodes in Organic Devices

Examples a1-a29

Use of PEIE Modified Electrodes in OPVs

Example a1

Inverted Solar Cells with ITO/PEIE (12 nm) Bottom Electrode, 80 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 22 shows a structure of the inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO_x was deposited on the ITO substrate by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the anode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes, blown dry with nitrogen.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, B119-90, Rieke Metals, FIG. 22): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 22) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 17 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 80 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

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FIG. 23 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 17.

TABLE 17

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
JWS-II-107G	0.637 ± 0.004	7.51 ± 0.13	0.65 ± 0.01	3.11 ± 0.01

Example a2

Inverted Solar Cells with ITO/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 24 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 24): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 24) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) connected to the glove box, and a MoO₃ (10 nm) and 150 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

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FIG. 25 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 18.

TABLE 18

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-150B	0.591 ± 0.004	10.24 ± 0.38	0.601 ± 0.013	3.64 ± 0.11

Example a3

Inverted Solar Cells with ITO/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode and their Air Stability

FIG. 26 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 26): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 26) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

To test the air stability of the devices, devices were kept in the dark under a regular atmosphere air up to 102 days without encapsulation and their photovoltaic performance was measured periodically by transferring the samples back into a nitrogen-filled glove box.

FIG. 27 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 19.

FIG. 28 shows a device performances under AM 1.5 100 mW/cm² illumination after stored in ambient air in dark for different time, according to an exemplary embodiment of the invention.

TABLE 19

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-150D	0.576 ± 0.004	9.57 ± 0.36	0.597 ± 0.006	3.29 ± 0.12

Example a4

Inverted Solar Cells with ITO (O₂ Plasma-Treated)/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 29 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. ITO substrates were treatment by O₂ plasma for 3 min.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, B119-90, Rieke Metals, FIG. 29): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 29) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 17 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of

10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 80 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 30 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 20.

TABLE 20

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-149G	0.558 ± 0.001	10.36 ± 0.49	0.554 ± 0.008	3.20 ± 0.15

Example a5

Inverted Solar Cells with ITO/PEIE (1.5 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 31 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.05 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 1.5 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

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Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BT19-90, Rieke Metals, FIG. 31): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) (1:0.7, weight ratio, FIG. 31) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) connected to the glove box, and a MoO₃ (10 nm) and 150 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 32 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 21.

TABLE 21

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-150A	0.590 ± 0.003	9.53 ± 0.42	0.580 ± 0.008	3.26 ± 0.16

Example a6

Inverted Solar Cells with ITO/PEIE (1.5 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 33 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.05 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 1.5 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

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Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 33): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 33) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 34 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 22.

TABLE 22

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-150C	0.587 ± 0.003	10.21 ± 0.25	0.568 ± 0.013	3.40 ± 0.10

Example a7

Inverted Solar Cells with ITO/PEIE (21 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 35 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40

wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 1 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 21 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 35): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 35) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 36 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 23.

TABLE 23

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-20C	0.546 ± 0.005	6.13 ± 0.54	0.393 ± 0.017	1.32 ± 0.17

Example a8

Inverted Solar Cells with ITO/PEIE (50 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 37 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The

patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 2 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 50 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 37): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 37) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 38 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 24.

TABLE 24

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-20D	0.544 ± 0.006	0.73 ± 0.17	0.358 ± 0.016	0.14 ± 0.03

Example a9

Inverted Solar Cells with ITO/PEIE (107 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 39 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq.}$ was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, $\text{HNO}_3:\text{HCl}$) for 5 min at 60°C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol) was dissolved in H_2O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 4 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120°C. for 10 min on hotplate in ambient air. The thickness of PEIE was 107 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N_2 -filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 39): [6,6]-phenyl C_{61} butyric acid methyl ester (PC_{60}BM , Nano-C, FIG. 39) (1:0.7, weight ratio) was filtered through $0.2\text{-}\mu\text{m}$ -pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160°C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110°C. for 10 min on hot plate in a N_2 -filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm^2 . The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N_2 -filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of $100 \text{ mW}/\text{cm}^2$ was used as the light source.

FIG. 40 shows a J-V characteristics of the solar cells in dark and under AM 1.5 $100 \text{ mW}/\text{cm}^2$ illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 25.

TABLE 25

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm^2)	FF	PCE (%)
YHZ-II-20E	0.484 ± 0.041	0.03 ± 0.02	0.314 ± 0.006	0.005 ± 0.004

Inverted Solar Cells with ITO/PEIE (5.5 nm by Dipping into 0.1 Wt % Methoxyethanol Solution for 30 s) Bottom Electrode, 200 nm P3HT: PC_{60}BM , PEDOT:PSS/Ag Top Electrode

FIG. 41 shows a device structure of inverted solar cells and chemical structure of P3HT and PC_{60}BM , according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq.}$ was used as the substrates for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, $\text{HNO}_3:\text{HCl}$) for 5 min at 60°C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol) was dissolved in H_2O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.1 wt. %. ITO substrates were then dipped into the PEIE solution for 30 sec and annealed at 120°C. for 10 min on hotplate in ambient air. The thickness of PEIE was 5.5 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N_2 -filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 41): [6,6]-phenyl C_{61} butyric acid methyl ester (PC_{60}BM , Nano-C, FIG. 41) (1:0.7, weight ratio) was filtered through $0.2\text{-}\mu\text{m}$ -pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160°C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110°C. for 10 min on hot plate in a N_2 -filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm^2 . The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N_2 -filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of $100 \text{ mW}/\text{cm}^2$ was used as the light source.

FIG. 42 shows a J-V characteristics of the solar cells in dark and under AM 1.5 $100 \text{ mW}/\text{cm}^2$ illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 26.

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TABLE 26

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156_C	0.574 ± 0.001	9.46 ± 0.34	0.608 ± 0.006	3.31 ± 0.10

Example a11

Inverted Solar Cells with ITO/PEIE (4.2 nm by Dipping into 0.1 Wt % Methoxyethanol Solution for 5 Min) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 43 shows a Device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as the substrates for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.1 wt. %. ITO substrates were then dipped into the PEIE solution for 5 min and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 4.2 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 43): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 43) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under

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illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 44 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 27.

TABLE 27

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156_D	0.577 ± 0.001	9.76 ± 0.09	0.614 ± 0.007	3.46 ± 0.03

Example a12

Inverted Solar Cells with ITO/PEIE (4.7 nm by Dipping into 0.1 Wt % Methoxyethanol Solution for 30 Min) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 45 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as the substrates for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.1 wt. %. ITO substrates were then dipped into the PEIE solution for 30 min and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 4.7 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 45): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 45) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 1000 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer

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was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 46 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 28.

TABLE 28

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156_G	0.570 ± 0.001	9.25 ± 0.30	0.589 ± 0.007	3.10 ± 0.08

Example a13

Inverted Solar Cells with ITO/PEIE (10 nm) Bottom Electrode, 200 nm P3HT:ICBA, MoO₃/Ag Top Electrode

FIG. 47 shows a device structure of inverted solar cells and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 47):Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 47) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 190 nm, measured by spectroscopic ellipsometry (J. A. Woollam Co.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) connected to the glove box, and 10 nm of MoO₃ and 150 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The com-

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pleted devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 48 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 29.

TABLE 29

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-26II_F	0.825 ± 0.001	7.84 ± 0.41	0.701 ± 0.011	4.54 ± 0.20

Example a14

Inverted Solar Cells with ITO/PEIE (10 nm) Bottom Electrode, 200 nm P3HT:ICBA, PEDOT:PSS 105D/Ag Top Electrode

FIG. 49 shows a device structure of inverted solar cells and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BI19-90, Rieke Metals, FIG. 49):Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 49) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 190 nm, measured by spectroscopic ellipsometry (J. A. Woollam Co.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were

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annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry the PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker), and 150 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 50 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 30.

TABLE 30

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-26II_G	0.827 ± 0.005	8.29 ± 0.36	0.676 ± 0.010	4.64 ± 0.19

Example a15

Inverted Solar Cells with ITO/PEIE (10 nm) Bottom Electrode, C₆₀ (45 nm)/CuPc (25 nm), MoO₃/Ag Top Electrode

FIG. 51 shows a device structure of inverted solar cells and chemical structure of CuPc and C₆₀, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as the substrates for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich. Then, it was further diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned ITO substrates at 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hotplate in ambient air. The thickness of PEIE was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker). 45 nm of C₆₀ followed by 25 nm of CuPc, 10 nm of MoO₃ and 150 nm of Ag were sequentially deposited at a base pressure of 2×10^{-7} Torr in sequence (FIG. 51). The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

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Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 52 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 31.

TABLE 31

Photovoltaic parameters of the inverted solar cells averaged over 10 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-30_A&B	0.357 ± 0.004	3.52 ± 0.06	0.578 ± 0.005	0.73 ± 0.01

Example a16

Semitransparent Inverted Solar Cells with ITO/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, CPP-PEDOT:PH-1000 Blend Top Electrode

FIG. 53 shows a device structure of semitransparent solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the diluted solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 53): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 53) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated, on each substrate, from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm, and at acceleration of 10000 rpm/s, and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000 (CLEVIOST™ PH 1000, HC Stack Inc., MA):CPP-PEDOT (CLEVIOST™ F CPP 105 DM, HC Stack Inc., MA) (3:1) was used as the top electrode by coating at a speed of 1000 rpm for 30 s in air. Then samples were transferred into a glove box, where top electrode was patterned with polydimethylsiloxane (PDMS) and annealed at 105° C. for 10 min. The effective device area was 24 mm². To improve the electrical contacts,

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silver paint was put outside the active area and onto the PEDOT:PSS blend prior to the electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 54 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 32.

TABLE 32

Photovoltaic performance of a semitransparent solar cell				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-154I#2	0.60	8.56	0.50	2.58

Example a17

Inverted Solar Cells with FTO/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode. PEIE (12 nm) Prepared on FTO by Spin Coating

FIG. 55 shows a device structure of solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Fluorine-doped tin oxide (FTO) (TEC-15) from Hartford Glass Co. Inc with a sheet resistance of 15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO_x was deposited on the cleaned FTO by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the anode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes and blown dry with nitrogen.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then diluted into methoxyethanol to a concentration of 0.5 wt. %. The diluted solution was spin coated onto cleaned FTO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 55): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 55) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)

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(CLEVIOSTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and at an acceleration of 1000 rpm/s. The samples were then annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer.

The samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 56 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 33.

TABLE 33

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156II_D	0.563 ± 0.003	8.62 ± 0.20	0.582 ± 0.014	2.84 ± 0.07

Example a18

Inverted Solar Cells with FTO/PEIE (4.2 nm by Dipping into 0.1 Wt % Methoxyethanol Solution) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS/Ag Top Electrode

FIG. 57 shows a device structure of solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Fluorine-doped tin oxide (FTO) (TEC-15) from Hartford Glass Co. Inc with a sheet resistance of 15 Ω/sq was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO_x was deposited on the cleaned FTO by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the anode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes and blown dry with nitrogen.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich and diluted into methoxyethanol to a concentration of 0.1 wt. %. The FTO substrates were dipped into the PEIE solution for 5 min and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 4.2 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 57): [6,6]-phenyl C₆₁

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butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 57) (1:0.7, weight ratio) was filtered through 0.2- μ m-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm, and at an acceleration of 10000 rpm/s, and then annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

The samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 58 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 34.

TABLE 34

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156II_E	0.573 \pm 0.002	8.36 \pm 0.26	0.595 \pm 0.008	2.85 \pm 0.08

Example a19

Inverted Solar Cells with ITO/PH1000/PEIE (12 nm)
Bottom Electrode, 200 Nm P3HT:PC₆₀BM,
MoO₃/Ag Top Electrode

FIG. 59 shows a device structure of solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ were used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by an O₂ plasma for 3 min to make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto the ITO glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s, and then annealed at 140° C. for 10 min on a hot plate in air. These resulted in

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PH1000 films with a thickness of 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin-coated onto the ITO glass/PH1000 substrate at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s, and then annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 59): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 59) (1:0.7, weight ratio) was filtered through 0.2- μ m-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s, and then annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm MoO₃ followed by a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 60 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 35.

TABLE 35

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156BB with PEIE	0.563 \pm 0.002	7.79 \pm 0.13	0.546 \pm 0.008	2.46 \pm 0.08

Example a20

Inverted Solar Cells with Glass/PH1000/PEIE (12 nm) Bottom Electrode, 200 Nm P3HT:PC₆₀BM,
MoO₃/Ag Top Electrode

FIG. 61 shows a device structure of solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water,

acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated with an O₂ plasma for 3 min to tune make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto ITO glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto glass/PH1000 at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 61): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 61) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

The samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 10 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 62 shows a J-V characteristics of the solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 36.

TABLE 36

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-156EE with PEIE	0.510 ± 0.011	7.10 ± 0.33	0.473 ± 0.011	1.77 ± 0.08

Example a21

Devices with ITO/PH1000 Bottom Electrode
(without PEIE Modification), 200 nm
P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 63 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Indium tin oxide (ITO)-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq was used as the substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O₂ for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto ITO glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 63): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 63) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s, and then annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 10 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 64 shows a J-V characteristics of the devices under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

Example a22

Devices with Glass/PH1000 Bottom Electrode
(without PEIE Modification), 200 nm
P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 65 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water,

acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated with an O₂ plasma for 3 min to tune make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOS™ PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto ITO glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 65): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 65) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

The samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 10 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 66 shows a J-V characteristics of the devices under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

Example a23

Fully Polymeric Semitransparent Inverted Solar Cells with Glass/PH1000/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, CPP-PEDOT:PH1000 Top Electrode

FIG. 67 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated with an O₂ plasma for 3 min to make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOS™ PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto the glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then, annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited

on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto glass/PH1000 at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then, annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 67): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 67) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000: CPP-PEDOT (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA) (3:1, by volume) was used as the top electrode. A 160 nm thick PEDOT:PSS blend layer was then deposited on top of the active layer by spin coating at a speed of 1000 rpm for 30 s in air. Then samples were transferred into a glove box, where top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The effective area of the device was 3.7 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 68 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 37.

TABLE 37

Photovoltaic parameters of the inverted solar cells averaged over 4 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-23A	0.568 ± 0.002	6.87 ± 0.54	0.511 ± 0.003	2.00 ± 0.15

Example a24

Fully Polymeric Devices with Glass/PH1000 Bottom Electrode (without PEIE Modification), 200 nm P3HT:PC₆₀BM, CPP-PEDOT:PH1000 Top Electrode

FIG. 69 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20

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minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated with O₂ plasma for 3 min to make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto the glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then, annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 69): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 69) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000: CPP-PEDOT (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA) (3:1, by volume) was used as the top electrode. A 160 nm thick PEDOT:PSS blend layer was then deposited on top of the active layer by spin coating at a speed of 1000 rpm for 30 s in air. Then samples were transferred into a glove box, where top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The effective area of the device was 3.7 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 70 shows a J-V characteristics of the devices in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

Example a25

Fully Polymeric Semitransparent Inverted Solar Cells with Glass/PH1000/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:ICBA, CPP-PEDOT:PH1000 Top Electrode

FIG. 71 shows a device structure and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated with an O₂ plasma for 3 min to make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto the glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then, annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited

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on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich, and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto glass/PH1000 at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then, annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 71):Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 71) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on a hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000: CPP-PEDOT (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA) (3:1, by volume) was used as the top electrode. A 160 nm thick PEDOT:PSS blend layer was then deposited on top of the active layer by spin coating at a speed of 1000 rpm for 30 s in air. Then samples were transferred into a glove box, where top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The effective area of the device was 3.7 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 72 shows a J-V characteristics of devices in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 38.

TABLE 38

Photovoltaic performance of a fully polymeric solar cell				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-23C	0.790	6.60	0.564	2.95

Example a26

Flexible Fully Polymeric Semitransparent Inverted Solar Cells with PES/PH1000/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:ICBA, CPP-PEDOT:PH1000 Top Electrode

FIG. 73 shows a device structure and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

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Polyethersulfone (PES) was used as the substrates for the flexible organic solar cells. For PH1000 patterning, a piece of polydimethylsiloxane (PDMS) was put down on half of the PES substrates as a shadow mask and then the PES substrates were treated with an O₂ plasma for 5 s.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated on PES substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140° C. for 10 min on a hot plate in air. PH1000 only wet half of the PES substrates with plasma treatment. The thickness of PH1000 was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. It was diluted into methoxyethanol to the weight concentration of 0.5%. PEIE was spin coated onto the substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 73):Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 73) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. For some some samples, active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) (1:0.7, weight ratio) was spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thicknesses of the active layer were 200 nm, measured using a profilometer.

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000: CPP-PEDOT (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA) (3:1, by volume) was used as the top electrode, prepared by spin coating at a speed of 1000 rpm for 30 s in air. Then samples were transferred into a glove box, where top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The thickness of the blend PEDOT:PSS was 160 nm. The effective area of the device was 4-7 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 74 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and performance summarized in Table 39.

FIG. 75 shows a photovoltaic performance of a device after continuous bending, according to an exemplary embodiment of the invention.

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TABLE 39

Photovoltaic parameters of the flexible fully polymeric solar cells, averaged over 3 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-34A	0.834 ± 0.001	5.63 ± 0.20	0.544 ± 0.024	2.55 ± 0.14

Example a27

Diodes with Ti/Au/PEIE (12 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 76 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

A Ti (10 nm)/Au (60 nm) electrode was deposited onto the glass substrates through a shadow mask by e-beam deposition (AXXIS, Kurt J. Lesker).

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto the glass/Ti/Au at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of P3HT (Rieke Metals, 4002-E, FIG. 76):PCBM (Nano-C, BJ091013, FIG. 76) (1:0.7, weight ratio) was spin-coated on each substrate from a 34 mg/ml chlorobenzene solution and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was measured to be 200 nm.

Samples were transferred to a vacuum thermal evaporation system (EvoVac) and 15 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm².

FIG. 77 shows J-V characteristics of the devices in dark, according to an exemplary embodiment of the invention. Current density-voltage (J-V) characteristics in the dark were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program.

Example a28

Devices with Ti/Au Bottom Electrode (without PEIE Modification), 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 78 shows a device structure and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glasses substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water,

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and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

A Ti (10 nm)/Au (60 nm) electrode was deposited onto the glass substrates through a shadow mask by e-beam deposition (AXXIS, Kurt J. Lesker).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of P3HT (Rieke Metals, 4002-E, FIG. 78):PCBM (Nano-C, BJ091013, FIG. 78) (1:0.7, weight ratio) was spin-coated on each substrate from a 34 mg/ml chlorobenzene solution and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was measured to be 200 nm.

Samples were transferred to a vacuum thermal evaporation system (EvoVac) and 15 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm².

FIG. 79 shows density-voltage (J-V) characteristics of devices in the dark, according to an exemplary embodiment of the invention. The J-V characteristics in the dark were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program.

Example a29

Inverted Tandem Solar Cells with ITO/PEIE (12 nm)
Bottom Electrode and MoO₃/Ag/PEIE (12 nm)
Recombination Layer

FIG. 80 shows a structure of tandem solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO_x was deposited on the ITO substrate by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the anode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes, blown dry with nitrogen.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % as received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto ITO glass at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of P3HT (Rieke Metals, 4002-E, FIG. 80):PCBM (Nano-C, FIG. 80) (1:0.7, weight ratio) was spin-coated on each substrate from a 17 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on hot plate inside the glove box. The thickness of the active layer was 60 nm measured by spectroscopic ellipsometry.

The substrates were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) connected to the glove box, and 10 nm MoO₃ followed by 1 nm Ag was deposited at a rate of 1-3 Å/s and a base pressure of 2×10⁻⁷

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Torr. Then, another layer of PEIE film was deposited onto the samples by spin coating from a 0.5 wt % methoxymethanol solution at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 120° C. for 10 min on hot plate in the glove box. Another layer of P3HT:PCBM was deposited on top of the second PEIE layer using the same condition used for the first layer.

Samples were then loaded into the vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) where 10 nm of MoO₃ followed by 150 nm of Ag were deposited at a rate of 1-3 Å/s through a shadow mask at a base pressure of 2×10⁻⁷ Torr to finish the device fabrication. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program.

FIG. 81 shows a J-V characteristics of devices in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 40.

To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

TABLE 40

Photovoltaic parameters of tandem solar
cells, averaged over 3 devices

Device	V _{OC} (mV)	J _{SC} (mA/cm ²)	FF	PCE (%)
JWS-II-107B	1042 ± 6	3.15 ± 0.03	0.62 ± 0.01	2.04 ± 0.02

4.4.2 Examples a30-a32

Use of PEIE Modified Electrodes in OLEDs

Example a30

Inverted Organic Light-Emitting Diodes with a
ITO/PEIE (1.6 nm) Electron-Injection Electrode

FIG. 82 shows a structure of inverted OLED and chemical structure of F8BT, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol), was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.05 wt. %. Then, the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in

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ambient air. The thickness of PEIE was 1.6 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Poly[9,9-dioctylfluorenyl-2,7-diyl-co-1,4-benzo-2{2,1'-3}-thiadiazole)] (F8BT, ADS133YE, American Dye Source, Inc., FIG. 82) was spin-coated on samples as the emissive layer from a 15 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s. Its thickness was 80 nm measured by spectroscopic ellipsometry.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), a 15 nm of MoO₃ followed by a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) and luminance-voltage (L-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 83 shows J-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

FIG. 84 shows L-EQE-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

Example a31

Inverted Organic Light-Emitting Diodes with a ITO/PEIE (12 nm) Electron-Injection Electrode

FIG. 85 shows a structure of inverted OLED and chemical structure of F8BT, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq.}$ was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol), was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Poly[9,9-dioctylfluorenyl-2,7-diyl-co-1,4-benzo-2{2,1'-3}-thiadiazole)] (F8BT, ADS133YE, American Dye Source, Inc., FIG. 85) was spin-coated on samples as the emissive layer from a 15 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s. Its thickness was 80 nm measured by spectroscopic ellipsometry.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), a 15 nm of MoO₃ followed by a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

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Current density-voltage (J-V) and luminance-voltage (L-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 86 shows J-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

FIG. 87 shows L-EQE-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

Example a32

Inverted Organic Light-Emitting Diodes with a ITO/PEIE (21 nm) Electron-Injection Electrode

FIG. 88 shows a structure of inverted OLED and chemical structure of F8BT, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq.}$ was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol), was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 1 wt. %. Then, the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 21 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Poly[9,9-dioctylfluorenyl-2,7-diyl-co-1,4-benzo-2{2,1'-3}-thiadiazole)] (F8BT, ADS133YE, American Dye Source, Inc., FIG. 88) was spin-coated on samples as the emissive layer from a 15 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s. Its thickness was 80 nm measured by spectroscopic ellipsometry.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), a 15 nm of MoO₃ followed by a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) and luminance-voltage (L-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 89 shows J-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

FIG. 90 shows L-EQE-V characteristics of the inverted OLEDs, according to an exemplary embodiment of the invention.

Use of PEIE Modified Electrodes in OFETs

Example a33

N-Channel PC₆₀BM Thin-Film Transistors Au/PEIE
(12 nm) as the Source and Drain Electrodes

FIG. 91 shows a structure of the OFET devices, according to an exemplary embodiment of the invention.

Bottom-contact bottom-gate OFETs were fabricated on heavily doped n-type silicon substrate (resistivity<0.005 Ωcm, with a wafer thickness of 525 μm from Silicon Quest Int., which also serves as gate electrode) with a 200 nm thick thermally grown SiO₂ which served as the gate dielectric. Using an e-beam deposition system (AXXIS, Kurt J. Lesker), a Ti/Au (10 nm/100 nm) metallization on the backside of the substrate was done to enhance the gate electrical contact. Then, Ti/Au (5/50 nm) bottom source and drain electrodes were deposited by e-beam deposition (AXXIS, Kurt J. Lesker) and patterned by photolithography and lift-off.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 12 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then samples were loaded in a N₂-filled glove box. A layer of [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) was deposited onto the substrates by spin coating from a 10 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 90° C. for 5 min. Its thickness was measured to be 50 nm using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). Device structure is shown in FIG. 91.

Current-voltage (I-V) characteristics of the transistors were measured in a N₂-filled glove box (O₂, H₂O<0.1 ppm) in the dark using an Agilent E5272A source/monitor unit and an Agilent 4284A LCR meter.

FIG. 92 shows transfer characteristics of the OFET devices, according to an exemplary embodiment of the invention.

FIG. 93 shows output characteristics of the OFET devices, according to an exemplary embodiment of the invention.

Example a34

N-Channel PC₆₀BM Thin-Film Transistors Au/PEIE
(1.6 nm) as the Source and Drain Electrodes

FIG. 94 shows a structure of the OFET devices, according to an exemplary embodiment of the invention.

Bottom-contact bottom-gate OFETs were fabricated on heavily doped n-type silicon substrate (resistivity<0.005 Ωcm, with a wafer thickness of 525 μm from Silicon Quest Int., which also serves as gate electrode) with a 200 nm thick thermally grown SiO₂ which served as the gate dielectric. Using an e-beam deposition system (AXXIS, Kurt J. Lesker), a Ti/Au (10 nm/100 nm) metallization on the backside of the substrate was done to enhance the gate electrical contact. Then, Ti/Au (5/50 nm) bottom source and drain electrodes were deposited by e-beam deposition (AXXIS, Kurt J. Lesker) and patterned by photolithography and lift-off.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.05 wt. %. Then, the solution was spin coated onto substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was 1.6 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then samples were loaded in a N₂-filled glove box. A layer of [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) was deposited onto the substrates by spin coating from a 10 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 90° C. for 5 min. Its thickness was measured to be 50 nm using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). Device structure is shown in FIG. 94.

Current-voltage (I-V) characteristics of the transistors were measured in a N₂-filled glove box (O₂, H₂O<0.1 ppm) in the dark using an Agilent E5272A source/monitor unit and an Agilent 4284A LCR meter.

FIG. 95 shows transfer characteristics of the OFET devices, according to an exemplary embodiment of the invention.

FIG. 96 shows output characteristics of the OFET devices, according to an exemplary embodiment of the invention.

Example a35

N-Channel PC₆₀BM Thin-Film Transistors Au/PEIE
(<1 nm) as the Source and Drain Electrodes

FIG. 97 shows a structure of the OFET devices, according to an exemplary embodiment of the invention.

Bottom-contact bottom-gate OFETs were fabricated on heavily doped n-type silicon substrate (resistivity<0.005 Ωcm, with a wafer thickness of 525 μm from Silicon Quest Int., which also serves as gate electrode) with a 200 nm thick thermally grown SiO₂ which served as the gate dielectric. Using an e-beam deposition system (AXXIS, Kurt J. Lesker), a Ti/Au (10 nm/100 nm) metallization on the backside of the substrate was done to enhance the gate electrical contact. Then, Ti/Au (5/50 nm) bottom source and drain electrodes were deposited by e-beam deposition (AXXIS, Kurt J. Lesker) and patterned by photolithography and lift-off.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.005 wt. %. Then, the solution was spin coated onto substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEIE was less than 1 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then samples were loaded in a N₂-filled glove box. A layer of [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) was deposited onto the substrates by spin coating from a 10 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 90° C. for 5 min. Its thickness was measured to be 50 nm using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). Device structure is shown in FIG. 97.

Current-voltage (I-V) characteristics of the transistors were measured in a N₂-filled glove box (O₂, H₂O<0.1 ppm) in the dark using an Agilent E5272A source/monitor unit and an Agilent 4284A LCR meter.

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FIG. 98 shows transfer characteristics of the OFET device, according to an exemplary embodiment of the invention.

FIG. 99 shows output characteristics of the OFET device, according to an exemplary embodiment of the invention.

Example a36

N-Channel PC₆₀BM Thin-Film Transistors Au as the Source and Drain Electrodes (without PEIE Modification)

FIG. 100 shows a structure of the OFET devices, according to an exemplary embodiment of the invention.

Bottom-contact bottom-gate OFETs were fabricated on heavily doped n-type silicon substrate (resistivity <0.005 Ωcm , with a wafer thickness of 525 μm from Silicon Quest Int., which also serves as gate electrode) with a 200 nm thick thermally grown SiO₂ which served as the gate dielectric. Using an e-beam deposition system (AXXIS, Kurt J. Lesker), a Ti/Au (10 nm/100 nm) metallization on the backside of the substrate was done to enhance the gate electrical contact. Then, Ti/Au (5/50 nm) bottom source and drain electrodes were deposited by e-beam deposition (AXXIS, Kurt J. Lesker) and patterned by photolithography and lift-off.

Then samples were loaded in a N₂-filled glove box. A layer of [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C) was deposited onto the substrates by spin coating from a 10 mg/ml chlorobenzene solution at a speed of 1000 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 90° C. for 5 min. Its thickness was measured to be 50 nm using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). Device structure is shown in FIG. 100.

Current-voltage (I-V) characteristics of the transistors were measured in a N₂-filled glove box (O₂, H₂O < 0.1 ppm) in the dark using an Agilent E5272A source/monitor unit and an Agilent 4284A LCR meter.

FIG. 101 shows transfer characteristics of the OFET device, according to an exemplary embodiment of the invention.

FIG. 102 shows output characteristics of the OFET device, according to an exemplary embodiment of the invention.

Example a37

Electron-Only Devices with ITO/PEIE/CuPc/Mg/Ag

FIG. 103 shows a scheme of electron-only devices, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq . was used as substrate. The ITO substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and methanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol), was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in nitrogen.

Samples were then loaded into a vacuum thermal evaporation system and a 100 nm thick Copper phthalocyanine (CuPc, 546682, Sigma-Aldrich) followed by a 100 nm of Mg/Ag was deposited through a shadow mask at a base pres-

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sure of 5×10^{-7} Torr was deposited. The effective area of the active layer was 0.11 mm². The completed devices were transferred, to a nitrogen-filled glove box for electrical measurements. Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a HP semiconductor parameter analyzer 4155A.

FIG. 104 shows a current density-voltage characteristics of electron only device with ITO and ITO/PEIE electrode, according to an exemplary embodiment of the invention. The electron-only devices (as illustrated in FIG. 103) clearly show the improved electron injection from ITO/PEIE compared to the control device without PEIE layer.

Examples b1-b11

Use of PEI Modified Electrodes in OPVs

Example B1

Inverted Solar Cells with ITO/PEI (1.5 nm; 750,000 g/mol) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 105 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq . was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched) solution (M_w=750,000 g/mol), which was dissolved in H₂O with a concentration of 50 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.05%. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 1.5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 105): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 105) (1:0.7, weight ratio) was filtered through 0.2- μm -pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm MoO₃ and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under

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illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 106 shows a J-V characteristics of solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 41.

TABLE 41

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17G	0.585 ± 0.002	8.65 ± 0.08	0.552 ± 0.009	2.79 ± 0.06

Example b2

Inverted Solar Cells with ITO/PEI (17 nm; 750,000 g/mol) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 107 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched) solution (M_w=750,000 g/mol), which was dissolved in H₂O with a concentration of 50 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 17 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 107): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 107) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm MoO₃ and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under

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illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 108 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 42.

TABLE 42

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17F	0.553 ± 0.007	8.27 ± 0.32	0.562 ± 0.007	2.57 ± 0.10

Example b3

Inverted Solar Cells with ITO/PEI (2.6 nm; 25,000 g/mol) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 109 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=25,000 g/mol, Aldrich) was diluted on methoxyethanol to a concentration of 0.1 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 2.6 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 109): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 109) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm MoO₃ and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

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FIG. 110 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 43.

TABLE 43

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17E	0.580 ± 0.002	9.06 ± 0.15	0.572 ± 0.004	3.01 ± 0.06

Example b4

Inverted Solar Cells with ITO/PEI (30 nm; 25,000 g/mol) Bottom Electrode, 200 Nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 111 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=25,000 g/mol, Aldrich) was diluted on methoxyethanol to a concentration of 1 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 30 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 111): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 111) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm-thick layer of MoO₃ and a 100 nm-thick layer of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass (AM) 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 112 shows a J-V characteristics of solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according

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to an exemplary embodiment of the invention, and device performance is summarized in Table 44.

TABLE 44

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17D	0.513 ± 0.004	5.24 ± 0.52	0.491 ± 0.004	1.32 ± 0.13

Example b5

Inverted Solar Cells with ITO/PEI (1.4 nm; 2,000 g/mol) Bottom Electrode, 200 Nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 113 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=2,000 g/mol, Aldrich), which was dissolved in H₂O with a concentration of 50 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.05 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 1.4 nm determined, by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 113): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 113) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm-thick layer of MoO₃ and a 100 nm-thick layer of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 114 shows J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an

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exemplary embodiment of the invention, and device performance is summarized in Table 45.

TABLE 45

Photovoltaic parameters of the inverted solar cells averaged over 3 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17I	0.566 ± 0.002	8.90 ± 0.20	0.542 ± 0.010	2.73 ± 0.01

Example b6

Inverted Solar Cells with ITO/PEI (14 nm; 2,000 g/mol) Bottom Electrode, 200 Nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode

FIG. 115 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=2,000 g/mol, Aldrich), which was dissolved in H₂O with a concentration of 50 wt. % when received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 14 nm determined, by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 115): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 115) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 10 nm MoO₃ and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 116 shows J-V characteristics of solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according to an

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exemplary embodiment of the invention, and device performance is summarized in Table 46.

TABLE 46

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17H	0.553 ± 0.003	7.95 ± 0.28	0.566 ± 0.008	2.49 ± 0.07

Example b7

Inverted Solar Cells with ITO/PEI (10 nm; 25,000 g/mol) Bottom Electrode, 200 Nm P3HT:ICBA, PEDOT:PSS 105D/Ag Top Electrode

FIG. 117 shows a device structure of inverted solar cells and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of 15 Ω/sq. was used as the substrate for the solar cells. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=25,000 g/mol, Aldrich) was diluted on methoxyethanol to a concentration of 0.4 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 117): Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 117) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrene-sulfonate) (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker), and a 150 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under

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illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 118 shows J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 47.

TABLE 47

Photovoltaic parameters of the inverted solar cells averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-26II_C	0.815 ± 0.001	8.16 ± 0.16	0.667 ± 0.004	4.44 ± 0.07

Example b8

Semitransparent Inverted Solar Cells with PH1000/PEI (14 nm; 25,000 g/mol) Bottom Electrode, 200 nm P3HT:PC₆₀BM, CPP-PEDOT:PH1000 Top Electrode

FIG. 119 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O₂ for 3 min to tune the surface becoming hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated ITO glass substrates at a speed of 1000 rpm for 30 s and an acceleration of 1000 rpm/s and annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on parts of the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine (PEI, branched, M_w=25,000 g/mol, Aldrich) was diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 14 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 119): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 119) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations of PH1000: CPP-PEDOT (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA) (3:1, by volume) was used as the top electrode, prepared by spin coating at a speed of 1000 rpm for 30 s in air. Then

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samples were transferred into a glove box, where top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The thickness of the blend PEDOT:PSS was 160 nm. The effective area of the device was 3.3 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 120 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 48.

TABLE 48

Photovoltaic parameters of the inverted solar cells averaged over 2 devices.				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-23D	0.570 ± 0.001	6.40 ± 0.10	0.567 ± 0.008	2.07 ± 0.05

Example b9

Fully Polymeric Semitransparent Inverted Solar Cells with PH1000/PEI (14 Nm; 25,000 g/mol) Bottom Electrode, 200 nm P3HT:ICBA, CPP-PEDOT:PH1000 Top Electrode

FIG. 121 shows a device structure of inverted solar cells and chemical structure of P3HT and ICBA, according to an exemplary embodiment of the invention.

Microscope glass substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths. Substrates were treated by O₂ plasma for 3 min to make the surface hydrophilic.

High conductivity PEDOT:PSS PH1000 (CLEVIOSTTM PH 1000, HC Stack Inc., MA) with 5% DMSO was spin coated onto ITO glass substrates at a speed of 1000 rpm for 30 s and at an acceleration of 1000 rpm/s; and then annealed at 140° C. for 10 min on a hot plate in air. Its thickness was 130 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.). A 300-nm-thick layer of SiO_x was deposited on the ITO glass/PH1000 by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the electrode.

Polyethylenimine (PEI branched, M_w=25,000 g/mol from Aldrich) was diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto glass/PH1000 at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 100° C. for 10 min on a hot plate in ambient air. The thickness of PEI was 14 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 121): Indene-C60 Bis-Adduct (ICBA, Lumtec, FIG. 121) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a

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speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on a hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

A blend of two Poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) formulations was used as the top electrode. The solution comprised PH1000 and CPP-PEDOT (CLEVIOSTTM F CPP 105 DM, HC Stack Inc., MA) at a 3:1 by volume ratio. The blended PEDOT:PSS layer was prepared by spin coating at a speed of 1000 rpm for 30 s in air. Then, the samples were transferred into a glove box, where the top electrode was patterned by polydimethylsiloxane (PDMS) and annealed at 110° C. for 10 min. The thickness of the PEDOT:PSS blend was 160 nm. The effective area of the device was 1.0 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 122 shows J-V characteristics of solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 49.

TABLE 49

Photovoltaic performance of a fully polymeric solar cell				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-23E	0.828	6.87	0.590	3.36

Example b10

Inverted Solar Cells with ITO/PEI (10 nm; 25,000 g/mol) Bottom Electrode, C₆₀ (45 nm)/Pentacene (50 nm), MoO₃/Ag Top Electrode

FIG. 123 shows a device structure of inverted solar cells and chemical structure of pentacene and C₆₀, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI branched, M_w=25,000 g/mol from Aldrich) was diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto ITO glass at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 100° C. for 10 min on a hot plate in ambient air. The thickness of PEI was 14 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) where 45 nm of C₆₀, 50 nm of pentacene, 10 nm of MoO₃ and 150 nm of Ag were sequentially deposited at a base pressure of 2×10⁻⁷ Torr.

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The effective area of the active layer was 10 mm². Device structure is shown in FIG. 123. The completed devices were transferred in a sealed container to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 124 shows J-V characteristics of the solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 50.

TABLE 50

Photovoltaic parameters of solar cells, averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-28A	0.429 ± 0.001	4.10 ± 0.16	0.404 ± 0.011	0.71 ± 0.05

Example B11

Inverted Solar Cells with ITO/PEI (10 nm; 25,000 g/mol) Bottom Electrode, C₆₀ (45 nm)/CuPc (25 nm), MoO₃/Ag Top Electrode

FIG. 125 shows a device structure of inverted solar cells and chemical structure of CuPc and C₆₀, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted 20 min. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine (PEI, branched, M_w=25,000 g/mol, Aldrich) was diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto some cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then, annealed at 100° C. for 10 min on hot plate in ambient air. The thickness of PEI was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Samples were then loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker), where 45 nm of C₆₀, 25 nm of CuPc, 10 nm of MoO₃ and 150 nm of Ag were sequentially deposited at a base pressure of 2×10⁻⁷ Torr in sequence. The effective area of the active layer was 10 mm². The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements. Device structure is shown in FIG. 125.

Current density-voltage (J-V) were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) and a calibrated photodiode integrated with a LabVIEW program.

FIG. 126 shows J-V characteristics of solar cells in the dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 51.

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TABLE 51

Photovoltaic performance of solar cells, averaged over 10 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-30_D&E	0.323 ± 0.003	3.65 ± 0.04	0.534 ± 0.006	0.63 ± 0.01

Examples C1-G1

Use of Other Amine Containing Polymers Modified Electrodes in OPVs

Examples c1-c2

Use of PAAm Modified Electrodes in OPVs

Example C1

Inverted Solar Cells with ITO/PAAm (1.3 nm)
Bottom Electrode, 200 nm P3HT:PC₆₀BM,
MoO₃/Ag Top Electrode

FIG. 127 shows a device structure of inverted solar cells and chemical structure of P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(allylamine) (PAAm) solution (M_w =17,000 g/mol), which was dissolved in H₂O with a concentration of 20 wt. % when received from Aldrich, and then further diluted into methoxyethanol to a concentration of 0.05 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 100° C. for 10 min on a hot plate in ambient air. The thickness of PAAm was 1.3 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 127): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 127) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 10 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by

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a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 128 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 52.

TABLE 52

Photovoltaic performance of solar cells, averaged over 5 devices				
Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF	PCE (%)
15 YHZ-II-17C	0.587 ± 0.001	11.65 ± 0.65	0.521 ± 0.005	3.56 ± 0.16

Example c2

Inverted Solar Cells with ITO/PAAm (17 nm)
Bottom Electrode, 200 nm P3HT:PC₆₀BM,
MoO₃/Ag Top Electrode

FIG. 129 shows a device structure of solar cells and chemical structure of PAAm, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(allylamine) (PAAm, FIG. 129) solution (M_w =17,000 g/mol), which was dissolved in H₂O with a concentration of 20 wt. % when received from Aldrich, and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 100° C. for 10 min on a hot plate in ambient air. The thickness of PAAm was 17 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 129): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 129) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 10 nm of MoO₃ followed by 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred to another nitrogen-filled glove box for electrical measurements in a sealed container.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under

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illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

FIG. 130 shows a J-V characteristics of the solar cells in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 53.

TABLE 53

Photovoltaic performance of solar cells, averaged over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-II-17B	0.575 ± 0.003	9.30 ± 0.39	0.552 ± 0.002	2.95 ± 0.11

Example D1

Use of PVP Modified Electrodes in OPVs. Inverted Solar Cells with ITO/PVP (1 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, MoO₃/Ag Top Electrode.

FIG. 131 shows a device structure of solar cells and chemical structure of PVP, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO₂ was deposited on the ITO substrate through a shadow mask by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the cathode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes, blown dry with nitrogen.

Polyvinylpyrrolidone (PVP, FIG. 131) was purchased from Aldrich and diluted in DI water to a concentration of 0.07 wt. %. This solution was spin-coated on ITO glass substrates at a speed of 3000 rpm and at an acceleration of 1000 rpm/s. The PVP film was then annealed at 80° C. for one minute.

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 131): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 131) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on a hot plate inside the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOST™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and at an acceleration of 1000 rpm/s. The samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10⁻⁷ Torr. The effective area of the active layer was 10 mm². The completed devices were transferred in a sealed container to another nitrogen-filled glove box for electrical measurements.

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Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass (AM) 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

S-shaped kink appeared in the J-V curves of devices under illumination. To remove the kink, devices were kept and exposed under the Oriel lamp with AM 1.5 filter for 20 min inside the N₂-filled glove box. After soaking, J-V characteristics of the devices were measured again both in the dark and under illumination of the above-mentioned light source.

FIG. 132 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 133 shows a J-V characteristics of solar cells exposed under solar simulator for 20 min under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 54.

TABLE 54

Performance of solar cells exposed under solar simulator for 20 min, over 5 devices				
Sample	V _{OC} (mV)	J _{SC} (mA/cm ²)	FF	PCE (%)
JWS-II-45F_20minUV	581 ± 6	9.04 ± 0.34	0.59 ± 0.01	3.10 ± 0.14

Example e1

Use of PDA-C Modified Electrodes in OPVs, Inverted Solar Cells with ITO/PDA-C (13 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS(CPP 105 D)/Ag Top Electrode

FIG. 134 shows a device structure of solar cells and chemical structure of PDA-C, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(diallyldimethylammonium chloride) (PDA-C, FIG. 134) was dissolved in H₂O with a concentration of 35 wt. % when received from Aldrich, and then, further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PDA-C was 13 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 134): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 134) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml

chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then annealed at 160° C. for 10 min on a hot plate inside the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOST™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and at an acceleration of 1000 rpm/s. Samples were then annealed at 110° C. for 10 min on a hot plate inside a N₂-filled glove box to dry PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), and a 100 nm of Ag was deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred in a sealed container to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

S-shaped kink appeared in the J-V curves of devices under illumination. To remove the kink, devices were kept and exposed under the Oriel lamp with AM 1.5 filter for 150 min inside the N₂-filled glove box. After soaking, J-V characteristics of the devices were measured again both in the dark and under illumination of the above-mentioned light source.

FIG. 135 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention.

FIG. 136 shows a J-V characteristics of solar cells exposed under solar simulator for 150 min under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 55.

TABLE 55

Performance of solar cells exposed under solar simulator for 150 min, over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-154C	0.557 ± 0.001	9.01 ± 0.53	0.492 ± 0.017	2.47 ± 0.23

Example fl

Use of PVP-DMA Modified Electrodes in OPVs, Solar Cells with ITO/PVP-DMA (14 nm) Bottom Electrode, 200 nm P3HT:PC₆₀BM, PEDOT:PSS(CPP 105 D)/Ag Top Electrode

FIG. 137 shows a device structure of solar cells and chemical structure of PVP-DMA, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then

cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly(1-vinylpyrrolidone-co-2-dimethylaminoethyl methacrylate) (PVP-DMA, FIG. 137) was dissolved in H₂O with a concentration of 19 wt. % when received from Aldrich and further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PVP-DMA was 14 nm determined by spectroscopic ellipsometry (J. A. Woolam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, BJ19-79, Rieke Metals, FIG. 137): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 137) (1:0.7, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and at an acceleration of 10000 rpm/s; and then, annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOST™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and at an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.) where 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred in a sealed container to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

S-shaped kink appeared in the J-V curves of devices under illumination. To remove the kink, devices were kept and exposed under the Oriel lamp with AM 1.5 filter for 36 min inside the N₂-filled glove box. After soaking, J-V characteristics of the devices were measured again both in the dark and under illumination of the above-mentioned light source.

FIG. 138 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 56.

TABLE 56

Performance of solar cells exposed under solar simulator for 36 min, over 5 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-154E	0.557 ± 0.001	9.28 ± 0.30	0.600 ± 0.010	3.10 ± 0.07

Use of PVP-DMA Modified Electrodes in OPVs,
Inverted Solar Cells with ITO/PBC-DMA (9.3 nm)
Bottom Electrode, 200 nm P3HT:PC₆₀BM,
PEDOT:PSS(CPP 105 D)/Ag Top Electrode

FIG. 140 shows a device structure of solar cells and chemical structure of PBC-DMA, P3HT and PC₆₀BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω /sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 5 min at 60° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Poly[bis(2-chloroethyl) ether-alt-1,3-bis[3-(dimethylamino)propyl]urea]quaternized (PBC-DMA, FIG. 140) was dissolved in H₂O with a concentration of 62 wt. % as received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto cleaned ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s; and then annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PBC-DMA was 9.3 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then the substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, B119-79, Rieke Metals, FIG. 140): [6,6]-phenyl C₆₁ butyric acid methyl ester (PC₆₀BM, Nano-C, FIG. 140) (1:0.7, weight ratio) was filtered through 0.2- μ m-pore PTFE filters and spin-coated on each substrate from a 34 mg/ml chlorobenzene solution at a speed of 700 rpm and an acceleration of 10000 rpm/s and annealed at 160° C. for 10 min on hot plate in the glove box. The thickness of the active layer was 200 nm, measured using a profilometer (Dektak 6M Stylus, Veeco, Plainview, N.Y.).

Samples were transferred out of the glove box and a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (CLEVIOS™ F CPP 105 DM, HC Stack Inc., MA, 90 nm) was spin coated on top of the active layer at a speed of 5000 rpm and at an acceleration of 1000 rpm/s. Samples were annealed at 110° C. for 10 min on hot plate in a N₂-filled glove box to dry PEDOT:PSS layer. Its thickness was 90 nm.

Samples were then loaded into a vacuum thermal evaporation system (EvoVac, Angstrom Engineering Inc.), where 100 nm of Ag were deposited through a shadow mask at a base pressure of 2×10^{-7} Torr. The effective area of the active layer was 10 mm². The completed devices were transferred in a sealed container to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

S-shaped kink appeared in the J-V curves of devices under illumination (FIG. 141). To remove the kink, devices were kept and exposed under the Oriel lamp with AM 1.5 filter for 5 min inside the N₂-filled glove box. After soaking, J-V

characteristics of the devices were measured again both in the dark and under illumination of the above-mentioned light source.

FIG. 141 shows a J-V characteristics of newly-fabricated solar cells under AM 1.5 100 mW/cm² illumination.

FIG. 142 shows a J-V characteristics of solar cells exposed under solar simulator for 5 min under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance after light soaking is summarized in Table 57.

TABLE 57

Performance of solar cells exposed under solar simulator for 5 min, over 3 devices				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
YHZ-I-154A	0.571 \pm 0.001	9.41 \pm 0.27	0.574 \pm 0.006	3.10 \pm 0.05

Example h1

OPV Structures of Some Embodiments

FIG. 143 shows OPV structures, according to exemplary embodiments of the invention.

An important aspect enabled by semitransparent OPVs, is that the back metal reflector, typically used to collect carriers and reflect light into the active layer, could become independent from the OPV device. This makes its electrical properties irrelevant for the operation of the solar cell. With this, new possibilities for the optical design of back reflectors arise, since diffuse reflectors with large surface roughness could be used. These types of reflectors are used in crystalline-Si cells, but are not applicable to thin-film PVs since fabrication becomes extremely challenging due to the formation of pinholes and defects.

FIG. 143 shows an OPV geometry embodiment where a semitransparent OPV is fabricated on top of a first transparent substrate with a high conductivity grid, embedded or deposited, and covered with a second transparent substrate with a high conductivity grid, embedded or deposited. In such geometry, a first substrate, which in some embodiments is flexible, will have a metal-grid embedded or deposited on a first surface and a diffuse or specular reflector on its second surface. The reflector could be made of a metal or another material that reflects light back into the polymeric active area and improves the OPV collection efficiency. The OPV device consist of a first transparent electrode deposited on the first surface of the first transparent substrate and is modified by a thin amine-containing polymer layer such as, for example, the ones described herein. The first transparent electrode can comprise a metal, transparent conducting oxide or conductive polymer. A polymer active layer is then deposited on top of said amine-containing polymer layer and first transparent electrode. A second transparent electrode is then deposited on top of the polymer active layer. The second transparent electrode can comprise a metal, transparent conducting oxide or conductive polymer. A high conductivity grid is then deposited on top of the second transparent electrode or is deposited or embedded on a second semitransparent substrate. Finally, the second transparent substrate is then laminated, deposited or attached to the second transparent electrode. Those skilled in the art would understand that both transparent substrates

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will, in some embodiments, be light-weight, flexible, have good barrier properties to oxygen and water, and have a low cost.

Example i1

Air-Stability of ITO Modified by PEIE (10 nm)

Indium tin oxide (ITO)-coated glass substrates (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$ were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Each ultrasonic bath lasted for 20 minutes. Nitrogen was used to dry the substrates after each of the last three baths.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol), which was dissolved in H_2O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. It was spin coated onto the substrates at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Then these samples were annealed at 100°C . for 10 min on hotplate in ambient air. Its thickness was measured to be 10 nm by spectroscopic ellipsometry (J. A. Woollam Co.). The work function of the ITO/PEIE samples was measured in air after cumulative exposure times in ambient air using a Kelvin probe (Besocke Delta Phi) and averaged over three locations. A highly ordered pyrolytic graphite (HOPG) sample with a work function of 4.5 eV was used as the reference sample.

FIG. 150 shows a work function of ITO/PEIE (10 nm) after exposed in ambient air for various cumulative exposure times, according to an exemplary embodiment of the invention.

Example j1

Characterization of PEIE by IPES

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol), which was dissolved in H_2O with a concentration of 35-40 wt. % when received from Aldrich, was diluted into methoxyethanol to the weight concentration of 0.5%. It was spin coated onto Au coated Si substrates at a speed of 5000 rpm for 1 min. Then these samples were transferred into an UHV analysis chamber to conduct inverse photoemission spectroscopy (IPES). IPES was carried out in the isochromat mode, with a resolution of 0.45 eV. Measurements were repeated two or three times per sample.

FIG. 151 shows an IPES spectrum of Au/PEIE (12 nm), according to an exemplary embodiment of the invention. FIG. 151 shows the energy levels of PEIE extracted from IPES and UPS measurements. The large band gap of 6.2 eV indicates that PEIE is an insulator.

Example k1

Inverted Tandem Solar Cells with ITO/PEIE (10 nm) Bottom Electrode and PEDOT:PSS/PEIE (10 nm) Recombination Layer

FIG. 152 shows a structure of tandem solar cells and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC_{60}BM , according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of $\sim 15 \Omega/\text{sq}$. was used as substrate. The substrates were cleaned in an ultrasonic bath of detergent

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water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. A 300-nm-thick layer of SiO_x was deposited on the ITO substrate by e-beam deposition (AXXIS, Kurt J. Lesker) to pattern the anode. Next, the substrates were ultrasonicated in isopropanol for 10 minutes, blown dry with nitrogen.

Polyethylenimine, 80% ethoxylated (PEIE) ($M_w=70,000$ g/mol) was dissolved in H_2O with a concentration of 35-40 wt. % as received from Aldrich and then further diluted into methoxyethanol to a concentration of 0.5 wt. %. Then, the solution was spin coated onto ITO glass at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s and annealed at 120°C . for 10 min on hot plate in ambient air. The thickness of PEIE was 10 nm, determined by spectroscopic ellipsometry (J. A. Woollam Co.).

Then, the substrates were transferred into a N_2 -filled glove box. The first active layer of P3HT (Rieke Metals, 4002-E, FIG. 152):ICBA (Lumtec, FIG. 152) (1:1, weight ratio) was spin-coated on each substrate from a 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s; and then annealed at 160°C . for 10 min on hot plate inside the glove box. The thickness of the active layer was 200 nm measured by spectroscopic ellipsometry.

After samples cooled down, they were transferred to ambient air and treated by with an O_2 plasma treatment for 1 s, to make the surface hydrophilic. PEDOT:PSS PH1000 was spin coated on top of the active layer at a speed of 4000 rpm for 1 min. Prior to spin coating, 5% (by weight) dimethyl sulfoxide was added into the as received PEDOT:PSS PH1000 (Heraeus) to enhance its conductivity. During spin coating, a piece of PDMS was coated onto the P3HT:ICBA layer, on the area without ITO. Samples were annealed at 100°C . for 10 min on a hot plate in a N_2 -filled glove box. The thickness of the PEDOT:PSS PH1000 layer was 50 nm by spectroscopic ellipsometry. PH1000 was coated with another PEIE layer (10 nm) following the same conditions previously described.

Then, the substrates were transferred back into a N_2 -filled glove box. Poly[(4,8-bis-(2-ethylhexyloxy)-benzo[1,2-b:4,5-b'] dithiophene)-2,6-diyl-alt-(4-(2-ethylhexanoyl)-thieno[3,4-b]thiophene))-2,6-diyl](PBDTTT-C, Solarmer):phenyl-C61-butyric acid methyl ester (PCBM, Nano-C) (1:1.5, weight ratio) was dissolved in a chlorobenzene:1,8 diiodooctane (97:3, v/v) solution with a total concentration of 25 mg/ml for the second layer. The second active layer of PBDTTT-C:PCBM was deposited by spin-coating at 1000 rpm for 20 s. The thickness of PBDTTT-C:PCBM was estimated to be around 100 nm by ellipsometry.

Samples were then loaded into the vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) where 10 nm of MoO_3 followed by 150 nm of Ag were deposited at a rate of $1\text{-}3 \text{ \AA/s}$ through a shadow mask at a base pressure of 2×10^{-7} Torr to finish the device fabrication. The effective area of the active layer was 10 mm^2 . The completed devices were transferred, in a sealed container, to another nitrogen-filled glove box for electrical measurements.

Current density-voltage (J-V) characteristics were measured inside the N_2 -filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program.

FIG. 153 shows a J-V characteristics of devices in the dark and under AM 1.5 100 mW/cm^2 illumination, according to an exemplary embodiment of the invention, and device performance is summarized in Table 58.

To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an intensity of 100 mW/cm² was used as the light source.

TABLE 58

Photovoltaic parameters of tandem solar cells, averaged over 25 devices				
Device	V _{OC} (mV)	J _{SC} (mA/cm ²)	FF	PCE (%)
Tandem solar cell	1480 ± 2	7.4 ± 0.4	0.68 ± 0.01	7.5 ± 0.7

Examples 11-15

Use of PEIE in Photovoltaic Modules with High Area Efficiency

Exemplary embodiments of the invention include a solar cell module. The solar cell module includes a plurality of solar cell elements that include a plurality of electrodes, a photoactive layer, and a plurality of interlayers. The interlayers are disposed between the photoactive layer and at least a portion of the electrodes, where each solar cell element has an associated polarity, and adjacent solar cell elements are arranged with alternating polarity, where the polarity is based at least in part on an arrangement and orientation of the plurality of interlayers. In an exemplary embodiment, the electrodes include a plurality of first electrodes electrically connecting x(N) and x(N+1) adjacent solar cell elements in a first plane; and the electrodes further include a plurality of second electrodes electrically connecting x(N+1) and x(N+2) adjacent solar cell elements in a second plane; wherein x and N are integers.

In an exemplary embodiment, the plurality of interlayers associated with the solar cell module are selectively patterned to control a work function associated with the plurality of first electrodes or the plurality of second electrodes. According to exemplary embodiments, the plurality of interlayers include at least an ultra-thin layer disposed between the photoactive layer and at least a portion of the electrodes, and the ultra-thin layer reduces the work function associated with the electrode by greater than 0.5 eV. According to exemplary embodiments, the work function is stable in ambient air and varies by less than 20 percent over a period of greater than 10 hours after forming the plurality of interlayers.

In one exemplary embodiment, the plurality of interlayers include one or more insulating layers having thickness less than 50 nm and preferably less than 25 nm. In another exemplary embodiment, the plurality of interlayers include one or more insulating layers having thickness less than 10 nm and preferably less than 5 nm.

In accordance with exemplary embodiments of the invention, the solar cell module includes a plurality of interlayers that are formed from a solution comprising a Lewis basic oligomer or polymer. In one exemplary embodiment, the Lewis basic oligomer or polymer includes nitrogen in a trivalent state bonded to carbon in a tetravalent state. In another exemplary embodiment, the Lewis basic oligomer or polymer includes oxygen in a divalent state bonded to carbon in a tetravalent state. In another exemplary embodiment, the Lewis basic oligomer or polymer includes sulfur in a divalent state bonded to carbon in a tetravalent state.

In accordance with exemplary embodiments of the invention, the solar cell module includes a plurality of interlayers

that are formed from a solution comprising a Lewis basic oligomer or polymer with molecules having molecular weight greater than 0.1 kDa and less than 1000 kDa.

In an exemplary embodiment, the solar cell module includes a plurality of interlayers that are disposed adjacent to one or more of an organic material, one or more polymers, a metal, a transparent conductive metal-oxide, graphene, metal nanorods, metal particles, or metal oxide particles, or a mixture thereof. According to an exemplary embodiment, the plurality of interlayers include one or more ultra-thin layer that reduce the work function associated with the electrode by forming an interfacial dipole at the interface between a surface of the electrode and a surface of the ultra-thin layer.

Example 11

Two-Cell Solar Module Comprising a P3HT:ICBA Active Layer with Solvent Annealing and Pre-Annealing, PEDOT:PSS and PEIE as Two Interlayers and Al as Top Electrode

FIG. 154 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC₆₀BM, according to an exemplary embodiment of the invention

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 10 min at 75° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. Then the substrates were treated by oxygen plasma for 2 min.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a weight concentration of 0.2 wt. % and 0.02%.

For reference single solar cells with inverted, PEIE (0.2 wt. %) was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, Rieke Metals):Indene-C60 Bis-Adduct (ICBA, Lumtec) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s and an acceleration of 10000 rpm/s. Then the active layers were treated through solvent annealing for 1 hour and thermally annealed at 150° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured by spectroscopic ellipsometer (J. A. Woollam Co.).

After samples cooled down for 20 min in the glove box, they were transferred in ambient air and treated by O₂ plasma treatment for 1 s to tune the surface hydrophilic. Then a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) (HTL Solar formulation mixed with 10 volume % CPP105D) was spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEDOT:PSS layer was about 40 nm.

For the reference single solar cells with conventional structures, PEDOT:PSS 4083 was spin coated onto ITO substrates

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at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEDOT:PSS was 40 nm. The P3HT:ICBA active layers were prepared in the same condition as prepared in the inverted single cells. Then a thin layer of PEIE was spin coated on top of plasma-treated active layer from a weight concentration of 0.02% at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s.

For a solar cell module comprising a first solar cell with an inverted structure and a second solar cell with a conventional structure an ITO substrate was etched with a gap about 1.7 mm to define two ITO electrodes. Then PEIE (0.2%) and PEDOT:PSS 4083 were spin coated onto the two parts of ITO at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s one after the other. A narrow (0.5-1 mm) polydimethylsiloxane (PDMS) was coated onto the gap between the patterned ITO electrodes prior to spin coating of PEIE and PEDOT:PSS, to selectively pattern PEIE and PEDOT:PSS. PDMS was peeled-off and the samples were annealed at 120° C. for 10 min on a hot plate in ambient air.

The active layers of P3HT:ICBA were prepared in the same condition as prepared for single solar cells. A thin layer of PEIE (from a 0.02 wt. % solution) and a layer of PEDOT:PSS (HTL Solar+10% v/v CPP 105D) were spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Prior to spin coating, the active layer was treated by an O₂ plasma for 1 s and PDMS was coated on the active layer to selectively patterned PEIE and PEDOT:PSS.

All the samples were transferred into a N₂-filled glove box and annealed on a hot plate at 110° C. for 10 min to dry PEIE and crosslink PEDOT:PSS HTL-CPP. All samples were loaded into a vacuum thermal evaporation system (SPEC-TROS, Kurt J. Lesker) and a layer of Al (150 nm) was deposited onto all of the samples through a shadow mask. The area of the solar cell module devices was about 18 mm² not including the gap between the ITO electrodes having an area of 1.7 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an irradiance of 100 mW/cm² was used as the light source.

FIG. 155 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 59.

FIG. 156 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 59.

FIG. 157 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 59.

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TABLE 59

Photovoltaic performance of inverted single cells and conventional single cells (averaged over 2 devices) and module devices (averaged over 2 devices); Data in parentheses are calculated with the total area including the gap (no ITO).				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
Inverted single	0.82 ± 0.01	10.2 ± 0.2	0.61 ± 0.01	5.1 ± 0.1
Conventional single	0.74 ± 0.01	8.4 ± 0.1	0.57 ± 0.01	3.6 ± 0.1
Module	1.55 ± 0.01	4.3 ± 0.1 (4.0 ± 0.1)	0.61 ± 0.01	4.1 ± 0.1 (3.8 ± 0.1)

Example 12

Two-Cell Solar Module Comprising a P3HT:ICBA Active Layer with Solvent Annealing and Pre-Annealing, PEDOT:PSS and PEIE as Two Interlayers and Ag as Top Electrode

FIG. 158 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC60BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 10 min at 75° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. Then the substrates were treated by oxygen plasma for 2 min.

Polyethylenimine, 80% ethoxylated (PEIE) (M_w=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a weight concentration of 0.2 wt. % and 0.02%.

For reference single solar cells with inverted, PEIE (0.2 wt. %) was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, Rieke Metals):Indene-C60 Bis-Adduct (ICBA, Lumtec) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s and an acceleration of 10000 rpm/s. Then the active layers were treated through solvent annealing for 1 hour and thermally annealed at 150° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured by spectroscopic ellipsometer (J. A. Woollam Co.).

After samples cooled down for 20 min in the glove box, they were transferred in ambient air and treated by O₂ plasma treatment for 1 s to tune the surface hydrophilic. Then a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) (HTL Solar formulation mixed with 10 volume % CPP105D) was spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEDOT:PSS layer was about 40 nm.

For the reference single solar cells with conventional structures, PEDOT:PSS 4083 was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEDOT:PSS was 40 nm. The P3HT:ICBA active layers were prepared in the same condition as prepared in the inverted single cells. Then a thin layer of PEIE was spin coated on top of plasma-treated active layer from a weight concentration of 0.02% at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s.

For a solar cell module comprising a first solar cell with an inverted structure and a second solar cell with a conventional structure an ITO substrate was etched with a gap about 1.7 mm to define two ITO electrodes. Then PEIE (0.2%) and PEDOT:PSS 4083 were spin coated onto the two parts of ITO at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s one after the other. A narrow (0.5-1 mm) polydimethylsiloxane (PDMS) was coated onto the gap between the patterned ITO electrodes prior to spin coating of PEIE and PEDOT:PSS, to selectively pattern PEIE and PEDOT:PSS. PDMS was peeled-off and the samples were annealed at 120° C. for 10 min on a hot plate in ambient air.

The active layers of P3HT:ICBA were prepared in the same condition as prepared for single solar cells. A thin layer of PEIE (from a 0.02 wt. % solution) and a layer of PEDOT:PSS (HTL Solar+10% v/v CPP 105D) were spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Prior to spin coating, the active layer was treated by an O₂ plasma for 1 s and PDMS was coated on the active layer to selectively patterned PEIE and PEDOT:PSS.

All the samples were transferred into a N₂-filled glove box and annealed on a hot plate at 110° C. for 10 min to dry PEIE and crosslink PEDOT:PSS HTL-CPP. All the samples were loaded into a vacuum thermal evaporation system (SPEC-TROS, Kurt J. Lesker) and a layer of Ag (150 nm) was deposited onto all of the samples through a shadow mask. The area of module devices was about 18 mm² not including the gap between the ITO electrodes having an area of 1.6 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an irradiance of 100 mW/cm² was used as the light source.

FIG. 159 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Ag) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 60.

FIG. 160 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Ag) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 60.

FIG. 161 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 59.

TABLE 60

Photovoltaic performance of inverted single cells and conventional single cells (averaged over 2 devices) and a module device; Data in parentheses are calculated with the area includes the gap (no ITO).

Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
Inverted single	0.82 ± 0.01	12.2 ± 0.3	0.61 ± 0.01	6.1 ± 0.2
Conventional single	0.71	8.7	0.57	3.5
Module	1.48	4.4 (4.0)	0.58	3.8 (3.4)

Example 13

Two-Cell Solar Module Comprising a P3HT:ICBA Active Layer with Pre-Annealing (No Solvent Annealing), PEDOT:PSS and PEIE as Two Interlayers and Al as Top Electrode

FIG. 162 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC60BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 10 min at 75° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. Then the substrates were treated by oxygen plasma for 2 min.

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a weight concentration of 0.2 wt. % and 0.02%.

For reference single solar cells with inverted structure, PEIE (0.2 wt. %) was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, Rieke Metals):Indene-C60 Bis-Adduct (ICBA, Lumtec) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s and an acceleration of 10000 rpm/s. Then the active layers were thermally annealed at 150° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured by spectroscopic ellipsometer (J. A. Woollam Co.).

After samples cooled down for 20 min in the glove box, they were transferred in ambient air and treated by O₂ plasma treatment for 1 s to tune the surface hydrophilic. Then a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) (HTL Solar formulation mixed with 10 volume % CPP105D) was spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEDOT:PSS layer was 40 nm.

For reference single solar cells with conventional structure, PEDOT:PSS 4083 was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in

ambient air. The thickness of PEDOT:PSS was 40 nm. The P3HT:ICBA active layers were prepared in the same condition as prepared in the inverted single cells. Then a thin layer of PEIE was spin coated on top of plasma-treated active layer from a weight concentration of 0.02% at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s.

For a solar cell module comprising a first solar cell with an inverted structure and a second solar cell with a conventional structure an ITO substrate was etched with a gap about 1.7 mm to define two ITO electrodes. Then PEIE (0.2%) and PEDOT:PSS 4083 were spin coated onto the two parts of ITO at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s one after the other. A narrow (0.5-1 mm) polydimethylsiloxane (PDMS) was coated onto the gap between the patterned ITO electrodes prior to spin coating of PEDOT:PSS, to selectively pattern PEIE and PEDOT:PSS. PDMS was peeled-off and the samples were annealed at 120° C. for 10 min on a hot plate in ambient air.

The active layers of P3HT:ICBA were prepared in the same condition as prepared for single solar cells. A thin layer of PEIE (from a 0.02 wt. % solution) and a layer of PEDOT:PSS (HTL Solar+10% v/v CPP 105D) were spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Prior to spin coating, the active layer was treated by an O₂ plasma for 1 s and PDMS was coated on the active layer to selectively pattern PEIE and PEDOT:PSS.

All the samples were transferred into a N₂-filled glove box and annealed on a hot plate at 110° C. for 10 min to dry PEIE and crosslink PEDOT:PSS HTL-CPP. All the samples were loaded into a vacuum thermal evaporation system (SPEC-TROS, Kurt J. Lesker) and a layer of Al (150 nm) was deposited onto all of the samples through a shadow mask. The area of module devices was about 18 mm² not including the gap between the ITO electrodes having an area of 1.6 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an irradiance of 100 mW/cm² was used as the light source.

FIG. 163 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 60.

FIG. 164 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 60.

FIG. 165 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 61.

TABLE 61

Photovoltaic performance of reference inverted single cells (averaged over 4 devices), reference conventional single cells (averaged over 3 devices) and a module solar cell devices; Data in parentheses are calculated with the area includes the gap (no ITO).					
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)	
Inverted single	0.83 0.01	8.3 ± 0.7	1	0.59 ± 0.01	2 4.0 ± 0.3

TABLE 61-continued

Photovoltaic performance of reference inverted single cells (averaged over 4 devices), reference conventional single cells (averaged over 3 devices) and a module solar cell devices; Data in parentheses are calculated with the area includes the gap (no ITO).					
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)	
Conventional single	0.80 ± 0.02	3 8.3 ± 0.1	4 0.46 ± 0.01	5	3.1 ± 0.1
Module	1.66	6 4.1 (3.0)	7 0.49	8	3.3 (2.5)

Example 14

Two-Cell Solar Module Comprising P3HT:ICBA Active Layer with Post-Annealing (No Solvent Annealing), PEDOT:PSS as Interlayer I (PEIE not Used in Single Cells with Conventional Geometry) and Al as Top Electrode

FIG. 166 shows a structure of inverted and conventional reference single solar cells, a solar cell module and chemical structure of PEIE, P3HT ICBA, PBDTTT-C and PC60BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 10 min at 75° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. Then the substrates were treated by oxygen plasma for 2 min.

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a weight concentration of 0.2 wt. % and 0.02%.

For reference single solar cells with inverted structure, PEIE (0.2 wt. %) was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, Rieke Metals):Indene-C60 Bis-Adduct (ICBA, Lumtec) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s and an acceleration of 10000 rpm/s. Then the active layers were thermally annealed at 150° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured by spectroscopic ellipsometer (J. A. Woollam Co.).

After samples cooled down for 20 min in the glove box, they were transferred in ambient air and treated by O₂ plasma treatment for 1 s to tune the surface hydrophilic. Then a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) (HTL Solar formulation mixed with 10 volume % CPP105D) was spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEDOT:PSS layer was 40 nm.

For reference single solar cells with conventional structure, PEDOT:PSS 4083 was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000

rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEDOT:PSS was 40 nm. The P3HT:ICBA active layers were prepared in the same condition as prepared in the inverted single cells.

For a solar cell module comprising a first solar cell with an inverted structure and a second solar cell with a conventional structure an ITO substrate was etched with a gap about 1.7 mm to define two ITO electrodes. Then PEIE (0.2%) and PEDOT:PSS 4083 were spin coated onto the two parts of ITO at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s one after the other. A narrow (0.5-1 mm) polydimethylsiloxane (PDMS) was coated onto the gap between the patterned ITO electrodes prior to spin coating of PEIE and PEDOT:PSS, to selectively pattern PEIE and PEDOT:PSS. PDMS was peeled-off and the samples were annealed at 120° C. for 10 min on a hot plate in ambient air.

The active layers of P3HT:ICBA were prepared in the same condition as prepared for single solar cells. A layer of PEDOT:PSS (HTL Solar+10% v/v CPP 105D) were spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Prior to spin coating, the active layer was treated by an O₂ plasma for 1 s and PDMS was coated on the active layer to selectively pattern PEDOT:PSS (to overlap the area containing PEIE underneath).

All the samples were transferred into a N₂-filled glove box and annealed on a hot plate at 110° C. for 10 min to crosslink PEDOT:PSS HTL-CPP. All the samples were loaded into a vacuum thermal evaporation system (SPECTROS, Kurt J. Lesker) and a layer of Al (150 nm) was deposited onto all of the samples through a shadow mask. The area of module devices was about 18 mm² not including the gap between the ITO electrodes having an area of 1.6 mm².

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an irradiance of 100 mW/cm² was used as the light source.

FIG. 167 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 61.

FIG. 168 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 61.

FIG. 169 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 61.

TABLE 61

Photovoltaic performance of inverted single cells (averaged over 4 devices) and conventional single cells (averaged over 5 devices) and a module device; Data in parentheses are calculated with the area includes the gap (no ITO).				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
Inverted single	0.83 ± 0.01	8.3 ± 0.7	0.59 ± 0.01	4.0 ± 0.3
Conventional single	0.61 ± 0.01	8.7 ± 0.2	0.57 ± 0.01	3.0 ± 0.1
Module	1.49	4.4 (3.7)	0.58	3.8 (3.2)

Four-Cell Solar Module Comprising a P3HT:ICBA Active Layer with Pre-Annealing and Solvent Annealing, PEDOT:PSS and PEIE as Two Interlayers and Al as Top Electrode

FIG. 170 shows a structure of inverted and conventional reference single solar cells, a four-cell solar module and chemical structure of PEIE, P3HT ICBA, PBDDTTT-C and PC60BM, according to an exemplary embodiment of the invention.

ITO-coated glass (Colorado Concept Coatings LLC) with a sheet resistivity of ~15 Ω/sq. was used as substrate. The ITO substrates were patterned with kapton tape and etched by acid vapor (1:3 by volume, HNO₃:HCl) for 10 min at 75° C. The patterned substrates were cleaned in an ultrasonic bath of detergent water, rinsed with deionized water, and then cleaned in sequential ultrasonic baths of deionized water, acetone, and isopropanol. Nitrogen was used to dry the substrates after each of the last three baths. Then the substrates were treated by oxygen plasma for 2 min.

Polyethylenimine, 80% ethoxylated (PEIE) (Mw=70,000 g/mol) was dissolved in H₂O with a concentration of 35-40 wt. % when received from Aldrich. Then, it was diluted into methoxyethanol to a weight concentration of 0.2 wt. % and 0.02%.

For reference single solar cells with inverted, PEIE (0.2 wt. %) was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on a hot plate in ambient air. The thickness of PEIE was 5 nm determined by spectroscopic ellipsometry (J. A. Woollam Co.).

The substrates were transferred into a N₂-filled glove box. The active layer of poly(3-hexylthiophene) (P3HT, 4002-E, Rieke Metals):Indene-C₆₀ Bis-Adduct (ICBA, Lumtec) (1:1, weight ratio) was filtered through 0.2-μm-pore PTFE filters and spin-coated on each substrate from a 40 mg/ml dichlorobenzene solution at a speed of 800 rpm for 30 s and an acceleration of 10000 rpm/s. Then the active layers were treated through solvent annealing for 1 hour and thermally annealed at 150° C. for 10 min on a hot plate in the glove box. The thickness of the active layer is 200 nm, measured by spectroscopic ellipsometer (J. A. Woollam Co.).

After samples cooled down for 20 min in the glove box, they were transferred in ambient air and treated by O₂ plasma treatment for 1 s to tune the surface hydrophilic. Then a layer of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS) (HTL Solar formulation mixed with 10 volume % CPP105D) was spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. The thickness of PEDOT:PSS layer was about 40 nm.

For the reference single solar cells with conventional structures, PEDOT:PSS 4083 was spin coated onto ITO substrates at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s and annealed at 120° C. for 10 min on hot plate in ambient air. The thickness of PEDOT:PSS was 40 nm. The P3HT:ICBA active layers were prepared in the same condition as prepared in the inverted single cells. Then a thin layer of PEIE was spin coated on top of plasma-treated active layer from a weight concentration of 0.02% at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s.

A four-cell module comprising two solar cells with an inverted structure and two solar cells with a conventional structure, as shown in FIG. 170. An ITO substrate was etched with two gaps about 2.0 mm to define ITO electrodes. Then PEIE (0.4%) and PEDOT:PSS 4083 were spin coated onto

four parts of ITO at a speed of 5000 rpm for 1 min and at an acceleration of 1000 rpm/s one after the other. Narrow pieces of (0.5-1 mm) polydimethylsiloxane (PDMS) were coated onto the gaps prior to spin coating to pattern the PEIE and PEDOT:PSS. After subsequent spin coatings of PEIE and PEDOT:PSS, PDMS was peeled off and the samples were annealed at 120° C. for 10 min on a hot plate in ambient air.

The active layers of P3HT:ICBA were prepared in the same condition as prepared for single solar cells. Then a thin layer of PEIE from a weight concentration of 0.04% and a layer of PEDOT:PSS HTL Solar were spin coated on top of the active layer at a speed of 5000 rpm for 1 min and an acceleration of 1000 rpm/s. Prior to spin coating, the active layer was treated by O₂ plasma for 1 s and PDMS was coated on the active layer to pattern PEIE and PEDOT:PSS.

All the samples were transferred into a N₂-filled glove box and annealed on a hot plate at 110° C. for 10 min to dry PEIE and crosslink PEDOT:PSS HTL-CPP. All samples were loaded into a vacuum thermal evaporation system (SPEC-TROS, Kurt J. Lesker) and a layer of Al (150 nm) was deposited onto all of the samples through a shadow mask. Area of module devices was about 15 mm² not including the gap between the ITO electrodes.

Current density-voltage (J-V) characteristics were measured inside the N₂-filled glove box by using a source meter (2400, Keithley Instruments, Cleveland, Ohio) controlled by a LabVIEW program. To test the solar cell properties under illumination, an Oriel lamp with an air mass 1.5 filter and an irradiance of 100 mW/cm² was used as the light source.

FIG. 171 shows a J-V characteristics of reference inverted single solar cell (glass/ITO/PEIE/P3HT:ICBA/PEDOT:PSS/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 62.

FIG. 172 shows a J-V characteristics of reference conventional single solar cell (glass/ITO/PEDOT:PSS/P3HT:ICBA/PEIE/Al) in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 62.

FIG. 173 shows a J-V characteristics of a solar cell module in dark and under AM 1.5 100 mW/cm² illumination, according to an exemplary embodiment of the invention. Device performance is summarized in Table 62.

TABLE 62

Photovoltaic performance of inverted single cells (averaged over 4 devices) and conventional single cells (averaged over 4 devices) and a module device;				
Sample	V _{OC} (V)	J _{SC} (mA/cm ²)	FF	PCE (%)
Inverted single	0.80 ± 0.01	10.7 ± 0.1	0.60 ± 0.01	5.2 ± 0.1
Conventional single	0.83 ± 0.01	9.4 ± 0.2	0.59 ± 0.01	4.6 ± 0.1
4-cell Module	3.18	2.3	0.70	5.1

As desired, embodiments of the invention may include the materials, layers, processes, and/or structures with more or less of the components illustrated in FIGS. 1-173.

While certain embodiments of the invention have been described in connection with what is presently considered to be the most practical and various embodiments, it is to be understood that the invention is not to be limited to the disclosed embodiments, but on the contrary, is intended to cover various modifications and equivalent arrangements included

within the scope of the appended claims. Although specific terms are employed herein, they are used in a generic and descriptive sense only and not for purposes of limitation.

This written description uses examples to disclose certain embodiments of the invention, including the best mode, and also to enable any person skilled in the art to practice certain embodiments of the invention, including making and using any devices or systems and performing any incorporated methods. The patentable scope of certain embodiments of the invention is defined in the claims, and may include other examples that occur to those skilled in the art. Such other examples are intended to be within the scope of the claims if they have structural elements that do not differ from the literal language of the claims, or if they include equivalent structural elements with insubstantial differences from the literal language of the claims.

The claimed invention is:

1. A method for reducing a work function of an electrode, the method comprising:

applying, to at least a portion of a conductive polymer electrode, a solution comprising a Lewis basic oligomer or polymer; and

based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 1.0 eV, and wherein forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 50 nm.

2. The method of claim 1, wherein forming the ultra-thin layer from the solution reduces the work function associated with the electrode, and wherein the work function is stable in ambient air and varies by less than 20 percent over a period of greater than 10 hours after forming the ultra thin layer.

3. The method of claim 1, wherein forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 10 nm.

4. The method of claim 1, wherein applying the solution comprises applying a Lewis basic oligomer or polymer comprising nitrogen in a trivalent state bonded to carbon in a tetravalent state.

5. The method of claim 1, wherein applying the solution comprises applying a Lewis basic oligomer or polymer comprising oxygen in a divalent state bonded to carbon in a tetravalent state.

6. The method of claim 1, wherein applying the solution comprises applying a Lewis basic oligomer or polymer comprising sulfur in a divalent state bonded to carbon in a tetravalent state.

7. The method of claim 1, wherein applying the solution comprises applying the Lewis basic oligomer or polymer, wherein the Lewis basic oligomer or polymer comprises molecules having molecular weight greater than 0.1 kDa and less than 1000 kDa.

8. The method of claim 1, wherein the conductive polymer electrode comprises an organic material.

9. The method of claim 1, wherein forming the ultra-thin layer reduces the work function associated with the electrode by forming an interfacial dipole at the interface between a surface of the electrode and a surface of the ultra-thin layer.

10. The method of claim 1, wherein the ultra-thin layer reduces the work function associated with the electrode by between 1.0 eV and 1.8 eV.

11. A method for reducing a work function of an electrode, the method comprising:

applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer, wherein

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the electrode comprises an organic material or mixtures of metals and organic materials; and
 based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by greater than 1.0 eV, and wherein forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 50 nm.

12. The method of claim 11, wherein forming the ultra-thin layer from the solution reduces the work function associated with the electrode, and wherein the work function is stable in ambient air and varies by less than 20 percent over a period of greater than 10 hours after forming the ultra thin layer.

13. The method of claim 11, wherein forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 10 nm.

14. The method of claim 11, wherein applying the solution comprises applying the Lewis basic oligomer or polymer, wherein the Lewis basic oligomer or polymer comprises molecules having molecular weight greater than 0.1 kDa and less than 1000 kDa.

15. The method of claim 11, wherein applying the solution to at least a portion of the electrode comprises applying the

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solution to one or more polymers, a transparent conductive metal-oxide, graphene, metal nanorods, metal particles, or metal oxide particles, or a mixture thereof.

16. The method of claim 11, wherein the ultra-thin layer reduces the work function associated with the electrode by between 1.0 eV and 1.8 eV.

17. A method for reducing a work function of an electrode, the method comprising:

applying, to at least a portion of the electrode, a solution comprising a Lewis basic oligomer or polymer, wherein the electrode comprises a metal or a mixtures of metals; and

based at least in part on applying the solution, forming an ultra-thin layer on a surface of the electrode, wherein the ultra-thin layer reduces the work function associated with the electrode by a value greater than 1.0 eV, and wherein forming the ultra-thin layer comprises forming, on the electrode, an insulating layer having a thickness less than 50 nm.

18. The method of claim 17, wherein applying the solution to at least a portion of the electrode comprises applying the solution to one or more of: metal nanorods, metal particles, or metal oxide particles, or a mixture thereof.

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